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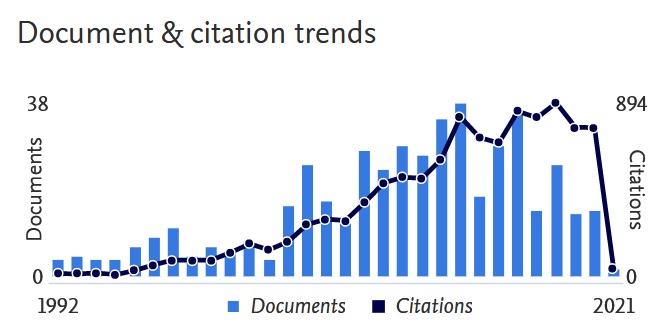
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* 1. **JOURNAL PAPERS (276)**

**2021**

1. [Rehman, A.; Smirnov, S.; Krajewska, A.; But, DB.; Liszewska, M.; Bartosewicz, B.; Pavlov, K.; Cywinski, G.; Lioubtchenko, D .; Knap, W.; Rumyantsev, S.; **Effect of ultraviolet light on 1/f noise in carbon nanotube networks.** *Materials Research Bulletin*, 2021, 134, 111093](https://sci-hub.se/10.1016/j.materresbull.2020.111093)

**2020**

1. [Vainshtein, S.; Duan, G.; Rahkonen, T.; Taylor, Z.; Zemlyakov, V.; Egorkin, V.; Smolyanskaya, O.; Skotnicki, T.; Knap, W., **Self-damping of the relaxation oscillations in miniature pulsed transmitter for sub-nanosecond-precision, long-distance LIDAR.** *Results in Physic*2020, *19*, 103509.](https://reader.elsevier.com/reader/sd/pii/S2211379720319616?token=4E634C2C3F07CCECCE9DE69A157192BDF834758C344E2938C3261AA232D6B5C2E5C6C7A615366DD276055D67D12E069A)
2. [Grigelionis, I.; Diakonova, N.; Knap, W.; Teppe, F.; Prystawko, P.; Kašalynas, I., **Radiation from shallow oxygen impurity in AlGaN/GaN HEMT structures in magnetic field.** *Solid State Communications* **2020**, *320*, 114019.](https://sci-hub.se/10.1016/j.ssc.2020.114019)
3. [Boubanga-Tombet, S.; Knap, W.; Yadav, D.; Satou, A.; But, D.B.; Popov, V.V.; Gorbenko, I.V.; Kachorovskii, V.; Otsuji, T.,](https://journals.aps.org/prx/pdf/10.1103/PhysRevX.10.031004) **[Room-Temperature Amplification of Terahertz Radiation by Grating-Gate Graphene Structures.](https://journals.aps.org/prx/pdf/10.1103/PhysRevX.10.031004)***[Physical Review X](https://journals.aps.org/prx/pdf/10.1103/PhysRevX.10.031004)* [2020,](https://journals.aps.org/prx/pdf/10.1103/PhysRevX.10.031004) *[10](https://journals.aps.org/prx/pdf/10.1103/PhysRevX.10.031004)*[(3), 031004.](https://journals.aps.org/prx/pdf/10.1103/PhysRevX.10.031004)
4. [Dub, M.; Sai, P.; Przewłoka, A.; Krajewska, A.; Sakowicz, M.; Prystawko, P.; Kacperski, J.; Pasternak, I.; Cywiński, G.; But, D.; Knap, W.; Rumyantsev, S., **Graphene as a schottky barrier contact to AlGaN/GaN heterostructures.** *Materials* 2020, *13*(18), 4140.](https://sci-hub.se/10.3390/ma13184140)
5. [Mantion, S.; Avogadri, C.; Krishtopenko, S.S.; Gebert, S.; Ruffenach, S.; Consejo, C.; Morozov, S.V.; Mikhailov, N.N.; Dvoretskii, S.A.; Knap, W.; Nanot, S.; Teppe, F.; Jouault, B., **Quantum Hall states in inverted HgTe quantum wells probed by transconductance fluctuations.** *Physical Review B* 2020, *102*(7), 075302.](https://sci-hub.se/10.1103/PhysRevB.102.075302)
6. [Krishtopenko, S.S.; Kadykov, A.M.; Gebert, S.; Ruffenach, S.; Consejo, C.; Torres, J.; Avogadri, C.; Jouault, B.; Knap, W.; Mikhailov, N.N.; Dvoretskii, S.A.; Teppe, F., **Many-particle effects in optical transitions from zero-mode Landau levels in HgTe quantum wells.** *Physical Review B* 2020, *102*(4), 041404.](https://sci-hub.se/10.1103/PhysRevB.102.041404)
7. [Barani, Z.; Kargar, F.; Godziszewski, K.; Rehman, A.; Yashchyshyn, Y.; Rumyantsev, S.; Cywiński, G.; Knap, W.; Balandin, A.A., **Graphene Epoxy-Based Composites as Efficient Electromagnetic Absorbers in the Extremely High-Frequency Band.** *ACS Applied Materials and Interfaces* 2020, *12*(25), 28635-28644.](https://sci-hub.se/10.1021/acsami.0c06729)
8. [Hubmann, S.; Budkin, G.V.; Otteneder, M.; But, D.; Sacré, D.; Yahniuk, I.; Diendorfer, K.; Bel'Kov, V.V.; Kozlov, D.A.; Mikhailov, N.N.; Dvoretsky, S.A.; Varavin, V.S.; Remesnik, V.G.; Tarasenko, S.A.; Knap, W.; Ganichev, S.D., **Symmetry breaking and circular photogalvanic effect in epitaxial CdxHg1-xTe films.** *Physical Review Material*s 2020, *4*(4), 043607.](https://kopernio.com/viewer?doi=10.1103%2Fphysrevmaterials.4.043607&token=WzMxMTI3NTAsIjEwLjExMDMvcGh5c3Jldm1hdGVyaWFscy40LjA0MzYwNyJd.BS9J0ieVCUwnInEWXHm1__IaYFo)
9. [Otteneder, M.; Sacré, D.; Yahniuk, I.; Budkin, G.V.; Diendorfer, K.; Kozlov, D.A.; Dmitriev, I.A.; Mikhailov, N.N.; Dvoretsky, S.A.; Bel'kov, V.V.; Knap, W.; Ganichev, S.D, *Physica Status Solidi (B) Basic Research*, 2020](https://onlinelibrary.wiley.com/doi/epdf/10.1002/pssb.202000023)
10. [Jorudas, J.; Simukovic, A.; Dub, M.; Sakowicz, M.; Prystawko, P.; Indrisiunas, S.; Kovalevskij, V.; Rumyantsev, S.; Knap, W.; Kasalynas, I.;](https://sci-hub.se/10.3390/mi11121131" \o "Find more records by this author) **[AlGaN/GaN on SiC Devices without a GaN Buffer Layer: Electrical and Noise Characteristics.](https://sci-hub.se/10.3390/mi11121131" \o "Find more records by this author)***[Micromachines](https://sci-hub.se/10.3390/mi11121131" \o "Find more records by this author)*[, 2020, 11(12), 1131](https://sci-hub.se/10.3390/mi11121131" \o "Find more records by this author)

**2019**

1. [Krishtopenko, S.; Ruffenach, S.; González-Posada Flores, F.; Consejo, C.; Desrat, W.; Jouault, B.; Knap, W.; Fadeev, M.; Kadykov, A.; Rumyantsev, V.; Morozov, S.; Bossier, G.; Tournie, E.; Gavrilenko, V.; Teppe, F., **Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well.** *JETP Letters* 2019,*109* (2), 96-101.](https://sci-hub.se/10.1134/S0021364019020085)
2. [Sai, P.; But, D.; Yahniuk, I.; Grabowski, M.; Sakowicz, M.; Kruszewski, P.; Prystawko, P.; Khachapuridze, A.; Nowakowski-Szkudlarek, K.; Przybytek, J.; Wiśniewski, P.; Stonio, B.; Słowikowski, M.; Rumyantsev, S.; Knap, W.; Cywiński, G., **AlGaN/GaN Field Effect Transistor with Two Lateral Schottky Barrier Gates Towards Resonant Detection in Sub-mm Range.** *Semiconductor Science and Technology* 2019,*34* (2), 024002.](https://iopscience.iop.org/article/10.1088/1361-6641/aaf4a7/pdf)
3. [Krishtopenko, S. S.; Desrat, W.; Spirin, K. E.; Consejo, C.; Ruffenach, S.; Gonzalez-Posada, F.; Jouault, B.; Knap, W.; Maremyani, K. V.; Gavrilenko, V. I.; Bossier, G.; Torres, J.; Zaknoune, M.; Tournie, E.; Teppe, F., **Massless Dirac Fermions in III-V Semiconductor Quantum Wells.** *Physical Review B* 2019,*99* (12), 121405.](https://sci-hub.se/10.1103/PhysRevB.99.121405)
4. [Zagrajek, P.; Danilov, S. N.; Marczewski, J.; Zaborowski, M.; Kolacinski, C.; Obrebski, D.; Kopyt, P.; Salski, B.; But, D.; Knap, W.; Gaichev, S. D., **Time Resolution and Dynamic Range of Field-Effect Transistor-Based Terahertz Detectors.**, *Journal of Infrared Millimeter and Terahertz Waves* 2019,*40* (7), 703-719.](https://sci-hub.se/https:/link.springer.com/article/10.1007/s10762-019-00605-0)
5. [Fahs, B.; Wu, K.; Aouimeur, W.; Mansha, M.W.; Gaquière, C.; Gamand, P.; Knap, W.; Hella, M.M., **About 250/285 GHz push–push oscillator using differential gate equalisation in digital 65-nm CMOS.**, *IET Microwaves, Antennas and Propagation* 2019,*13* (12), 2073-2080.](https://sci-hub.se/10.1049/iet-map.2018.5308)
6. [Sai, P.; Jorudas, J.; Dub, M.; Sakowicz, M.; Jakstas, V.; But, D. B.; Prystawko, P.; Cywiński, G.; Kasalynas, I.; Knap, W.; Rumyantsev, S., **Low frequency Noise and Trap Density in GaN/AlGaN field effect transistors.** *Applied Physics Letters* 2019,*115* (18), 183501.](https://aip.scitation.org/doi/pdf/10.1063/1.5119227)
7. [But, D. B.; Mittendorff, M.; Consejo, C.; Teppe, F.; Mikhailov, N. N.; Dvoretskii, S. A.; Faugeras, C.; Winnerl, S.; Helm, M.; Knap, W.; Potemski, M.; Orlita, M.,](https://sci-hub.se/https:/www.nature.com/articles/s41566-019-0496-1) **[Suppressed Auger Scattering and Tunable Light Emission of Landau-Quantized Massless Kane Electrons.](https://sci-hub.se/https:/www.nature.com/articles/s41566-019-0496-1)**[,](https://sci-hub.se/https:/www.nature.com/articles/s41566-019-0496-1) *[Nature Photonic](https://sci-hub.se/https:/www.nature.com/articles/s41566-019-0496-1)* [2019,](https://sci-hub.se/https:/www.nature.com/articles/s41566-019-0496-1)*[13](https://sci-hub.se/https:/www.nature.com/articles/s41566-019-0496-1)* [(11), 783-787.](https://sci-hub.se/https:/www.nature.com/articles/s41566-019-0496-1)
8. [Yahniuk, I.; Krishtopenko, S. S.; Grabecki, G.; Jouault, B.; Consejo, C.; Desrat, W.; Majewicz, M.; Kadykov, A. M.; Spirin, K. E.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretsky, S. A.; But, D. B.; Teppe, F.; Wróbel, J.; Cywiński, G.; Kret, S.; Dietl, T.; Knap, W.,](https://sci-hub.se/10.1038/s41535-019-0154-3) **[Magneto-Transport in Inverted HgTe Quantum Wells.](https://sci-hub.se/10.1038/s41535-019-0154-3)***[npj Quantum Materials](https://sci-hub.se/10.1038/s41535-019-0154-3)* [2019,](https://sci-hub.se/10.1038/s41535-019-0154-3)*[4](https://sci-hub.se/10.1038/s41535-019-0154-3)* [(1), 13.](https://sci-hub.se/10.1038/s41535-019-0154-3)
9. [Zholudev, S. M.; Kadykov, M. A.; Fadeev, A. M.; Marcinkiewicz, M.; Ruffenach, S.; Consejo, C.; Knap, W.; Torres, J.; Morozov, S. V.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretskii, S. A.; Teppe, F., **Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells.** *Condensed Matter* 2019,*4* (1), 27.](https://sci-hub.se/10.3390/condmat4010027)

**2018**

1. [Yavorskiy, D.; Karpierz, K.; Grynberg, M.; Knap, W.; Łusakowski, J., **Indium antimonide detector for spectral characterization of terahertz sources** *Journal of Applied Physics* 2018,*123* (6).](https://sci-hub.se/10.1063/1.5002765)

2. [Kadykov, A. M.; Krishtopenko, S. S.; Jouault, B.; Desrat, W.; Knap, W.; Ruffenach, S.; Consejo, C.; Torres, J.; Morozov, S. V.; Mikhailov, N. N.; Dvoretskii, S. A.; Teppe, F., **Temperature-Induced Topological Phase Transition in HgTe Quantum Wells.** *Physical Review Letters* 2018,*120* (8 — 23 ).](https://hal.archives-ouvertes.fr/hal-01740166/document)

[3. Cywiński, G.; Yahniuk, I.; Kruszewski, P.; Grabowski, M.; Nowakowski-Szkudlarek, K.; Prystawko, P.; Sai, P.; Knap, W.; Simin, G. S.; Rumyantsev, S. L., **Electrically controlled wire-channel GaN/AlGaN transistor for terahertz plasma applications** *Applied Physics Letters* 2018,*112* (13).](https://sci-hub.se/10.1063/1.5023391)

4. [Desrat, W.; Krishtopenko, S. S.; Piot, B. A.; Orlita M; Consejo, C.; Ruffenach, S.; Knap*,* W.; Nateprov, A.; Arushanov, E.; Teppe, F., **Band Splitting in Cd3As2 Measured by Magnetotransport.** *Physical Review B*2018,*97* (24), 245203.](https://sci-hub.se/10.1103/PhysRevB.97.245203)

5. [Krishtopenko, S. S., Ruffenach, S.; Gonzalez-Posada, F.; Boissier, G.; Marcinkiewicz, M.; Fadeev, M. A.; Kadykov*,* A. M.; Rumyantsev, V. V.; Morozov, S. V.; Gavrilenko, V. I.; Consejo, C.; Desrat, W.; Jouault, B.; Knap, W.; Tournie, E.; Teppe, F., **Temperature-Dependent Terahertz Spectroscopy of Inverted-Band Three-Layer InAs/GaSb/InAs Quantum Well.** *Physical Review B*2018,*97* (24), 245419.](https://sci-hub.se/10.1103/PhysRevB.97.245419)

6. [Zhang, B.; Wei, Y.; Li, Z.; Bai, L.; Cywinski, G.; Yahniuk, I.; Szkudlarek, K.;Skierbiszewski, C.; Przybytek, J.; But, D.; Coquillat, D.; Knap, W.; Yang, F.-H., **An Effective Method for Antenna Design in Field Effect Transistor Terahertz Detectors.** *Journal of infrared and milimeter waves* 2018*,37* (4), 389-392.](https://www.researchgate.net/publication/329116974_An_effective_method_for_antenna_design_in_field_effect_transistor_terahertz_detectors)

7. [Coquillat, D., Duhant, A.; Triki, M.; Nodjiadjim, V.; Konczykowska, A.; Riet, M.; Dyakonova, N.; Strauss, O.; Knap, W., **InP Double Heterojunction Bipolar Transistors for Terahertz Computed Tomography.** *AIP Advances* 2018*,8* (8), 085320.](https://aip.scitation.org/doi/pdf/10.1063/1.5039331)

8. [Bąk, M.; Yavorskiy, D.; Karpierz, K.; Łusakowski, J.; But, D.; Przybytek, J.; Yahniuk, I.; Cywiński, G.; Knap, W.; Teppe, F.; Krishtopenko, S.; Mikhailov, N. N.; Dvoretsky, S. A.; Gavrilenko, V. I., **Magnetoconductivity of a mercury cadmium telluride resonant THz detector.** *Acta Physica Polonica A* 2018*,134* (4), 973-977.](http://przyrbwn.icm.edu.pl/APP/PDF/134/app134z4p16.pdf)

9. [Marczewski, J.; Coquillat, D.; Knap, W.; Kolacinski, C.; Kopyt, P.; Kucharski, K.; Lusakowski*,* J.; Obrebski, D.; Tomaszewski, D.; Yavorskiy, D.; Zagrajek P.; Ryniec, R.; Palka, N., **Thz Detectors Based on Si-CMOS Technology Field Effect Transistors – Advantages, Limitations and Perspectives for Thz Imaging and Spectroscopy.** *Opto-Electronics Review* 2018*,*2*6* (4), 261-269.](https://sci-hub.se/10.1016/j.opelre.2018.08.002)

10. [Yavorskiy, D.; Karpierz, K.; Baj, M.; Bąk, M. M.; Mikhailov, N. N.; Dvoretsky, S. A.; Gavrilenko, V. I.; Knap, W.; Teppe, F.; Łusakowski, J., **Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer.** *Sensors* 2018*,18* (12), 4341.](https://sci-hub.se/10.3390/s18124341)

**2017**

1. [Ruffenach, S.; Kadykov, A.; Rumyantsev, V. V.; Torres, J.; Coquillat, D.; But, D.; Krishtopenko, S. S.; Consejo, C.; Knap, W.; Winnerl, S.; Helm, M.; Fadeev, M. A.; Mikhailov, N. N.; Dvoretskii, S. A.; Gavrilenko, V. I.; Morozov, S. V.; Teppe, F., **HgCdTe-based heterostructures for terahertz photonics.** *APL Materials* 2017,*5* (3), 035503.](https://sci-hub.se/10.1063/1.4977781)
2. [Rachon, M.; Liebert, K.; Siemion, A.; Bomba, J.; Sobczyk, A.; Knap, W.; Coquillat, D.; Suszek, J.; Sypek, M., **Geometrical Aberration Suppression for Large Aperture Sub-THz Lenses.** *Journal of Infrared, Millimeter, and Terahertz Waves* 2017,*38* (3), 347-355](https://sci-hub.se/10.1007/s10762-016-0342-1)
3. [Marcinkiewicz, M.; Ruffenach, S.; Krishtopenko, S. S.; Kadykov, A. M.; Consejo, C.; But, D. B.; Desrat, W.; Knap, W.; Torres, J.; Ikonnikov, A. V.; Spirin, K. E.; Morozov, S. V.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretskii, S. A.; Teppe, F., **Temperature-driven single-valley Dirac fermions in HgTe quantum wells.** *Physical Review B* 2017,*96* (3), 35405-35405.](https://sci-hub.se/10.1103/PhysRevB.96.035405)
4. [Liebert, K.; Rachon, M.; Siemion, A.; Suszek, J.; But, D.; Knap, W.; Sypek, M., **THz Beam Shaper Realizing Fan-Out Patterns.** *Journal of Infrared, Millimeter, and Terahertz Waves* 2017,*38* (8), 1019-1030](https://sci-hub.se/10.1007/s10762-017-0398-6)
5. [Krishtopenko, S. S.; Ikonnikov, A. V.; Maremyanin, K. V.; Bovkun, L. S.; Spirin, K. E.; Kadykov, A. M.; Marcinkiewicz, M.; Ruffenach, S.; Consejo, C.; Teppe, F.; Knap, W.; Semyagin, B. R.; Putyato, M. A.; Emelyanov, E. A.; Preobrazhenskii, V. V.; Gavrilenko, V. I., **Cyclotron resonance of dirac fermions in InAs/GaSb/InAs quantum wells.** *Semiconductors* 2017,*51* (1), 38-42](https://sci-hub.se/10.1134/S1063782617010109)
6. [Auton, G.; But, D. B.; Zhang, J.; Hill, E.; Coquillat, D.; Consejo, C.; Nouvel, P.; Knap, W.; Varani, L.; Teppe, F.; Torres, J.; Song, A., **Terahertz Detection and Imaging Using Graphene Ballistic Rectifiers.** *Nano Letters* 2017,*17* (11), 7015-7020.](https://sci-hub.se/10.1021/acs.nanolett.7b03625)
7. [Ruffenach, S.; Krishtopenko, S. S.; Bovkun, L. S.; Ikonnikov, A. V.; Marcinkiewicz, M.; Consejo, C.; Potemski, M.; Piot, B.; Orlita, M.; Semyagin, B. R.; Putyato, M. A.; Emel’yanov, E. A.; Preobrazhenskii, V. V.; Knap, W.; Gonzalez-Posada, F.; Boissier, G.; Tournié, E.; Teppe, F.; Gavrilenko, V. I., **Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs “Three-Layer” Gapless Quantum Wells.** *JETP Letters 2017,106, 727-732*](https://sci-hub.se/10.1134/S0021364017230102)

**2016**

1. [Viti, L.; Hu, J.; Coquillat, D.; Politano, A.; Knap, W.; Vitiello, M. S., **Efficient Terahertz detection in black-phosphorus nano-transistors with selective and controllable plasma-wave, bolometric and thermoelectric response.** *Scientific Reports* 2016,*6*.](https://sci-hub.se/10.1038/srep20474)
2. [Viti, L.; Hu, J.; Coquillat, D.; Politano, A.; Consejo, C.; Knap, W.; Vitiello, M. S., **Heterostructured hBN-BP-hBN Nanodetectors at Terahertz Frequencies.** *Advanced Materials* 2016,*28* (34), 7390-7396.](https://sci-hub.se/10.1002/adma.201601736)
3. [Viti, L.; Coquillat, D.; Politano, A.; Kokh, K. A.; Aliev, Z. S.; Babanly, M. B.; Tereshchenko, O. E.; Knap, W.; Chulkov, E. V.; Vitiello, M. S., **Plasma-Wave Terahertz Detection Mediated by Topological Insulators Surface States.** *Nano Letters* 2016,*16* (1), 80-87](https://sci-hub.se/10.1021/acs.nanolett.5b02901)
4. [Teppe, F.; Marcinkiewicz, M.; Krishtopenko, S. S.; Ruffenach, S.; Consejo, C.; Kadykov, A. M.; Desrat, W.; But, D.; Knap, W.; Ludwig, J., **Temperature-driven massless Kane fermions in HgCdTe crystals.** *Nature communications* 2016,*7*.](https://sci-hub.se/10.1038/ncomms12576)
5. [Szkudlarek, K.; Sypek, M.; Cywiński, G.; Suszek, J.; Zagrajek, P.; Feduniewicz-Żmuda, A.; Yahniuk, I.; Yatsunenko, S.; Nowakowska-Siwińska, A.; Coquillat, D.; But, D. B.; Rachoń, M.; Węgrzyńska, K.; Skierbiszewski, C.; Knap, W., **Terahertz 3D printed diffractive lens matrices for field-effect transistor detector focal plane arrays.** *Optics Express* 2016,*24*  (18), 20119-20131](https://sci-hub.se/10.1364/OE.24.020119)
6. [Ryzhii, V.; Otsuji, T.; Ryzhii, M.; Leiman, V. G.; Fedorov, G.; Goltzman, G. N.; Gayduchenko, I. A.; Titova, N.; Coquillat, D.; But, D.; Knap, W.; Mitin, V.; Shur, M. S., **Two-dimensional plasmons in lateral carbon nanotube network structures and their effect on the terahertz radiation detection.** *Journal of Applied Physics* 2016,*120* (4), 044501.](https://sci-hub.se/10.1063/1.4959215)
7. [Nahar, S.; Shafee, M.; Blin, S.; Pénarier, A.; Nouvel, P.; Coquillat, D.; Safwa, A. M. E.; Knap, W.; Hella, M. M., **Wide modulation bandwidth terahertz detection in 130 nm CMOS technology.** *The European Physical Journal Applied Physics* 2016,*76* (2), 20101.](https://sci-hub.se/10.1051/epjap/2016160302)
8. [Krishtopenko, S. S.; Yahniuk, I.; But, D. B.; Gavrilenko, V. I.; Knap, W.; Teppe, F., **Pressure- and temperature-driven phase transitions in HgTe quantum wells.** *Physical Review B* 2016,*94* (24), 245402-245402.](https://sci-hub.se/10.1103/PhysRevB.94.245402)
9. [Krishtopenko, S. S.; Knap, W.; Teppe, F., **Phase transitions in two tunnel-coupled HgTe quantum wells: Bilayer graphene analogy and beyond.** *Scientific Reports* 2016,*6*, 30755](https://sci-hub.se/10.1038/srep30755)
10. [Knap, W.; But, D. B.; Couquillat, D.; Dyakonova, N.; Sypek, M.; Suszek, J.; Domracheva, E.; Chernyaeva, M.; Vaks, V.; Maremyanin, K.; Gavrilenko, V.; Archier, C.; Moulin, B.; Cywinski, G.; Yahniuk, I.; Szkudlarek, K., **Imaging and Gas Spectroscopy for Health Protection in Sub-THz Frequency Range.** *International Journal of High Speed Electronics and Systems* 2016,*25* (49), 1640017](https://sci-hub.se/10.1142/S0129156416400176)
11. [Kadykov, A. M.; Torres, J.; Krishtopenko, S. S.; Consejo, C.; Ruffenach, S.; Marcinkiewicz, M.; But, D.; Knap, W.; Morozov, S. V.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretsky, S. A.; Teppe, F., **Terahertz imaging of Landau levels in HgTe-based topological insulators.** *Applied Physics* ***Letters* 2016,*108*** (26), 262102.](https://sci-hub.se/10.1063/1.4955018)
12. [Kadykov, A. M.; Consejo, C.; Marcinkiewicz, M.; Viti, L.; Vitiello, M. S.; Krishtopenko, S. S.; Ruffenach, S.; Morozov, S. V.; Desrat, W.; Dyakonova, N.; Knap, W.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretsky, S. A.; Teppe, F., **Observation of topological phase transition by terahertz photoconductivity in HgTe-based transistors.** *Physica Status Solidi C-Current Topics in Solid State Physics* 2016,*13* (7-9), 534-537.](https://sci-hub.se/10.1002/pssc.201510264)
13. [Ikonnikov, A. V.; Krishtopenko, S. S.; Drachenko, O.; Goiran, M.; Zholudev, M. S.; Platonov, V. V.; Kudasov, Y. B.; Korshunov, A. S.; Maslov, D. A.; Makarov, I. V.; Surdin, O. M.; Philippov, A. V.; Marcinkiewicz, M.; Ruffenach, S.; Teppe, F.; Knap, W.; Mikhailov, N. N.; Dvoretsky, S. A.; Gavrilenko, V. I., **Temperature-dependent magnetospectroscopy of HgTe quantum wells.** *Physical Review B* 2016,*94* (15), 155421-155421.](https://sci-hub.se/10.1103/PhysRevB.94.155421)
14. [Dyakonova, N.; Faltermeier, P.; But, D. B.; Coquillat, D.; Ganichev, S. D.; Knap, W.; Szkudlarek, K.; Cywinski, G., **Saturation of photoresponse to intense THz radiation in AlGaN/GaN HEMT detector.** *JOURNAL OF APPLIED PHYSICS* 2016,*120* (16), 164507.](https://sci-hub.se/10.1063/1.4966575)
15. [Cywiński, G.; Szkudlarek, K.; Kruszewski, P.; Yahniuk, I.; Yatsunenko, S.; Muzioł, G.; Skierbiszewski, C.; Knap, W.; Rumyantsev, S. L., **Low frequency noise in two-dimensional lateral GaN/AlGaN Schottky diodes.** *Applied Physics Letters* 2016,*109* (3).](https://sci-hub.se/10.1063/1.4958857)
16. [Cywiński, G.; Szkudlarek, K.; Kruszewski, P.; Yahniuk, I.; Yatsunenko, S.; Muzioł, G.; Siekacz, M.; Skierbiszewski, C.; Rumyantsev, S.; Knap, W., **MBE grown GaN/AlGaN lateral Schottky barrier diodes for high frequency applications.** *Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics* 2016,*34* (2).](https://sci-hub.se/10.1116/1.4944320)
17. [Coquillat, D.; Nodjiadjim, V.; Blin, S.; Konczykowska, A.; Dyakonova, N.; Consejo, C.; Nouvel, P.; Pènarier, A.; Torres, J.; But, D.; Ruffenach, S.; Teppe, F.; Riet, M.; Muraviev, A.; Gutin, A.; Shur, M.; Knap, W., **High-Speed Room Temperature Terahertz Detectors Based on InP Double Heterojunction Bipolar Transistors.** *International Journal of High Speed Electronics and Systems* 2016,*25* (03n04), 1640011.](https://sci-hub.se/10.1142/s0129156416400115)
18. [Coquillat, D.; Marczewski, J.; Kopyt, P.; Dyakonova, N.; Giffard, B.; Knap, W., **Improvement of terahertz field effect transistor detectors by substrate thinning and radiation losses reduction.** *Optics Express* 2016,*24* (1), 272-281.](https://sci-hub.se/10.1364/OE.24.000272)
19. [Bovkun, L. S.; Krishtopenko, S. S.; Ikonnikov, A. V.; Aleshkin, V. Y.; Kadykov, A. M.; Ruffenach, S.; Consejo, C.; Teppe, F.; Knap, W.; Orlita, M.; Piot, B.; Potemski, M.; Mikhailov, N. N.; Dvoretskii, S. A.; Gavrilenko, V. I., **Magnetospectroscopy of double HgTe/CdHgTe quantum wells.** *Semiconductors* 2016,*50* (11), 1532-1538.](https://sci-hub.se/10.1134/S1063782616110063)
20. [Bai, L.; Yan, W.; Li, Z.-F.; Yang, X.; Zhang, B.-W.; Tian, L.-X.; Zhang, F.; Cywinski, G.; Szkudlarek, K.; Skierbiszewski, C., **Surface Leakage Currents in SiN and Al2O3 Passivated AlGaN/GaN High Electron Mobility Transistors.** *Chinese Physics Letters* 2016, ***33*** (6).](https://sci-hub.se/10.1088/0256-307X/33/6/067201)

**2015**

1. [Zholudev, M.; Teppe, F.; Morozov, S.; Orlita, M.; Consejo, C.; Ruffenach, S.; Knap, W.; Gavrilenko, V.; Dvoretskii, S.; Mikhailov, N., **Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure.** *JETP letters* 2015,*100* (12), 790-794.](https://sci-hub.se/10.1134/S0021364014240175)
2. [Watanabe, T.; Kawasaki, T.; Satou, A.; Tombet, S. B.; Suemitsu, T.; Ducournau, G.; Coquillat, D.; Knap, W.; Minamide, H.; Ito, H.; Popov, V. V.; Meziani, Y. M.; Otsuji, T., **Room-temperature zero-bias plasmonic THz detection by asymmetric dual-grating-gate HEMT.** *Terahertz, Rf, Millimeter, And Submillimeter-Wave Technology And Applications* 2015,*9362*, 7.](https://sci-hub.se/10.1117/12.2079184)
3. [Vitiello, M. S.; Viti, L.; Coquillat, D.; Knap, W.; Ercolani, D.; Sorba, L., **One dimensional semiconductor nanostructures: An effective active -material for terahertz detection.** *APL Materials* 2015,*3* (2).](https://sci-hub.se/10.1063/1.4906878)
4. [Viti, L.; Hu, J.; Coquillat, D.; Knap, W.; Tredicucci, A.; Politano, A.; Vitiello, M. S., **Black phosphorus terahertz photodetectors.** *Advanced materials* 2015,*27* (37), 5567-5572.](https://sci-hub.se/10.1002/adma.201502052)
5. [Suszek, J.; Siemion, A.; Bieda, M. S.; Blocki, N.; Coquillat, D.; Cywinski, G.; Czerwinska, E.; Doch, M.; Kowalczyk, A.; Palka, N.; Sobczyk, A.; Zagrajek, P.; Zaremba, M.; Kolodziejczyk, A.; Knap, W.; Sypek, M., **3-D-printed flat optics for THz linear scanners.** *IEEE Transactions on Terahertz Science and Technology* 2015,*5* (2), 314-316.](https://sci-hub.se/10.1109/TTHZ.2015.2398313)
6. [Polischuk, O. V.; Popov, V. V.; Knap, W., **Ultra-broadband near-field antenna for terahertz plasmonic applications.** *Semiconductors* 2015,*49* (1), 104-108.](https://sci-hub.se/10.1134/S1063782615010212)
7. [Orlita, M.; Faugeras, C.; Barra, A.; Martinez, G.; Potemski, M.; Basko, D. M.; Zholudev, M. S.; Teppe, F.; Knap, W.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretskii, S. A.; Neugebauer, P.; Berger, C.; Heer, W. A. D., **Infrared magneto-spectroscopy of two-dimensional and three-dimensional massless fermions : A comparison.** *Journal of Applied Physics* 2015,*117* (11), 1-5.](https://sci-hub.se/10.1063/1.4913828)
8. [Marczewski, J.; Knap, W.; Tomaszewski, D.; Zaborowski, M.; Zagrajek, P., **Silicon junctionless field effect transistors as room temperature terahertz detectors.** *Journal of Applied Physics* 2015,*118* (10).](https://sci-hub.se/10.1063/1.4929967)
9. [Krishtopenko, S. S.; Ikonnikov, A. V.; Orlita, M.; Sadofyev, Y. G.; Goiran, M.; Teppe, F.; Knap, W.; Gavrilenko, V. I., **Effect of electron-electron interaction on cyclotron resonance in high-mobility InAs/AlSb quantum wells.** *Journal of Applied Physics* 2015,*117* (11), 112813-112813.](https://sci-hub.se/10.1063/1.4913927)
10. [Kadykov, A. M.; Teppe, F.; Consejo, C.; Viti, L.; Vitiello, M. S.; Krishtopenko, S. S.; Ruffenach, S.; Morozov, S. V.; Marcinkiewicz, M.; Desrat, W.; Dyakonova, N.; Knap, W.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretsky, S. A., **Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors.** *Applied Physics Letters* 2015,*107* (15), 1-5.](https://sci-hub.se/10.1063/1.4932943)
11. [Grigelionis, I.; Białek, M.; Grynberg, M.; Czapkiewicz, M.; Kolkovskiy, V.; Wiater, M.; Wojciechowski, T.; Wróbel, J.; Wojtowicz, T.; Diakonova, N.; Knap, W.; Łusakowski, J., **Terahertz magneto-spectroscopy of a point contact based on CdTe/CdMgTe quantum well.** *Journal of nanophotonics* 2015,*9* (1), 93082-93088.](https://sci-hub.se/10.1117/1.JNP.9.093082)
12. [Dyakonova, N.; But, D. B.; Coquillat, D.; Knap, W.; Drexler, C.; Olbrich, P.; Karch, J.; Schafberger, M.; Ganichev, S. D.; Ducournau, G.; Gaquiere, C.; Poisson, M. A.; Delage, S.; Cywinski, G.; Skierbiszewski, C., **AlGaN/GaN HEMT's photoresponse to high intensity THz radiation.** *Opto-electronics Review* 2015,*23* (3), 195-199.](https://sci-hub.se/10.1515/oere-2015-0026)
13. [Consejo, C.; Prystawko, P.; Knap, W.; Nowakowska-Siwinska, A.; Perlin, P.; Leszczynski, M., **Mechanism of Hydrogen Sensing by AlGaN/GaN Pt-Gate Field Effect Transistors: Magnetoresistance Studies.** *IEEE Sensors Journal* 2015,*15* (1), 123-127.](https://sci-hub.se/10.1109/JSEN.2014.2340436)
14. [Bovkun, L. S.; Krishtopenko, S. S.; Zholudev, M. S.; Ikonnikov, A. V.; Spirin, K. E.; Dvoretsky, S. A.; Mikhailov, N. N.; Teppe, F.; Knap, W.; Gavrilenko, V. I., **Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells.** *Semiconductors* 2015,*49* (12), 1627-1633.](https://sci-hub.se/10.1134/S1063782615120052)

**2014**

1. [Viti, L.; Coquillat, D.; Ercolani, D.; Sorba, L.; Knap, W.; Vitiello, M. S., **Nanowire Terahertz detectors with a resonant four-leaf-clover-shaped antenna.** *Optics Express* 2014,*22* (8), 8996-8996.](https://sci-hub.se/10.1364/OE.22.008996)
2. [Spirito, D.; Coquillat, D.; De Bonis, S. L.; Lombardo, A.; Bruna, M.; Ferrari, A. C.; Pellegrini, V.; Tredicucci, A.; Knap, W.; Vitiello, M. S., **High performance bilayer-graphene Terahertz detectors.** *Applied Physics Letters* 2014,*104* (6).](https://sci-hub.se/10.1063/1.4864082)
3. [Romeo, L.; Coquillat, D.; Husanu, E.; Ercolani, D.; Tredicucci, A.; Beltram, F.; Sorba, L.; Knap, W.; Vitiello, M. S., **Terahertz photodetectors based on tapered semiconductor nanowires.** *Applied Physics Letters* 2014,*105* (23).](https://sci-hub.se/10.1063/1.4903473)
4. [Penot, A.; Torres, J.; Nouvel, P.; Varani, L.; Teppe, F.; Consejo, C.; Dyakonova, N.; Knap, W.; Cordier, Y.; Chenot, S.,](https://www.lmaleidykla.lt/ojs/index.php/physics/article/view/2848/1676) **[Generation of THz radiation due to 2D-plasma oscillations in interdigitated GaN quantum well structures at room temperature.](https://www.lmaleidykla.lt/ojs/index.php/physics/article/view/2848/1676)***[Lithuanian Journal of Physics](https://www.lmaleidykla.lt/ojs/index.php/physics/article/view/2848/1676)* [2014,](https://www.lmaleidykla.lt/ojs/index.php/physics/article/view/2848/1676)*[54](https://www.lmaleidykla.lt/ojs/index.php/physics/article/view/2848/1676)* [(1).](https://www.lmaleidykla.lt/ojs/index.php/physics/article/view/2848/1676)
5. [Otsuji, T.; Watanabe, T.; Tombet, S. A. B.; Satou, A.; Ryzhii, V.; Popov, V.; Knap, W., **Emission and detection of terahertz radiation using two-dimensional plasmons in semiconductor nanoheterostructures for nondestructive evaluations.** *Optical Engineering* 2014,*53* (3), 031206-031206.](https://sci-hub.se/10.1117/1.OE.53.3.031206)
6. [Orlita, M.; Basko, D. M.; Zholudev, M. S.; Teppe, F.; Knap, W.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretskii, S. A.; Neugebauer, P.; Faugeras, C.; Barra, A. L.; Martinez, G.; Potemski, M., **Observation of three-dimensional massless Kane fermions in a zinc-blende crystal.** *Nature Physics* 2014,*10* (3), 233-238.](https://sci-hub.se/10.1038/nphys2857)
7. [Nagatsuma, T.; Nouvel, P.; Tohmé, L.; Knap, W.; Coquillat, D.; Pénarier, A.; Blin, S.; Lampin, J. F.; Varani, L.; Hisatake, S.; Ducournau, G., **Terahertz wireless communication using GaAs transistors as detectors.** *Electronics Letters* 2014,*50* (4), 323-325.](https://sci-hub.se/10.1049/el.2013.3702)
8. [Kurita, Y.; Ducoumau, G.; Coquillat, D.; Satou, A.; Kobayashi, K.; Tombet, S. B.; Meziani, Y. M.; Popov, V. V.; Knap, W.; Suemitsu, T.; Otsuji, T., **Ultrahigh sensitive sub- Terahertz detection by InP-based asymmetric dual-grating-gate high-electron-mobility transistors and their broadband characteristics.** *Applied Physics Letters* 2014,*104* (25), 0-4.](https://sci-hub.se/10.1063/1.4885499)
9. [Kopyt, P.; Zagrajek, P.; Marczewski, J.; Kucharski, K.; Salski, B.; Lusakowski, J.; Knap, W.; Gwarek, W. K., **Analysis of sub-THz radiation detector built of planar antenna integrated with MOSFET.** *Microelectronics Journal* 2014,*45* (9), 1168-1176.](https://sci-hub.se/10.1016/j.mejo.2014.04.004)
10. [But, D. B.; Drexler, C.; Sakhno, M. V.; Dyakonova, N.; Drachenko, O.; Sizov, F. F.; Gutin, A.; Ganichev, S. D.; Knap, W., **Nonlinear photoresponse of field effect transistors terahertz detectors at high irradiation intensities.** *Journal of Applied Physics* 2014,*115* (16), 164514.](https://sci-hub.se/10.1063/1.4872031)

**2013**

1. [Watanabe, T.; Boubanga-Tombet, S. A.; Tanimoto, Y.; Fateev, D.; Popov, V.; Coquillat, D.; Knap, W.; Meziani, Y. M.; Wang, Y.; Minamide, H.; Ito, H.; Otsuji, T., **InP- and GaAs-Based Plasmonic High-Electron-Mobility Transistors for Room-Temperature Ultrahigh-Sensitive Terahertz Sensing and Imaging.** *IEEE Sensors Journal* 2013,*13* (1), 89-99.](https://sci-hub.se/10.1109/JSEN.2012.2225831)
2. [Rumyantsev, S. L.; Coquillat, D.; Ribeiro, R.; Goiran, M.; Knap, W.; Shur, M. S.; Balandin, A. A.; Levinshtein, M. E., **The effect of a transverse magnetic field on 1/f noise in graphene.** *Applied Physics Letters* 2013,*103* (17), 173114.](https://sci-hub.se/10.1063/1.4826644)
3. [Romeo, L.; Coquillat, D.; Pea, M.; Ercolani, D.; Beltram, F.; Sorba, L.; Knap, W.; Tredicucci, A.; Vitiello, M. S., **Nanowire-based field effect transistors for terahertz detection and imaging systems.** *Nanotechnology* 2013,*24* (21), 214005.](https://sci-hub.se/10.1088/0957-4484/24/21/214005)

1. [Otsuji, T.; Watanabe, T.; Tombet, S. A. B.; Satou, A.; Knap, W. M.; Popov, V. V.; Ryzhii, M.; Ryzhii, V., **Emission and Detection of Terahertz Radiation Using Two-Dimensional Electrons in III–V Semiconductors and Graphene.** *IEEE Transactions on Terahertz Science and Technology* 2013,*3* (1), 63-71.](https://sci-hub.se/10.1109/TTHZ.2012.2235911)
2. [Muraviev, A. V.; Rumyantsev, S. L.; Liu, G.; Balandin, A. A.; Knap, W.; Shur, M. S., **Plasmonic and bolometric terahertz detection by graphene field-effect transistor.** *Applied Physics Letters* 2013,*103* (18).](https://sci-hub.se/10.1063/1.4826139)
3. [Meziani, Y. M.; Garcìa-Garcìa, E.; Velázquez-Pérez, J. E.; Coquillat, D.; Dyakonova, N.; Knap, W.; Grigelionis, I.; Fobelets, K., **Terahertz imaging using strained-Si MODFETs as sensors.** *Solid-State Electronics* 2013,*83*, 113-117.](https://sci-hub.se/10.1016/j.sse.2013.01.030)
4. [Knap, W.; Rumyantsev, S.; Vitiello, M. S.; Coquillat, D.; Blin, S.; Dyakonova, N.; Shur, M.; Teppe, F.; Tredicucci, A.; Nagatsuma, T., **Nanometer size field effect transistors for terahertz detectors.** *Nanotechnology* 2013,*24* (21).](https://sci-hub.se/10.1088/0957-4484/24/21/214002)
5. [Knap, W.; Dyakonov, M. I., **Field effect transistors for terahertz applications.** *Handbook of Terahertz Technology* 2013, 121-155.](https://sci-hub.se/10.1533/9780857096494.1.121)
6. [Kachorovskii, V. Y.; Rumyantsev, S. L.; Knap, W.; Shur, M., **Performance limits for field effect transistors as terahertz detectors.** *Applied Physics Letters* 2013,*102* (22), 223505.](https://sci-hub.se/10.1063/1.4809672)
7. [Grabecki, G.; Wróbel, J.; Czapkiewicz, M.; Cywiński, Ł.; Gierałtowska, S.; Guziewicz, E.; Zholudev, M.; Gavrilenko, V.; Mikhailov, N. N.; Dvoretski, S. A.; Teppe, F.; Knap, W.; Dietl, T., **Nonlocal resistance and its fluctuations in microstructures of band-inverted HgTe/(Hg,Cd)Te quantum wells.** *Physical Review B* 2013,*88* (16).](https://sci-hub.se/10.1103/PhysRevB.88.165309)
8. [Blin, S.; Tohme, L.; Coquillat, D.; Horiguchi, S.; Minamikata, Y.; Hisatake, S.; Nouvel, P.; Cohen, T.; Pénarier, A.; Cano, F.; Varani, L.; Knap, W.; Nagatsuma, T., **Wireless communication at 310 GHz using GaAs high-electron-mobility transistors for detection.** *Journal of Communications and Networks* 2013,*15* (6), 559-568.](https://sci-hub.se/10.1109/JCN.2013.000104)

**2012**

1. [Zholudev, M. S.; Ikonnikov, A. V.; Teppe, F.; Orlita, M.; Maremyanin, K. V.; Spirin, K. E.; Gavrilenko, V. I.; Knap, W.; Dvoretskiy, S. A.; Mihailov, N. N.,](https://sci-hub.se/10.1186/1556-276X-7-534) **[Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields](https://sci-hub.se/10.1186/1556-276X-7-534)***[Nanoscale Research Letters](https://sci-hub.se/10.1186/1556-276X-7-534)* [2012,](https://sci-hub.se/10.1186/1556-276X-7-534)*[7](https://sci-hub.se/10.1186/1556-276X-7-534)* [(1), 534-534.](https://sci-hub.se/10.1186/1556-276X-7-534)
2. [Zholudev, M.; Teppe, F.; Orlita, M.; Consejo, C.; Torres, J.; Dyakonova, N.; Czapkiewicz, M.; Wróbel, J.; Grabecki, G.; Mikhailov, N.; Dvoretskii, S.; Ikonnikov, A.; Spirin, K.; Aleshkin, V.; Gavrilenko, V.; Knap, W.,](https://sci-hub.se/10.1103/PhysRevB.86.205420) **[Magnetospectroscopy of two-dimensional HgTe-based topological insulators around the critical thickness.](https://sci-hub.se/10.1103/PhysRevB.86.205420)***[Physical Review B](https://sci-hub.se/10.1103/PhysRevB.86.205420)* [2012,](https://sci-hub.se/10.1103/PhysRevB.86.205420)*[86](https://sci-hub.se/10.1103/PhysRevB.86.205420)* [(20), 205420.](https://sci-hub.se/10.1103/PhysRevB.86.205420)
3. [Watanabe, T.; Tombet, S. B.; Tanimoto, Y.; Wang, Y.; Minamide, H.; Ito, H.; Fateev, D.; Popov, V.; Coquillat, D.; Knap, W.; Meziani, Y.; Otsuji, T.,](https://sci-hub.se/10.1364/CLEO_SI.2012.CTu2B.8) **[Ultrahigh sensitive plasmonic terahertz detector based on an asymmetric dual-grating gate HEMT structure.](https://sci-hub.se/10.1364/CLEO_SI.2012.CTu2B.8)***[Solid-State Electronics](https://sci-hub.se/10.1364/CLEO_SI.2012.CTu2B.8)* [2012,](https://sci-hub.se/10.1364/CLEO_SI.2012.CTu2B.8)*[78](https://sci-hub.se/10.1364/CLEO_SI.2012.CTu2B.8)*[, 109-114.](https://sci-hub.se/10.1364/CLEO_SI.2012.CTu2B.8)
4. [Vitiello, M. S.; Coquillat, D.; Viti, L.; Ercolani, D.; Teppe, F.; Pitanti, A.; Beltram, F.; Sorba, L.; Knap, W.; Tredicucci, A., **Room-Temperature Terahertz Detectors Based on Semiconductor Nanowire Field-Effect Transistors.** *Nano Letters* 2012,*12* (1), 96-101.](https://sci-hub.se/10.1021/nl2030486)
5. [Vicarelli, L.; Vitiello, M. S.; Coquillat, D.; Lombardo, A.; Ferrari, A. C.; Knap, W.; Polini, M.; Pellegrini, V.; Tredicucci, A., **Graphene field-effect transistors as room-temperature terahertz detectors.** *Nature materials* 2012,*11* (10), 865-871.](https://sci-hub.se/10.1038/NMAT3417)
6. [Pitanti, A.; Coquillat, D.; Ercolani, D.; Sorba, L.; Teppe, F.; Knap, W.; De Simoni, G.; Beltram, F.; Tredicucci, A.; Vitiello, M. S., **Terahetz detection by heterostructed InAs/InSb nanowire based field effect transistors.** *Applied Physics Letters* 2012,*101* (14).](https://sci-hub.se/10.1063/1.4757005)
7. [Moutaouakil, A. E.; Suemitsu, T.; Otsuji, T.; Coquillat, D.; Knap, W., **Nonresonant Detection of Terahertz Radiation in High-Electron-Mobility Transistor Structure Using InAlAs/InGaAs/InP Material Systems at Room Temperature.** *Journal of nanoscience and nanotechnology* 2012,*12* (8), 6737-6740.](https://sci-hub.se/10.1166/jnn.2012.4575)
8. [Klimenko, O. A.; Knap, W.; Iniguez, B.; Coquillat, D.; Mityagin, Y. A.; Teppe, F.; Dyakonova, N.; Videlier, H.; But, D.; Lime, F.; Marczewski, J.; Kucharski, K., **Temperature enhancement of terahertz responsivity of plasma field effect transistors.** *Journal of Applied Physics* 2012,*112* (1), 14506-14506.](file:///C:\Users\ADMIN\AppData\Roaming\Microsoft\Word\10.1063\1.4733465)
9. [Grigelionis, I.; Białek, M.; Grynberg, M.; Czapkiewicz, M.; Kolkovskiy, V.; Wiater, M.; Wojciechowski, T.; Wróbel, J.; Wojtowicz, T.; But, D., **Terahertz Response of a Point Contact Based on CdTe/CdMgTe Quantum Well in Magnetic Field.** *Acta Physica Polonica A* 2012,*122* (6), 1069-1072.](http://przyrbwn.icm.edu.pl/APP/PDF/122/a122z6p28.pdf)
10. [Drexler, C.; Dyakonova, N.; Olbrich, P.; Karch, J.; Schafberger, M.; Karpierz, K.; Mityagin, Y.; Lifshits, M. B.; Teppe, F.; Klimenko, O.; Meziani, Y. M.; Knap, W.; Ganichev, S. D., **Helicity sensitive terahertz radiation detection by field effect transistors.** *Journal of Applied Physics* 2012,*111* (12), 124504-124504.](https://sci-hub.se/10.1063/1.4729043)
11. [But, D.; Dyakonova, N.; Coquillat, D.; Teppe, F.; Knap, W.; Watanabe, T.; Tanimoto, Y.; Tombet, S. B.; Otsuji, T., **THz Double-Grating Gate Transistor Detectors in High Magnetic Fields.** *Acta Physica Polonica A* 2012,*122* (6), 1080-1082.](http://przyrbwn.icm.edu.pl/APP/PDF/122/a122z6p31.pdf)
12. [Blin, S.; Teppe, F.; Tohme, L.; Hisatake, S.; Arakawa, K.; Nouvel, P.; Coquillat, D.; Penarier, A.; Torres, J.; Varani, L.; Knap, W.; Nagatsuma, T., **Plasma-Wave Detectors for Terahertz Wireless Communication.** *IEEE Electron Device Letters* 2012,*33* (10), 1354-1356.](https://sci-hub.se/10.1109/LED.2012.2210022)

**2011**

1. [Vitiello, M. S.; Coquillat, D.; Viti, L.; Ercolani, D.; Teppe, F.; Pitanti, A.; Beltram, F.; Sorba, L.; Knap, W.; Tredicucci, A., **Room-temperature terahertz detectors based on semiconductor nanowire field-effect transistors.** *Nano letters* 2011,*12* (1), 96-101.](https://sci-hub.se/10.1021/nl2030486)
2. [Videlier, H.; Dyakonova, N.; Teppe, F.; Consejo, C.; Chenaud, B.; Knap, W.; Lusakowski, J.; Tomaszewski, D.; Marczewski, J.; Grabiec, P., **Terahertz Photovoltaic Response of Si-MOSFETs: Spin Related Effect.** *Acta Physica Polonica A* 2011,*120* (5), 927-929.](http://przyrbwn.icm.edu.pl/APP/PDF/120/a120z5p31.pdf)
3. [Torres, J.; Varani, L.; Teppe, F.; Knap, W.; Boubanga-Tombet, S.; Otsuji, T.; Shiktorov, P.; Starikov, E.; Gružinskis, V., **Investigation of 2D plasma resonances in hemts by using electro-optical sampling technique.** *Lithuanian Journal of Physics* 2011,*51* (4), 324-329.](https://pdfs.semanticscholar.org/4839/0d429525093c0a33d5379e1c132b4129932c.pdf)
4. [Schuster, F.; Knap, W.; Nguyen, V., **Terahertz imaging achieved with low-cost CMOS detectors.** *Laser Focus World* 2011,*47* (7), 37-+.](https://www.laserfocusworld.com/detectors-imaging/article/16562753/cmos-detectors-terahertz-imaging-achieved-with-lowcost-cmos-detectors)
5. [Schuster, F.; Coquillat, D.; Videlier, H.; Sakowicz, M.; Teppe, F.; Dussopt, L.; Giffard, B.; Skotnicki, T.; Knap, W., **Broadband terahertz imaging with highly sensitive silicon CMOS detectors.** *Optics Express* 2011,*19* (8), 7827-7832.](https://sci-hub.se/10.1364/OE.19.007827)
6. [Sakowicz, M.; Lifshits, M. B.; Klimenko, O. A.; Schuster, F.; Coquillat, D.; Teppe, F.; Knap, W., **Terahertz responsivity of field effect transistors versus their static channel conductivity and loading effects.** *Journal of Applied Physics* 2011,*110* (5), 054512.](https://sci-hub.se/10.1063/1.3632058)
7. [Popov, V. V.; Fateev, D. V.; Otsuji, T.; Meziani, Y. M.; Coquillat, D.; Knap, W., **Plasmonic terahertz detection by a double-grating-gate field-effect transistor structure with an asymmetric unit cell.** *Applied Physics Letters* 2011,*99* (24), 243504.](https://sci-hub.se/10.1063/1.3670321)
8. [Otsuji, T.; Watanabe, T.; El Moutaouakil, A.; Karasawa, H.; Komori, T.; Satou, A.; Suemitsu, T.; Suemitsu, M.; Sano, E.; Knap, W.; Ryzhii, V., **Emission of Terahertz Radiation from Two-Dimensional Electron Systems in Semiconductor Nano- and Hetero-Structures.** *Journal of Infrared, Millimeter, and Terahertz Waves* 2011,*32* (5), 629-645.](https://sci-hub.se/10.1007/s10762-010-9714-0)
9. [Nogajewski, K.; Łusakowski, J.; Knap, W.; Popov, V. V.; Teppe, F.; Rumyantsev, S. L.; Shur, M. S., **Localized and collective magnetoplasmon excitations in AlGaN/GaN-based grating-gate terahertz modulators.** *Applied Physics Letters* 2011,*99* (21), 213501.](https://sci-hub.se/10.1063/1.3663626)
10. [Knap, W.; Nadar, S.; Videlier, H.; Boubanga-Tombet, S.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Karpierz, K.; Łusakowski, J.; Sakowicz, M.; Kasalynas, I.; Seliuta, D.; Valusis, G.; Otsuji, T.; Meziani, Y.; El Fatimy, A.; Vandenbrouk, S.; Madjour, K.; Théron, D.; Gaquière, C., **Field Effect Transistors for Terahertz Detection and Emission.** *Journal of Infrared, Millimeter, and Terahertz Waves* 2011,*32* (5), 618-628.](https://sci-hub.se/10.1007/s10762-010-9647-7)
11. [Ikonnikov, A. V.; Zholudev, M. S.; Spirin, K. E.; Lastovkin, A. A.; Maremyanin, K. V.; Aleshkin, V. Y.; Gavrilenko, V. I.; Drachenko, O.; Helm, M.; Wosnitza, J.; Goiran, M.; Mikhailov, N. N.; Dvoretskii, S. A.; Teppe, F.; Diakonova, N.; Consejo, C.; Chenaud, B.; Knap, W., **Cyclotron resonance and interband optical transitions in HgTe/CdTe(0 1 3) quantum well heterostructures.** *Semiconductor Science and Technology* 2011,*26* (12), 125011.](https://sci-hub.se/10.1088/0268-1242/26/12/125011)
12. [Han, R.; Zhang, Y.; Coquillat, D.; Videlier, H.; Knap, W.; Brown, E.; K. K, O., **A 280-GHz Schottky Diode Detector in 130-nm Digital CMOS.** *IEEE Journal of Solid-State Circuits* 2011,*46* (11), 2602-2612.](https://sci-hub.se/10.1109/JSSC.2011.2165234)
13. [Dyakonova, N.; El Fatimy, A.; Meziani, Y.; Coquillat, D.; Knap, W.; Teppe, F.; Buzatu, P.; Diforte-Poisson, M. A.; Dua, C.; Piotrowicz, S.; Morvan, E.; Delage, S., **THz Emission Related to Hot Plasmons and Plasma Wave Instability in Field Effect Transistors.** *Acta Physica Polonica A* 2011,*120* (5), 924-926.](file:///C:\Users\ADMIN\AppData\Roaming\Microsoft\Word\10.12693\APhysPolA.120.92)

**2010**

1. [Seok, E.; Shim, D.; Mao, C.; Han, R.; Sankaran, S.; Cao, C.; Knap, W.; K. K, O., **Progress and Challenges Towards Terahertz CMOS Integrated Circuits.** *IEEE JOURNAL OF SOLID-STATE CIRCUITS* 2010,*45* (8), 1554-1564.](https://sci-hub.se/10.1109/JSSC.2010.2049793)
2. [Otsuji, T.; Watanabe, T.; El Moutaouakil, A.; Karasawa, H.; Komori, T.; Satou, A.; Suemitsu, T.; Suemitsu, M.; Sano, E.; Knap, W.; Ryzhii, V., **Emission of Terahertz Radiation from Two-Dimensional Electron Systems in Semiconductor Nano- and Hetero-Structures.** *Journal of Infrared, Millimeter, and Terahertz Waves* 2010,*32* (5), 629-645.](https://sci-hub.se/10.1007/s10762-010-9714-0)
3. [Nadar, S.; Videlier, H.; Coquillat, D.; Teppe, F.; Sakowicz, M.; Dyakonova, N.; Knap, W.; Seliuta, D.; Kašalynas, I.; Valušis, G., **Room temperature imaging at 1.63 and 2.54 THz with field effect transistor detectors.** *Journal of Applied Physics* 2010,*108* (5), 54508-54508.](https://sci-hub.se/10.1063/1.3463414)
4. [Kosarev, A.; Rumyantsev, S.; Moreno, M.; Torres, A.; Boubanga, S.; Knap, W., **Si*x*Ge*y*:H-based micro-bolometers studied in the terahertz frequency range.** *Solid-State Electronics* 2010,*54* (4), 417-419.](https://sci-hub.se/10.1016/j.sse.2009.12.032)
5. [Knap, W.; Videlier, H.; Nadar, S.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Bialek, M.; Grynberg, M.; Karpierz, K.; Lusakowski, J.; Nogajewski, K.; Seliuta, D.; Kašalynas, I.; Valušis, G., **Field effect transistors for terahertz detection - silicon versus III–V material issue.** *Opto-Electronics Review* 2010,*18* (3), 225-230.](https://sci-hub.se/10.2478/s11772-010-1018-7)
6. [Knap, W.; Nadar, S.; Videlier, H.; Boubanga-Tombet, S.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Karpierz, K.; Łusakowski, J.; Sakowicz, M.; Kasalynas, I.; Seliuta, D.; Valusis, G.; Otsuji, T.; Meziani, Y.; El Fatimy, A.; Vandenbrouk, S.; Madjour, K.; Théron, D.; Gaquière, C., **Field Effect Transistors for Terahertz Detection and Emission.** *Journal of Infrared, Millimeter, and Terahertz Waves* 2010,*32* (5), 618-628.](https://sci-hub.se/10.1007/s10762-010-9647-7)
7. [Knap, W.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Klimenko, O.; Videlier, H.; Nadar, S.; Łusakowski, J.; Valusis, G.; Schuster, F.; Giffard, B.; Skotnicki, T.; Gaquière, C.; El Fatimy, A., **Plasma excitations in field effect transistors for terahertz detection and emission.** *Comptes Rendus Physique* 2010,*11* (7), 433-443.](https://sci-hub.se/10.1016/j.crhy.2010.06.010)
8. [Klimenko, O. A.; Mityagin, Y. A.; Videlier, H.; Teppe, F.; Dyakonova, N. V.; Consejo, C.; Bollaert, S.; Murzin, V. N.; Knap, W., **Terahertz response of InGaAs field effect transistors in quantizing magnetic fields.** *Applied Physics Letters* 2010,*97* (2), 22111-22111.](https://sci-hub.se/10.1063/1.3462072)
9. [Ikonnikov, A.; Krishtopenko, S.; Gavrilenko, V.; Sadofyev, Y.; Vasilyev, Y.; Orlita, M.; Knap, W., **Splitting of Cyclotron Resonance Line in InAs/AlSb QW Heterostructures in High Magnetic Fields: Effects of Electron-Electron and Electron-Phonon Interaction.** *Journal of Low Temperature Physics* 2010,*159* (1), 197-202.](https://sci-hub.se/10.1007/s10909-009-0151-1)
10. [El Fatimy, A.; Dyakonova, N.; Meziani, Y.; Otsuji, T.; Knap, W.; Vandenbrouk, S.; Madjour, K.; Théron, D.; Gaquiere, C.; Poisson, M. A.; Delage, S.; Prystawko, P.; Skierbiszewski, C., **AlGaN/GaN high electron mobility transistors as a voltage-tunable room temperature terahertz sources.** *Journal of Applied Physics* 2010,*107* (2), 24504-24504.](https://sci-hub.se/10.1063/1.3291101)
11. [Coutaz, J.; Ito, H.; Komiyama, S.; Knap, W., **Terahertz electronic and optoelectronic components and systems Foreword** *COMPTES RENDUS PHYSIQUE* 2010,*11* (7-8), 411-412.](https://sci-hub.se/10.1016/j.crhy.2010.09.003)
12. [Coquillat, D.; Nadar, S.; Teppe, F.; Dyakonova, N.; Boubanga-Tombet, S.; Knap, W.; Nishimura, T.; Otsuji, T.; Meziani, Y. M.; Tsymbalov, G. M.; Popov, V. V., **Room temperature detection of sub-terahertz radiation in double-grating-gate transistors.** *Optics Express* 2010,*18* (6), 6024-6032.](https://sci-hub.se/10.1364/OE.18.006024)
13. [Boubanga-Tombet, S.; Teppe, F.; Torres, J.; El Moutaouakil, A.; Coquillat, D.; Dyakonova, N.; Consejo, C.; Arcade, P.; Nouvel, P.; Marinchio, H.; Laurent, T.; Palermo, C.; Penarier, A.; Otsuji, T.; Varani, L.; Knap, W., **Room temperature coherent and voltage tunable terahertz emission from nanometer-sized field effect transistors.** *Applied Physics Letters* 2010,*97* (26), 262108-262108.](https://sci-hub.se/10.1063/1.3529464)

**2009**

1. [Pardo, J. F. M.; Reggiani, L.; Pousset, J.; Varani, L.; Palermo, C.; Knap, W.; Mateos, J.; González, T.; Perez, S., **A** **Monte Carlo investigation of plasmonic noise in nanometric n-In 0.53 Ga 0.47 As channels.** *Journal of Statistical Mechanics: Theory and Experiment* 2009,*2009* (01), P01040-P01040.](https://sci-hub.se/10.1088/1742-5468/2009/01/P01040)
2. [Otsuji, T. N.; Nobuhiro, M.; Irina, K.; Tetsuya, S.; Wojtek, K.; Taiichi, **Analysis of Fringing Effect on Resonant Plasma Frequency in Plasma Wave Devices.** *Japanese Journal of Applied Physics* 2009,*48* (4S), 04C096-04C096.](https://iopscience.iop.org/article/10.1143/JJAP.48.04C096)
3. [Nadar, S.; Coquillat, D.; Sakowicz, M.; Videlier, H.; Teppe, F.; Dyakonova, N.; Knap, W.; Peiris, J. M.; Lyonnet, J.; Seliuta, D., **Terahertz imaging using high electron mobility transistors as plasma wave detectors.** *Physica Status Solidi C-Current Topics in Solid State Physics* 2009,*6* (12), 2855-2857.](https://sci-hub.se/10.1002/pssc.200982532)
4. [Meziani, Y. M.; Nishimura, T.; Handa, H.; Tsuda, H.; Suemitsu, T.; Knap, W.; Otsuji, T.; Sano, E.; Tsymbalov, G. M.; Popov, V. V., **Efficiency enhancement of emission of terahertz radiation by optical excitation from dual grating gate HEMT.** *Journal of Nanophotonics,* 2009,*3*, 31911-31980.](https://sci-hub.se/10.1117/1.3266497)
5. Knap, W.; Valušis, G.; Łusakowski, J.; Coquillat, D.; Teppe, F.; Dyakonova, N.; Nadar, S.; Karpierz, K.; Bialek, M.; Seliuta, D., **Field effect transistors for terahertz imaging.** *physica status solidi (c)* 2009,*6* (12), 2828-2833.
6. [Knap, W.; Dyakonov, M.; Coquillat, D.; Teppe, F.; Dyakonova, N.; Łusakowski, J.; Karpierz, K.; Sakowicz, M.; Valusis, G.; Seliuta, D.; Kasalynas, I.; El Fatimy, A.; Meziani, Y. M.; Otsuji, T., **Field Effect Transistors for Terahertz Detection: Physics and First Imaging Applications.** *Journal of Infrared, Millimeter, and Terahertz Waves* 2009,*30* (12), 1319-1337.](https://sci-hub.se/10.1002/pssc.200982562)
7. [El Fatimy, A.; Delagnes, J. C.; Younus, A.; Nguema, E.; Teppe, F.; Knap, W.; Abraham, E.; Mounaix, P., **Plasma wave field effect transistor as a resonant detector for 1 terahertz imaging applications.** *Optics Communications* 2009,*282* (15), 3055-3058.](https://sci-hub.se/10.1016/j.optcom.2009.04.054)
8. [Caumes, J. P.; Chassagne, B.; Coquillat, D.; Teppe, F.; Knap, W., **Focal-plane micro-bolometer arrays for 0.5 THz spatial room-temperature imaging.** *Electronics Letters* 2009,*45* (1), 34-35.](https://sci-hub.se/10.1049/el:20092943)
9. [Boubanga‐Tombet, S.; Teppe, F.; Dyakonova, N.; Coquillat, D.; Knap, W.; Karpierz, K.; Łusakowski, J.; Grynberg, M.; Dyakonov, M. I., **Influence of Shubnikov de Haas and cyclotron resonance effect on terahertz detection by field effect transistors.** *physica status solidi (c)* 2009,*6* (12), 2858-2860.](https://sci-hub.se/10.1002/pssc.200982564)
10. [Boubanga-Tombet, S.; Sakowicz, M.; Coquillat, D.; Teppe, F.; Knap, W.; Dyakonov, M. I.; Karpierz, K.; Łusakowski, J.; Grynberg, M., **Terahertz radiation detection by field effect transistor in magnetic field.** *Applied Physics Letters* 2009,*95* (7), 72106-72106.](https://sci-hub.se/10.1063/1.3207886)
11. [Boubanga-Tombet, S.; Nogajewski, K.; Teppe, F.; Knap, W.; Karpierz, K.; Lusakowski, J.; Grynberg, M.; Dyakonov, M., **High Magnetic Field Effects on Plasma Wave THz Detection in Field-Effect Transistors.** *Acta Physica Polonica A* 2009,*116* (5), 939-940.](http://przyrbwn.icm.edu.pl/APP/PDF/116/a116z556.pdf)
12. [Antonov, A. V.; Gavrilenko, V. I.; Maremyanin, K. V.; Morozov, S. V.; Teppe, F.; Knap, W., **Resonance detection of terahertz radiation in submicrometer field-effect GaAs/AlGaAs transistors with two-dimensional electron gas.** *Semiconductors* 2009,*43* (4), 528-531.](https://sci-hub.se/10.1134/S106378260904023X)

**2008**

1. [Teppe, F.; Fatimy, A. E.; Boubanga, S.; Seliuta, D.; Valusis, G.; Chenaud, B.; Knap, W., **Terahertz resonant detection by plasma waves in nanometric transistors.** *Acta Physica Polonica-Series A General Physics* 2008,*113* (3), 815-820.](http://przyrbwn.icm.edu.pl/APP/PDF/113/a113z308.pdf)
2. [Shchepetov, A.; Gardès, C.; Roelens, Y.; Cappy, A.; Bollaert, S.; Boubanga-Tombet, S.; Teppe, F.; Coquillat, D.; Nadar, S.; Dyakonova, N.; Videlier, H.; Knap, W.; Seliuta, D.; Vadoklis, R.; Valušis, G., **Oblique modes effect on terahertz plasma wave resonant detection in InGaAs∕InAlAs multichannel transistors.** *Applied Physics Letters* 2008,*92* (24), 242105-242105.](https://sci-hub.se/10.1063/1.2945286)
3. [Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Knap, W.; Grynberg, M.; Köhler, K.; Valusis, G.; Gołaszewska, K.; Kamińska, E.; Piotrowska, A., **Terahertz Detection by the Entire Channel of High Electron Mobility Transistors.** *Acta Physica Polonica A* 2008,*114* (5), 1343-1348.](http://przyrbwn.icm.edu.pl/APP/PDF/114/a114z551.pdf)
4. [Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Grynberg, M.; Knap, W.; Köhler, K.; Valušis, G.; Gołaszewska, K.; Kamińska, E.; Piotrowska, A., **Terahertz detection by two dimensional plasma field effect transistors in quantizing magnetic fields.** *Applied Physics Letters* 2008,*92* (20), 203509-203509.](https://sci-hub.se/10.1063/1.2930682)
5. [Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Grynberg, M.; Knap, W.; Gwarek, W., **Polarization sensitive detection of 100 GHz radiation by high mobility field-effect transistors.** *Journal of Applied Physics* 2008,*104* (2), 24519-24519.](https://sci-hub.se/10.1063/1.2957065)
6. [Popov, V. V.; Polischuk, O. V.; Knap, W.; El Fatimy, A., **Broadening of the plasmon resonance due to plasmon-plasmon intermode scattering in terahertz high-electron-mobility transistors.** *Applied Physics Letters* 2008,*93* (26), 263503-263503.](https://sci-hub.se/10.1063/1.3055610)
7. [Popov, T. O.; Meziani, Y. M.; Nishimura, T.; Suemitsu, T.; Knap, W.; Sano, E.; Asano, T.; V, V., **Emission of terahertz radiation from dual grating gate plasmon-resonant emitters fabricated with InGaP/InGaAs/GaAs material systems** *Journal of Physics: Condensed Matter* 2008,*20* (38), 384206-384206.](https://sci-hub.se/10.1088/0953-8984/20/38/384206)
8. [Millithaler, J. F.; Reggiani, L.; Pousset, J.; Varani, L.; Palermo, C.; Knap, W.; Mateos, J.; González, T.; Perez, S.; Pardo, D., **Monte Carlo investigation of terahertz plasma oscillations in ultrathin layers of n-type In0.53Ga0.47As.** *Applied Physics Letters* 2008,*92* (4), 42113-42113.](https://sci-hub.se/10.1063/1.2837183)
9. [Meziani, Y. M.; Handa, H.; Knap, W.; Otsuji, T.; Sano, E.; Popov, V. V.; Tsymbalov, G. M.; Coquillat, D.; Teppe, F., **Room temperature terahertz emission from grating coupled two-dimensional plasmons.** *Applied Physics Letters* 2008,*92* (20), 201108-201108.](https://sci-hub.se/10.1063/1.2919097)
10. [Łusakowski, W. K.; Teppe, F.; Dyakonova, N.; Coquillat, D., **Plasma wave oscillations in nanometer field effect transistors for terahertz detection and emission.** *Journal of Physics: Condensed Matter* 2008,*20* (38), 384205-384205.](https://sci-hub.se/10.1088/0953-8984/20/38/384205)
11. [Lisauskas, A.; Spiegel, W. V.; Boubanga-Tombet, S.; Fatimy, A. E.; Coquillat, D.; Teppe, F.; Dyakonova, N.; Knap, W.; Roskos, H. G., **Terahertz imaging with GaAS field-effect transistors.** *Electronics Letters* 2008,*44* (6), 408-409.](https://sci-hub.se/10.1049/el:20080172)
12. [Boubanga-Tombet, S.; Teppe, F.; Coquillat, D.; Nadar, S.; Dyakonova, N.; Videlier, H.; Knap, W.; Shchepetov, A.; Gardès, C.; Roelens, Y.; Bollaert, S.; Seliuta, D.; Vadoklis, R.; Valušis, G., **Current driven resonant plasma wave detection of terahertz radiation: Toward the Dyakonov–Shur instability.** *Applied Physics Letters* 2008,*92* (21), 212101-212101.](https://sci-hub.se/10.1063/1.2936077)

**2007**

1. [Vainshtein, S.; Kostamovaara, J.; Yuferev, V.; Knap, W.; Fatimy, A.; Diakonova, N., **Terahertz Emission from Collapsing Field Domains during Switching of a Gallium Arsenide Bipolar Transistor.** *Physical Review Letters* 2007,*99* (17), 176601-176601.](https://sci-hub.se/10.1103/PhysRevLett.99.176601)
2. [Tauk, R.; Tiberj, A.; Lorenzini, P.; Bougrioua, Z.; Azize, M.; Sakowicz, M.; Karpierz, K.; Knap, W., **Magnetotransport characterization of AlGaN/GaN interfaces.** *physica status solidi (a)* 2007,*204* (2), 586-590.](https://sci-hub.se/10.1002/pssa.200622330)
3. [Tauk, R.; Łusakowski, J.; Knap, W.; Tiberj, A.; Bougrioua, Z.; Azize, M.; Lorenzini, P.; Sakowicz, M.; Karpierz, K.; Fenouillet-Beranger, C.; Cassé, M.; Gallon, C.; Boeuf, F.; Skotnicki, T., **Low electron mobility of field-effect transistor determined by modulated magnetoresistance.** *Journal of Applied Physics* 2007,*102* (10), 103701-103701.](https://sci-hub.se/10.1063/1.2815610)
4. [Siekacz, M.; Dybko, K.; Maude, D.; Potemski, M.; Knap, W.; Skierbiszewski, C., **Electron-Electron Interaction Effects in Quantum Hall Regime of GaN/AlGaN Heterostructures.** *Acta Physica Polonica-Series A General Physics* 2007,*112* (2), 269-274.](http://przyrbwn.icm.edu.pl/APP/PDF/112/a112z223.pdf)
5. [Łusakowski, J.; Martínez, M. J. M.; Rengel, R.; González, T.; Tauk, R.; Meziani, Y. M.; Knap, W.; Boeuf, F.; Skotnicki, T., **Quasiballistic transport in nanometer Si metal-oxide-semiconductor field-effect transistors: Experimental and Monte Carlo analysis.** *Journal of Applied Physics* 2007,*101* (11), 114511-114511.](https://sci-hub.se/10.1063/1.2739307)
6. [Levinshtein, M. E.; Rumyantsev, S. L.; Tauk, R.; Boubanga, S.; Dyakonova, N.; Knap, W.; Shchepetov, A.; Bollaert, S.; Rollens, Y.; Shur, M. S., **Low frequency noise in InAlAs/InGaAs modulation doped field effect transistors with 50-nm gate length.** *Journal of Applied Physics* 2007,*102* (6), 64506-64506.](https://sci-hub.se/10.1063/1.2781087)
7. [Knap, W.; El Fatimy, A.; Torres, J.; Teppe, F.; Orlov, M.; Gavrilenko, V., **Plasma wave resonant detection of terahertz radiations by nanometric transistors.** *Low Temperature Physics* 2007,*33* (2), 291-294.](https://sci-hub.se/10.1063/1.2719970)
8. [Gavrilenko, V. I.; Demidov, E. V.; Marem’yanin, K. V.; Morozov, S. V.; Knap, W.; Lusakowski, J., **Electron transport and detection of terahertz radiation in a GaN/AlGaN submicrometer field-effect transistor.** *Semiconductors* 2007,*41* (2), 232-234.](https://sci-hub.se/10.1134/S1063782607020224)

**2006**

1. [Veksler, D.; Teppe, F.; Dmitriev, A. P.; Kachorovskii, V. Y.; Knap, W.; Shur, M. S., **Detection of terahertz radiation in gated two-dimensional structures governed by dc current.** *Physical Review B* 2006,*73* (12), 125328-125328.](https://sci-hub.se/10.1103/PhysRevB.73.125328)
2. [Teppe, F.; Orlov, M.; El Fatimy, A.; Tiberj, A.; Knap, W.; Torres, J.; Gavrilenko, V.; Shchepetov, A.; Roelens, Y.; Bollaert, S., **Room temperature tunable detection of subterahertz radiation by plasma waves in nanometer InGaAs transistors.** *Applied Physics Letters* 2006,*89* (22), 222109-222109.](https://sci-hub.se/10.1063/1.2392999)
3. [Tauk, R.; Teppe, F.; Boubanga, S.; Coquillat, D.; Knap, W.; Meziani, Y. M.; Gallon, C.; Boeuf, F.; Skotnicki, T.; Fenouillet-Beranger, C.; Maude, D. K.; Rumyantsev, S.; Shur, M. S., **Plasma wave detection of terahertz radiation by silicon field effects transistors: Responsivity and noise equivalent power.** *Applied Physics Letters* 2006,*89* (25), 253511-253511.](https://sci-hub.se/10.1063/1.2410215)
4. [Sakowicz, M.; Tauk, R.; Łusakowski, J.; Tiberj, A.; Knap, W.; Bougrioua, Z.; Azize, M.; Lorenzini, P.; Karpierz, K.; Grynberg, M., **Low temperature electron mobility and concentration under the gate of AlGaN∕GaN field effect transistors.** *Journal of Applied Physics* 2006,*100* (11), 113726-113726.](https://sci-hub.se/10.1063/1.2353786)
5. [Ryzhii, V.; Satou, A.; Knap, W.; Shur, M. S., **Plasma oscillations in high-electron-mobility transistors with recessed gate.** *Journal of Applied Physics* 2006,*99* (8), 84507-84507.](https://sci-hub.se/10.1063/1.2191628)
6. [Meziani, Y. M.; Dyakonova, N.; Knap, W.; Seliuta, D.; Sirmulis, E.; Devenson, J.; Valusis, G.; Boeuf, F.; Skotnicki, T., **Non resonant response to terahertz radiation by submicron CMOS transistors.** *IEICE transactions on electronics* 2006,*89* (7), 993-998.](https://www.researchgate.net/profile/Edmundas_Sirmulis/publication/220241517_Non_Resonant_Response_to_Terahertz_Radiation_by_Submicron_CMOS_Transistors/links/09e415097b5e2b4192000000.pdf)
7. [Łusakowski, J.; Knap, W.; Meziani, Y.; Cesso, J. P.; El Fatimy, A.; Tauk, R.; Dyakonova, N.; Ghibaudo, G.; Boeuf, F.; Skotnicki, T., **Electron mobility in quasi-ballistic Si MOSFETs.** *Solid-State Electronics* 2006,*50* (4), 632-636.](https://sci-hub.se/10.1016/j.sse.2006.03.017)
8. [Knap, W.; Teppe, F.; Dyakonova, N.; El Fatimy, A., **Terahertz emission and detection by plasma waves in nanometer size field effect transistors.** *IEICE transactions on electronics* 2006,*89* (7), 926-930.](https://www.researchgate.net/profile/A_El_Fatimy/publication/220242500_Terahertz_Emission_and_Detection_by_Plasma_Waves_in_Nanometer_Size_Field_Effect_Transistors/links/004635318a9d17e23b000000.pdf)
9. [Inushima, T.; Kato, N.; Maude, D. K.; Lu, H.; Schaff, W. J.; Tauk, R.; Meziani, Y.; Ruffenack, S.; Briot, O.; Knap, W., **Superconductivity of InN with a well defined Fermi surface.** *physica status solidi (b)* 2006,*243* (7), 1679-1686.](https://sci-hub.se/10.1002/pssb.200565419)
10. [El Fatimy, A.; Tombet, S. B.; Teppe, F.; Knap, W.; Veksler, D. B.; Rumyantsev, S.; Shur, M. S.; Pala, N.; Gaska, R.; Fareed, Q., **Terahertz detection by GaN/AlGaN transistors.** *Electronics Letters* 2006,*42* (23), 1342-1344.](https://www.researchgate.net/publication/3389384_Terahertz_detection_by_GaNAlGaN_transistors)
11. [El Fatimy, A.; Teppe, F.; Dyakonova, N.; Knap, W.; Seliuta, D.; Valušis, G.; Shchepetov, A.; Roelens, Y.; Bollaert, S.; Cappy, A.; Rumyantsev, S., **Resonant and voltage-tunable terahertz detection in InGaAs∕InP nanometer transistors.** *Applied Physics Letters* 2006,*89* (13), 131926-131926.](https://sci-hub.se/10.1063/1.2358816)
12. [Dyakonova, N.; El Fatimy, A.; Łusakowski, J.; Knap, W.; Dyakonov, M. I.; Poisson, M. A.; Morvan, E.; Bollaert, S.; Shchepetov, A.; Roelens, Y., **Room-temperature terahertz emission from nanometer field-effect transistors.** *Applied Physics Letters* 2006,*88* (14), 141906.](https://sci-hub.se/10.1063/1.2191421)

**2005**

1. [Teppe, F.; Veksler, D.; Kachorovski, V. Y.; Dmitriev, A. P.; Xie, X.; Zhang, X. C.; Rumyantsev, S.; Knap, W.; Shur, M. S., **Plasma wave resonant detection of femtosecond pulsed terahertz radiation by a nanometer field-effect transistor.** *Applied Physics Letters* 2005,*87* (2), 22102-22102.](https://sci-hub.se/10.1063/1.1952578)
2. [Teppe, F.; Knap, W.; Veksler, D.; Shur, M. S.; Dmitriev, A. P.; Kachorovskii, V. Y.; Rumyantsev, S., **Room-temperature plasma waves resonant detection of sub-terahertz radiation by nanometer field-effect transistor.** *Applied Physics Letters* 2005,*87* (5), 52107-52107.](https://sci-hub.se/10.1063/1.2005394)
3. [Skierbiszewski, C.; Dybko, K.; Knap, W.; Siekacz, M.; Krupczyński, W.; Nowak, G.; Boćkowski, M.; Łusakowski, J.; Wasilewski, Z. R.; Maude, D.; Suski, T.; Porowski, S., **High mobility two-dimensional electron gas in AlGaN∕GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy.** *Applied Physics Letters* 2005,*86* (10), 102106-102106.](https://sci-hub.se/10.1063/1.1873056)
4. [Popov, V. V.; Tsymbalov, G. M.; Shur, M. S.; Knap, W., **The resonant terahertz response of a slot diode with a two-dimensional electron channel.** *Semiconductors* 2005,*39* (1), 142-146.](https://sci-hub.se/10.1134/1.1852665)
5. [Meziani, Y. M.; Maleyre, B.; Sadowski, M. L.; Ruffenach, S.; Briot, O.; Knap, W., **Terahertz investigation of high quality indium nitride epitaxial layers.** *physica status solidi (a)* 2005,*202* (4), 590-592.](https://sci-hub.se/10.1002/pssa.200460434)
6. [Łusakowski, J.; Teppe, F.; Dyakonova, N.; Meziani, Y. M.; Knap, W.; Parenty, T.; Bollaert, S.; Cappy, A.; Popov, V.; Shur, M. S., **Terahertz generation by plasma waves in nanometer gate high electron mobility transistors.** *physica status solidi (a)* 2005,*202* (4), 656-659.](https://sci-hub.se/10.1002/pssa.200460468)
7. [Łusakowski, J.; Knap, W.; Meziani, Y.; Cesso, J. P.; Fatimy, A. E.; Tauk, R.; Dyakonova, N.; Ghibaudo, G.; Boeuf, F.; Skotnicki, T., **Ballistic and pocket limitations of mobility in nanometer Si metal-oxide semiconductor field-effect transistors.** *Applied Physics Letters* 2005,*87* (5), 53507-53507.](https://sci-hub.se/10.1063/1.1993747)
8. [Lusakowski, J.; Knap, W.; Dyakonova, N.; Varani, L.; Mateos, J.; Gonzalez, T.; Roelens, Y.; Bollaert, S.; Cappy, A.; Karpierz, K., **Voltage tuneable terahertz emission from a ballistic nanometer InGaAs∕InAlAs transistor.** *Journal of Applied Physics* 2005,*97* (6), 64307-64307.](https://sci-hub.se/10.1063/1.1861140)
9. [Lorenzini, P.; Bougrioua, Z.; Tiberj, A.; Tauk, R.; Azize, M.; Sakowicz, M.; Karpierz, K.; Knap, W., **Quantum and transport lifetimes of two-dimensional electrons gas in AlGaN∕GaN heterostructures.** *Applied Physics Letters* 2005,*87* (23), 232107-232107.](https://sci-hub.se/10.1063/1.2140880)
10. [Knap, W.; Skierbiszewski, C.; Dybko, K.; Łusakowski, J.; Siekacz, M.; Grzegory, I.; Porowski, S., **Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures.** *Journal of Crystal Growth* 2005,*281* (1), 194-201.](https://sci-hub.se/10.1016/j.jcrysgro.2005.03.025)
11. [Knap, W; Lusakowski, J; Teppe, F; Dyakonova, N; Meziani, Y, **Terahertz generation and detection by plasma waves in nanometer gate high electron mobility transistors.** *Acta Physica Polonica A* 2005,107(1), 82-91.](http://przyrbwn.icm.edu.pl/APP/PDF/107/a107z109.pdf)
12. [Dyakonova, N.; Teppe, F.; Łusakowski, J.; Knap, W.; Levinshtein, M.; Dmitriev, A. P.; Shur, M. S.; Bollaert, S.; Cappy, A., **Magnetic field effect on the terahertz emission from nanometer InGaAs/AlInAs high electron mobility transistors.** *Journal of Applied Physics* 2005,*97* (11), 114313-114313.](https://sci-hub.se/10.1063/1.1921339)
13. [Dyakonova, N.; Rumyantsev, S. L.; Shur, M. S.; Meziani, Y.; Pascal, F.; Hoffmann, A.; Fareed, Q.; Hu, X.; Bilenko, Y.; Gaska, R., **High magnetic field studies of 1/f noise in GaN/AlGaN heterostructure field effect transistors.** *physica status solidi (a)* 2005,*202* (4), 677-679.](https://sci-hub.se/10.1002/pssa.200460472)

**2004**

1. [Shur, W. K.; Fal’ko, V. I.; Frayssinet, E.; Lorenzini, P.; Grandjean, N.; Maude, D.; Karczewski, G.; Brandt, B. L.; Łusakowski, J.; Grzegory, I.; Leszczyński, M.; Prystawko, P.; Skierbiszewski, C.; Porowski, S.; Hu, X.; Simin, G.; a, M. A. K., **Spin and interaction effects in Shubnikov–de Haas oscillations and the quantum Hall effect in GaN/AlGaN heterostructures.** *Journal of Physics: Condensed Matter* 2004,*16* (20), 3421-3421.](https://sci-hub.se/10.1088/0953-8984/16/20/013)
2. [Rumyantsev, S. L.; Shur, M. S.; Dyakonova, N.; Knap, W.; Meziani, Y.; Pascal, F.; Hoffman, A.; Hu, X.; Fareed, Q.; Bilenko, Y.; Gaska, R., **1∕f noise in GaN∕AlGaN heterostructure field-effect transistors in high magnetic fields at 300K.** *Journal of Applied Physics* 2004,*96* (7), 3845-3847.](https://sci-hub.se/10.1063/1.1787911)
3. [Meziani, Y. M.; Łusakowski, J.; Knap, W.; Dyakonova, N.; Teppe, F.; Romanjek, K.; Ferrier, M.; Clerc, R.; Ghibaudo, G.; Boeuf, F.; Skotnicki, T., **Magnetoresistance characterization of nanometer Si metal-oxide-semiconductor transistors.** *Journal of Applied Physics* 2004,*96* (10), 5761-5765.](https://sci-hub.se/10.1063/1.1806991)
4. [Lusakowski, J.; Knap, W.; Dyakonova, N.; Kaminska, E.; Piotrowska, A.; Golaszewska, K.; Shur, M. S.; Smirnov, D.; Gavrilenko, V.; Antonov, A.; Morozov, S., **Magnetotransport characterization of THz detectors based on plasma oscillations in submicron field-effect transistors.** *PHYSICS OF THE SOLID STATE* 2004,*46* (1), 138-145.](https://sci-hub.se/10.1134/1.1641940)
5. [Knap, W.; Teppe, F.; Meziani, Y.; Dyakonova, N.; Lusakowski, J.; Boeuf, F.; Skotnicki, T.; Maude, D.; Rumyantsev, S.; Shur, M. S., **Plasma wave detection of sub-terahertz and terahertz radiation by silicon field-effect transistors.** *Applied Physics Letters* 2004,*85* (4), 675-677.](https://sci-hub.se/10.1063/1.1775034)
6. [Knap, W.; Lusakowski, J.; Parenty, T.; Bollaert, S.; Cappy, A.; Popov, V. V.; Shur, M. S., **Terahertz emission by plasma waves in 60 nm gate high electron mobility transistors.** *Applied Physics Letters* 2004,*84* (13), 2331-2333.](https://sci-hub.se/10.1063/1.1689401)
7. [Antonov, A. V.; Gavrilenko, V. I.; Demidov, E. V.; Morozov, S. V.; Dubinov, A. A.; Lusakowski, J.; Knap, W.; Dyakonova, N.; Kaminska, E.; Piotrowska, A.; Golaszewska, K.; Shur, M. S., **Electron transport and terahertz radiation detection in submicrometer-sized GaAs/AlGaAs field-effect transistors with two-dimensional electron gas.** *Physics of the Solid State* 2004,*46* (1), 146-149.](https://sci-hub.se/10.1134/1.1641941)

**2003**

1. [Neu, G.; Teisseire‐Doninelli, M.; Morhain, C.; Semond, F.; Grandjean, N.; Beaumont, B.; Frayssinet, E.; Knap, W.; Witowski, A. M.; Sadowski, M. L., **Residual donors in wurtzite GaN homoepitaxial layers and heterostructures.** *PHYSICA STATUS SOLIDI B-BASIC RESEARCH* 2003,*235* (1), 20-25.](https://sci-hub.se/10.1002/pssb.200301524)
2. [Łusakowski, J.; Knap, W.; Kamińska, E.; Piotrowska, A.; Gavrilenko, V., **Magnetoconductivity of GaAs Transistors as Detectors of THz Radiation.** *Acta Physica Polonica A* 2003,*103* (6), 545-551.](http://przyrbwn.icm.edu.pl/APP/PDF/103/A103Z605.pdf)
3. [Chwalisz, B.; Wysmołek, A.; Bożek, R.; Korona, K.; Stępniewski, R.; Knap, W.; Pakuła, K.; Baranowski, J.; Grandjean, N.; Massies, J.; Prystawko, P.; Grzegory, I., **Localization Effects in GaN/AlGaN Quantum Well - Photoluminescence Studies.** *Acta Physica Polonica A* 2003,*103* (6), 573-578.](http://przyrbwn.icm.edu.pl/APP/PDF/103/A103Z609.pdf)

**2002**

1. [Rumyantsev, S. L.; Deng, Y.; Borovitskaya, E.; Dmitriev, A.; Knap, W.; Pala, N.; Shur, M. S.; Levinshtein, M. E.; Khan, M. A.; Simin, G.; Yang, J.; Hu, X., **Low-frequency noise in GaN/AlGaN heterostructure field-effect transistors at cryogenic temperatures.** *Journal of Applied Physics* 2002,*92* (8), 4726-4730.](https://sci-hub.se/10.1063/1.1508432)
2. [Peralta, X.; Knap, W., **THz detection by resonant 2-D plasmons in field effect devices.** *International Journal of High Speed Electronics and Systems* 2002,*12* (02), 491-500.](https://sci-hub.se/10.1142/S012915640200140X)
3. [Knap, W.; Kachorovskii, V.; Deng, Y.; Rumyantsev, S.; Lü, J. Q.; Gaska, R.; Shur, M. S.; Simin, G.; Hu, X.; Khan, M. A.; Saylor, C. A.; Brunel, L. C., **Nonresonant detection of terahertz radiation in field effect transistors.** *Journal of Applied Physics* 2002,*91* (11), 9346-9353.](https://sci-hub.se/10.1063/1.1468257)
4. [Knap, W.; Deng, Y.; Rumyantsev, S.; Shur, M. S., **Resonant detection of subterahertz and terahertz radiation by plasma waves in submicron field-effect transistors.** *Applied Physics Letters* 2002,*81* (24), 4637-4639.](https://sci-hub.se/10.1063/1.1525851)
5. [Knap, W.; Deng, Y.; Rumyantsev, S.; Lü, J. Q.; Shur, M. S.; Saylor, C. A.; Brunel, L. C., **Resonant detection of subterahertz radiation by plasma waves in a submicron field-effect transistor.** *Applied Physics Letters* 2002,*80* (18), 3433-3435.](https://sci-hub.se/10.1063/1.1473685)
6. [Knap, W.; Borovitskaya, E.; Shur, M. S.; Hsu, L.; Walukiewicz, W.; Frayssinet, E.; Lorenzini, P.; Grandjean, N.; Skierbiszewski, C.; Prystawko, P.; Leszczynski, M.; Grzegory, I., **Acoustic phonon scattering of two-dimensional electrons in GaN/AlGaN heterostructures.** *Applied Physics Letters* 2002,*80* (7), 1228-1230.](https://sci-hub.se/10.1063/1.1448401)

**2001**

1. [Frayssinet, E.; Knap, W.; Krukowski, S.; Perlin, P.; Wisniewski, P.; Suski, T.; Grzegory, I.; Porowski, S., **Evidence of free carrier concentration gradient along the c-axis for undoped GaN single crystals.** *Journal of Crystal Growth* 2001,*230* (3), 442-447.](https://sci-hub.se/10.1016/S0022-0248(01)01294-5)
2. [Contreras, S.; Knap, W.; Frayssinet, E.; Sadowski, M. L.; Goiran, M.; Shur, M., **High magnetic field studies of two-dimensional electron gas in a GaN/GaAlN heterostructure: Mechanisms of parallel conduction.** *Journal of Applied Physics* 2001,*89* (2), 1251-1255.](https://sci-hub.se/10.1063/1.1328788)

**2000**

1. [Skierbiszewski, C.; Perlin, P.; Wisniewski, P.; Knap, W.; Suski, T.; Walukiewicz, W.; Shan, W.; Yu, K. M.; Ager, J. W.; Haller, E. E., **Large, nitrogen-induced increase of the electron effective mass in In y Ga 1− y N x As 1− x.** *Applied Physics Letters* 2000,*76* (17), 2409-2411.](https://sci-hub.se/10.1063/1.126360)
2. [Neu, G.; Teisseire, M.; Frayssinet, E.; Knap, W.; Sadowski, M. L.; Witowski, A. M.; Pakula, K.; Leszczynski, M.; Prystawko, P., **Far-infrared and selective photoluminescence studies of shallow donors in GaN hetero-and homoepitaxial layers.** *Applied Physics Letters* 2000,*77* (9), 1348-1350.](https://sci-hub.se/10.1063/1.1290386)
3. [Knap, W.; Borovitskaya, E.; Shur, M. S.; Gaska, R.; Karczewski, G.; Brandt, B.; Maude, D.; Frayssinet, E.; Lorenzini, P.; Grandjean, N., **High magnetic field studies of AlGaN/GaN heterostructures grown on bulk GaN, SiC, and sapphire substrates.** *MRS Online Proceedings Library Archive* 2000,*639*.](https://sci-hub.se/https:/doi.org/10.1557/PROC-639-G7.3)
4. [Frayssinet, E.; Prystawko, P.; Leszczynski, M.; Domagala, J.; Knap, W.; Robert, J. L., **Microwave plasma etching of GaN in nitrogen atmosphere.** *physica status solidi (a)* 2000,*181* (1), 151-155.](https://sci-hub.se/10.1002/1521-396X(200009)181:1%3C151::AID-PSSA151%3E3.0.CO;2-7)
5. [Frayssinet, E.; Knap, W.; Prystawko, P.; Leszczynski, M.; Grzegory, I.; Suski, T.; Beaumont, B.; Gibart, P., **Infrared studies on GaN single crystals and homoepitaxial layers.** *Journal of Crystal Growth* 2000,*218* (2), 161-166.](https://sci-hub.se/https:/doi.org/10.1016/S0022-0248(00)00537-6)
6. [Frayssinet, E.; Knap, W.; Lorenzini, P.; Grandjean, N.; Massies, J.; Skierbiszewski, C.; Suski, T.; Grzegory, I.; Porowski, S.; Simin, G., **High electron mobility in AlGaN/GaN heterostructures grown on bulk GaN substrates.** *Applied Physics Letters* 2000,*77* (16), 2551-2553.](https://sci-hub.se/10.1063/1.1318236)
7. [Asif Khan, M.; Yang, J. W.; Knap, W.; Frayssinet, E.; Hu, X.; Simin, G.; Prystawko, P.; Leszczynski, M.; Grzegory, I.; Porowski, S., **GaN–AlGaN heterostructure field-effect transistors over bulk GaN substrates.** *Applied Physics Letters* 2000,*76* (25), 3807-3809.](https://sci-hub.se/10.1063/1.126788)
8. [Alause, H.; Knap, W.; Robert, J. L.; Planel, R.; Thierry-Mieg, V.; Julien, F. H.; Zekentes, K.; Mosser, V., **Room-temperature GaAs/AlGaAs multiple-quantum-well optical modulators for the 3-5 µm atmospheric window.** *Semiconductor Science and Technology* 2000,*15* (7), 724.](https://sci-hub.se/https:/iopscience.iop.org/article/10.1088/0268-1242/15/7/310)

**1999**

1. [Leszczynski, M.; Beaumont, B.; Frayssinet, E.; Knap, W.; Prystawko, P.; Suski, T.; Grzegory, I.; Porowski, S., **GaN homoepitaxial layers grown by metalorganic chemical vapor deposition.** *Applied Physics Letters* 1999,*75* (9), 1276-1278.](https://sci-hub.se/10.1063/1.124666)
2. [Knap, W.; Frayssinet, E.; Skierbiszewski, C.; Chaubet, C.; Sadowski, M. L.; Maude, D.; Asif Khan, M.; Shur, M. S., **Conduction Band Energy Spectrum of Two‐Dimensional Electrons in GaN/AlGaN Heterojunctions.** *physica status solidi (b)* 1999,*216* (1), 719-725.](https://onlinelibrary.wiley.com/doi/epdf/10.1002/%28SICI%291521-3951%28199911%29216%3A1%3C719%3A%3AAID-PSSB719%3E3.0.CO%3B2-4)
3. [Knap, W.; Frayssinet, E.; Sadowski, M. L.; Skierbiszewski, C.; Maude, D.; Falko, V.; Khan, M. A.; Shur, M. S., **Effective g\* factor of two-dimensional electrons in GaN/AlGaN heterojunctions.** *Applied Physics Letters* 1999,*75* (20), 3156-3158.](https://sci-hub.se/10.1063/1.125262)
4. [Frayssinet, E.; Knap, W.; Robert, J.; Prystawko, P.; Leszczynski, M.; Suski, T.; Wisniewski, P.; Litwin-Staszewska, E.; Porowski, S.; Beaumont, B.; Gibart, P., **Infrared reflectivity and transport investigations of GaN single crystals and homoepitaxial layers** *PHYSICA STATUS SOLIDI B-BASIC RESEARCH* 1999,*216* (1), 91-94.](https://onlinelibrary.wiley.com/doi/abs/10.1002/%28SICI%291521-3951%28199911%29216%3A1%3C91%3A%3AAID-PSSB91%3E3.0.CO%3B2-E)
5. [Aleshkin, V. Y.; Andronov, A. A.; Antonov, A. V.; Bekin, N. A.; Gavrilenko, A. V.; Gavrilenko, V. I.; Revin, D. G.; Uskova, E. A.; Zvonkov, B. N.; Zvonkov, N. B., **Far infrared emission and population inversion of hot holes in MQW InGaAs/GaAs heterostructures excited at lateral transport.** *COMPOUND SEMICONDUCTORS 1998* 1999, (162), 105-110.](https://sci-hub.se/10.1016/S0921-4526(98)00356-1)

**1998**

1. [Wisniewski, P.; Knap, W.; Malzac, J. P.; Camassel, J.; Bremser, M. D.; Davis, R. F.; Suski, T., **Investigation of optically active E1 transversal optic phonon modes in AlxGa1−xN layers deposited on 6H–SiC substrates using infrared reflectance.** *Applied Physics Letters* 1998,*73* (13), 1760-1762.](https://sci-hub.se/10.1063/1.122273)
2. [Skierbiszewski, C.; Knap, W.; Dur, D.; Ivchenko, E. L.; Huant, S.; Etienne, B., **Far infrared spectroscopy with high resolution cyclotron resonance filters.** *Journal of Applied Physics* 1998,*84* (1), 433-438.](https://sci-hub.se/10.1063/1.368081)
3. [Prystawko, P.; Leszczynski, M.; Beaumont, B.; Gibart, P.; Frayssinet, E.; Knap, W.; Wisniewski, P.; Bockowski, M.; Suski, T.; Porowski, S., **Doping of homoepitaxial GaN layers.** *physica status solidi (b)* 1998,*210* (2), 437-443.](https://sci-hub.se/10.1002/(SICI)1521-3951(199812)210:2%3C437::AID-PSSB437%3E3.0.CO;2-L)
4. [Levinshtein, M. E.; Pascal, F.; Contreras, S.; Knap, W.; Rumyantsev, S. L.; Gaska, R.; Yang, J. W.; Shur, M. S., **Low-frequency noise in GaN/GaAlN heterojunctions.** *Applied Physics Letters* 1998,*72* (23), 3053-3055.](https://sci-hub.se/10.1063/1.121538)
5. [Leszczyński, M.; Prystawko, P.; Śliwinski, A.; Suski, T.; Litwin-Staszewska, E.; Porowski, S.; Paszkiewicz, R.; Tłaczała, M.; Beaumont, B.; Gibart, P., **Polarity related problems in growth of GaN homoepitaxial layers.** *Acta Physica Polonica A* 1998,*94* (3), 427-430.](http://przyrbwn.icm.edu.pl/APP/PDF/94/a094z3p14.pdf)
6. [Goiran, M.; Engelbrecht, F.; Yang, F.; Knap, W.; Huant, S.; Negre, N.; Barbaste, R.; Leotin, J.; Helbig, R.; Askenazy, S., **Cyclotron resonance of electrons in 6H-SiC in high magnetic fields up to 50T.** *Physica B: Condensed Matter* 1998,*246-247*, 270-273.](https://sci-hub.se/10.1016/S0921-4526(97)00913-7)
7. [Farah, W.; Dyakonov, M.; Scalbert, D.; Knap, W., **Optically induced nuclear magnetic field in InP.** *Physical Review B* 1998,*57* (8), 4713-4719.](https://sci-hub.se/10.1103/PhysRevB.57.4713)
8. [Falkovsky, L. A.; Knap, W.; Chervin, J. C.; Wisniewski, P., **Phonon modes and metal-insulator transition in GaN crystals under pressure.** *Physical Review B* 1998,*57* (18), 11349-11355.](https://sci-hub.se/10.1103/PhysRevB.57.11349)
9. [D’yakonova, N. V.; Levinshtein, M. E.; Contreras, S.; Knap, W.; Beaumont, B.; Gibart, P., **Low-frequency noise in n-GaN.** *SEMICONDUCTORS* 1998,*32* (3), 257-260.](https://sci-hub.se/10.1134/1.1187374)
10. [Contreras, S.; Goiran, M.; Knap, W.; Yang, F.; Rakoto, H.; Barbaste, R.; Robert, J. L.; Leotin, J.; Askenazy, S.; Chen, Q.; Asif Khan, M., **High magnetic field studies of quantum transport and cyclotron resonance on 2D gas in GaN/GaAlN heterojunction.** *Physica B* 1998,*246-247*, 274-277.](https://sci-hub.se/10.1016/S0921-4526(97)00914-9)
11. [Allegre, J.; Lefebvre, P.; Juillaguet, S.; Camassel, J.; Knap, W.; Chen, Q.; Khan, M., **Optical properties of InGaN/GaN multiple quantum wells.** *SILICON CARBIDE, III-NITRIDES AND RELATED MATERIALS, PTS 1 AND 2* 1998,*264*, 1295-1298.](https://hal.archives-ouvertes.fr/hal-00543785)
12. [Aleshkin, V. Y.; Andronov, A. A.; Antonov, A. V.; Bekin, N. A.; Gavrilenko, A. V.; Gavrilenko, V. I.; Revin, D. G.; Uskova, E. A.; Zvonkov, B. N.; Zvonkov, N. B.; Knap, W.; Lusakowski, J.; Skierbiszewski, C., **Far Infrared Emission and Population Inversion of Hot Holes in MQW InGaAs/GaAs Heterostructures under Real Space Transfer.** *Materials Science Forum* 1998,*297-298*, 261-264.](https://sci-hub.se/10.4028/www.scientific.net/MSF.297-298.261)

**1997**

1. [Zduniak, A.; Dyakonov, M. I.; Knap, W., **Universal behavior of magnetoconductance due to weak localization in two dimensions.** *Physical Review B* 1997,*56* (4), 1996-2003.](https://sci-hub.se/10.1103/PhysRevB.56.1996)
2. [Knap, W.; Contreras, S.; Alause, H.; Skierbiszewski, C.; Camassel, J.; Dyakonov, M.; Robert, J. L.; Yang, J.; Chen, Q.; Asif Khan, M.; Sadowski, M. L.; Huant, S.; Yang, F. H.; Goiran, M.; Leotin, J.; Shur, M. S., **Cyclotron resonance and quantum Hall effect studies of the two-dimensional electron gas confined at the GaN/AlGaN interface.** *Applied Physics Letters* 1997,*70* (16), 2123-2125.](https://sci-hub.se/10.1063/1.118967)
3. [Dmowski, L. H.; Cheremisin, M.; Skierbiszewski, C.; Knap, W., **Far-infrared narrow-band photodetector based on magnetically tunable cyclotron resonance-assisted transitions in pure n-type InSb.** *ACTA PHYSICA POLONICA A* 1997,*92* (4), 733-736.](http://przyrbwn.icm.edu.pl/APP/PDF/92/a092z4p18.pdf)
4. [Contreras, S.; Knap, W.; Skierbiszewski, C.; Alause, H.; Robert, J. L.; Khan, M. A., **Observation of quantum Hall effect in 2D-electron gas confined in GaN/GaAlN heterostructure.** *Materials Science and Engineering: B* 1997,*46* (1), 92-95.](https://sci-hub.se/10.1016/S0921-5107(96)01939-3)
5. [Allègre, J.; Lefebvre, P.; Juillaguet, S.; Knap, W.; Camassel, J.; Chen, Q.; Khan, M. A., **Time-resolved photoluminescence studies of InGaN/GaN multiple quantum wells.** *MRS Internet Journal of Nitride Semiconductor Research* 1997,*2* (33-41).](https://sci-hub.se/10.1557/S1092578300001605)
6. [Alause, H.; Skierbiszewski, C.; Dyakonov, M.; Knap, W.; Sadowski, M. L.; Huant, S.; Young, J.; Asif Khan, M.; Chen, Q., **Contactless characterisation of 2D-electrons in GaN/AlGaN HFETs.** *DIAMOND AND RELATED MATERIALS* 1997,*6* (10), 1536-1538.](https://sci-hub.se/10.1016/S0925-9635(97)00052-6)
7. [Alause, H.; Malzac, J. P.; Grasdepot, F.; Nouaze, V.; Hermann, J.; Knap, W., **Micromachined optical tunable filter for long term stability gas sensors.** *IEE Proceedings-Optoelectronics* 1997,*144* (5), 350-354.](https://sci-hub.se/10.1049/ip-opt:19971575)
8. [Alause, H.; Knap, W.; Azema, S. C.; Bluet, J. M.; Sadowski, M. L.; Huant, S.; Young, J.; Khan, M. A.; Chen, Q.; Shur, M., **Optical and electrical properties of 2-dimensional electron gas in GaN/AlGaN heterostructures.** *Materials Science and Engineering: B* 1997,*46* (1), 79-83.](https://sci-hub.se/10.1016/S0921-5107(96)01936-8)
9. [Alause, H.; Grasdepot, F.; Malzac, J. P.; Knap, W.; Hermann, J., **Micromachined optical tunable filter for domestic gas sensors.** *Sensors and Actuators B: Chemical* 1997,*43* (1), 18-23.](https://sci-hub.se/10.1016/S0925-4005(97)00139-1)

**1996**

1. [Perlin, P.; Litwin‐Staszewska, E.; Suchanek, B.; Knap, W.; Camassel, J.; Suski, T.; Piotrzkowski, R.; Grzegory, I.; Porowski, S.; Kaminska, E.; Chervin, J. C., **Determination of the effective mass of GaN from infrared reflectivity and Hall effect.** *Applied Physics Letters* 1996,*68* (8), 1114-1116.](https://sci-hub.se/10.1063/1.115730)
2. Perlin, P.; Knap, W.; Taliercio, T.; Camassel, J.; Robert, J. L.; Suski, T.; Grzegory, I.; Jun, J.; Porowski, S.; Chervin, J. C., **Optical characterization of the free electron gas in bulk single crystals of GaN by means of Raman scattering and infrared reflectivity: evidence of phonon-plasmon coupled modes.** *Institute of Physics Conference Series* 1996,*142*, 951-954.
3. [Perlin, P.; Knap, W.; Camassel, J.; Polian, A.; Chervin, J. C.; Suski, T.; Grzegory, I.; Porowski, S., **Metal‐Insulator Transition in GaN Crystals.** *physica status solidi (b)* 1996,*198* (1), 223-233.](https://sci-hub.se/10.1002/pssb.2221980130)
4. [Knap, W.; Skierbiszewski, C.; Zduniak, A.; Litwin-Staszewska, E.; Bertho, D.; Kobbi, F.; Robert, J. L.; Pikus, G. E.; Pikus, F. G.; Iordanskii, S. V.; Mosser, V.; Zekentes, K.; Lyanda-Geller, Y. B., **Weak antilocalization and spin precession in quantum wells.** *Physical Review B* 1996,*53* (7), 3912-3924.](https://sci-hub.se/10.1103/PhysRevB.53.3912)
5. [Knap, W.; Alause, H.; Bluet, J. M.; Camassel, J.; Young, J.; Asif Khan, M.; Chen, Q.; Huant, S.; Shur, M., **The cyclotron resonance effective mass of two-dimensional electrons confined at the GaN/AlGaN interface.** *Solid State Communications* 1996,*99* (3), 195-199.](https://sci-hub.se/10.1016/0038-1098(96)00232-3)
6. [Grasdepot, F.; Alause, H.; Knap, W.; Malzac, J. P.; Suski, J., **Domestic gas sensor with micromachined optical tunable filter.** *Sensors and Actuators B: Chemical* 1996,*36* (1), 377-380.](https://sci-hub.se/10.1016/S0925-4005(97)80099-8)
7. [Dmowski, L. H.; Zduniak, A.; Litwin‐Staszewska, E.; Contreras, S.; Knap, W.; Robert, J. L., **Study of quantum and classical scatterIng times In pseudomorphic AlGaAs/InGaAs/GaAs by means of pressure.** *physica status solidi (b)* 1996,*198* (1), 283-288.](https://sci-hub.se/10.1002/pssb.2221980136)

**1995**

1. [Perlin, P.; Camassel, J.; Knap, W.; Taliercio, T.; Chervin, J. C.; Suski, T.; Grzegory, I.; Porowski, S., **Investigation of longitudinal‐optical phonon‐plasmon coupled modes in highly conducting bulk GaN.** *Applied Physics Letters* 1995,*67* (17), 2524-2526.](https://sci-hub.se/10.1063/1.114446)
2. [Lancefield, D.; Adams, A. R.; Meney, A. T.; Knap, W.; Litwin-Staszewska, E.; Skierbiszewski, C.; Robert, J. L., **The light-hole mass in a strained InGaAs/GaAs single quantum well and its pressure dependence.** *Journal of Physics and Chemistry of Solids* 1995,*56* (3), 469-473.](https://sci-hub.se/10.1016/0022-3697(94)00223-1)
3. [Knap, W.; Skierbiszewski, C.; Litwin-Staszewska, E.; Kobbi, F.; Zduniak, A.; Robert, J. L.; Pikus, G. E.; Iordanskii, S. V.; Mosser, V.; Zekentes, K.,](http://przyrbwn.icm.edu.pl/APP/PDF/87/a087z2p31.pdf) **[Weak Antilocalization in Quantum Wells.](http://przyrbwn.icm.edu.pl/APP/PDF/87/a087z2p31.pdf)***[Acta Physica Polonica-Series A General Physics](http://przyrbwn.icm.edu.pl/APP/PDF/87/a087z2p31.pdf)* [1995,](http://przyrbwn.icm.edu.pl/APP/PDF/87/a087z2p31.pdf)*[87](http://przyrbwn.icm.edu.pl/APP/PDF/87/a087z2p31.pdf)* [(2), 427-432.](http://przyrbwn.icm.edu.pl/APP/PDF/87/a087z2p31.pdf)
4. [Essaleh, L.; Galibert, J.; Rincón, C.; Wasim, S. M.; Knap, W.; Leotin, J., **Infrared Reflectivity and Electrical Parameters of Zn‐Doped Degenerate CuInSe2.** *physica status solidi (b)* 1995,*189* (1).](https://sci-hub.se/10.1002/pssb.2221890134)

**1994**

1. [Stȩpniewski, R.; Potemski, M.; Buhmann, H.; Toet, D.; Maan, J. C.; Martinez, G.; Knap, W.; Raymond, A.; Etienne, B., **Magneto-optical spectroscopy of free- and bound-electron-hole excitations in the presence of a two-dimensional electron gas.** *Physical Review B* 1994,*50* (16), 11895-11901.](https://sci-hub.se/10.1103/PhysRevB.50.11895)
2. [Zawadzki W.; Chaubet, C.; Dur, D.; Knap, W.; Raymond, A., **Cyclotron emission study of electron masses in GaAs-GaAlAs heterostructures.** *Semiconductor Science and Technology* 1994,*9* (3), 320-320.](https://sci-hub.se/10.1088/0268-1242/9/3/012)
3. [Litwin-Staszewska, E.; Kobbi, F.; Kamal-Saadi, M.; Dur, D.; Skierbiszewski, C.; Sibari, H.; Zekentes, K.; Mosser, V.; Raymond, A.; Knap, W.; Robert, J. L., **Determination of the basic parameters of pseudomorphic GaInAs quantum wells by means of simultaneous transport and optical investigations.** *SOLID-STATE ELECTRONICS* 1994,*37* (4), 665-667.](https://sci-hub.se/10.1016/0038-1101(94)90271-2)

**1993**

1. [Vicente, P.; Kavokin, A. V.; Raymond, A.; Lyapin, S. G.; Zekentes, K.; Dur, D.; Knap, W., **Oscillator strength of the E1HH1 excitonic transition as a function of magnetic field in modulation doped GaAlAs/GaAs quantum well.** *JOURNAL DE PHYSIQUE IV* 1993,*3* (C5), C5-323.](https://hal.archives-ouvertes.fr/jpa-00251653/document)
2. Smirnov, D. V. M., D. V.; Safonchik, M. O.; Roznovan, Yu. V.; Leotin, J.; Knap, W., **Magnetophonon resonance and infrared lattice reflection.** *Semiconductors* 1993,*27* (10), 901-905.
3. [A. Raymond, C. Chaubet, D. Dur, W. Knap, W. Zawadzki and J. P. Andre,](https://iopscience.iop.org/article/10.7567/JJAPS.32S1.78/pdf) **[FIR Properties of GaAs–GaAlAs Heterojunctions Controlled by Metastable States under Pressure.](https://iopscience.iop.org/article/10.7567/JJAPS.32S1.78/pdf)** *[Japanese Journal of Applied Physics](https://iopscience.iop.org/article/10.7567/JJAPS.32S1.78/pdf)* [1993,](https://iopscience.iop.org/article/10.7567/JJAPS.32S1.78/pdf)

**1992**

1. [Knap, W.; Lusakowski, J.; Karpierz, K.; Orsal, B.; Robert, J. L., **Improved performance of magnetically tunable GaAs and InP far‐infrared detectors.** *Journal of Applied Physics* 1992,*72* (2), 680-683.](https://sci-hub.se/10.1063/1.351852)
2. [Knap, W.; Dur, D.; Raymond, A.; Meny, C.; Leotin, J.; Huant, S.; Etienne, B., **A far‐infrared spectrometer based on cyclotron resonance emission sources.** *Review of Scientific Instruments* 1992,*63* (6), 3293-3297.](https://sci-hub.se/10.1063/1.1142540)
3. [Gregorkiewicz, T.; Knap, W.; Bekman, H. H. P. T.; Brunel, L. C.; Ammerlaan, C. A. J.; Martinez, G., **High-field EPR spectroscopy of thermal donors in silicon.** *Physica B: Condensed Matter* 1992,*177* (1), 476-480.](https://sci-hub.se/10.1016/0921-4526(92)90153-J)
4. [Gregorkiewicz, T.; Bekman, H. H. P. T.; Ammerlaan, C. A. J.; Knap, W.; Brunel, L. C.; Martinez, G., **High-resolution EPR spectroscopy of the Si-NL10 thermal donor.** *Physical Review B* 1992,*45* (11), 5873-5878.](https://sci-hub.se/10.1103/PhysRevB.45.5873)

**1991**

1. [Rau, U.; Peinke, J.; Parisi, J.; Karpierz, K.; Łusakowski, J.; Knap, W., **Reconstruction of traveling waves in semi-insulating GaAs.** *Physics Letters A* 1991,*152* (7), 356-360.](https://sci-hub.se/10.1016/0375-9601(91)90738-T)
2. [Andre, C. C.; Raymond, A.; Knap, W.; Mulot, J. Y.; Baj, M.; J, P., **Pressure dependence of the cyclotron mass in n-GaAs-GaAlAs heterojunctions by FIR emission and transport experiments.** *Semiconductor Science and Technology* 1991,*6* (3), 160-160.](https://sci-hub.se/10.1088/0268-1242/6/3/003)

**1990**

1. [Stȩpniewski, R.; Knap, W.; Raymond, A.; Martinez, G.; Maan, J. C.; Etienne, B.; Ploog, K., **Exciton-one-component plasma interaction in high magnetic fields.** *Surface Science* 1990,*229* (1), 519-521.](https://sci-hub.se/10.1016/0039-6028(90)90945-5)
2. [Knap, W.; Huant, S.; Chaubet, C.; Etienne, B., **Magneto-emission from shallow donors in quantum wells.** *Superlattices and Microstructures* 1990,*8* (3), 313-316.](https://sci-hub.se/10.1016/0749-6036(90)90255-6)

**1989**

1. Karpierz, K., J. Lusakowski, and W. Knap, **ACTIVATION OF LOW-FREQUENCY OSCILLATIONS IN SI GAAS.** *Acta Physica Polonica A* 1989,*75* (2), 207-210

**1988**

1. Slupinski, T. a. W. K., **DETECTION OF THE OPTICAL-TRANSITIONS BETWEEN LANDAU SUBLEVELS IN HGTE BASED ON OPTICALLY INDUCED NERNST-ETTINGHAUSEN EFFECT.** *Acta Physica Polonica A* 1988,*73* (3), 389-394
2. [Lusakowski, J., M. Jezewski, W. Knap, and W. Kuszko, **LOW-FREQUENCY OSCILLATIONS AND CHAOS IN SEMIINSULATING GAAS.** *Acta Physica Polonica A* 1988,*73* (2), 183-187](https://sci-hub.se/10.1016/0038-1101(88)90395-4)
3. Knap, W.; Jeżewski, M.; Lusakowski, J.; Kuszko, W., **Low frequency and chaotic current oscillations in semiinsulating GaAs.** *solid-state Electronics* 1988,*31* (3-4), 813-816.
4. Kaminska, E., A. Piotrowska, W. Knap, and P. Trautman, **OHMIC CONTACTS TO SEMI-INSULATING GAAS.** *Acta Physica Polonica A* 1988,*73* (3), 501-503 .
5. [Etienne, S. H.; Knap, W.; Martinez, G., **Quasi-Two-Dimensional Resonant Bound Polarons.** *EPL (Europhysics Letters)* 1988,*7* (2), 159-159.](https://www.researchgate.net/profile/Serge_Huant/publication/231036249_Quasi-Two-Dimensional_Resonant_Bound_Polarons/links/55b8895408aed621de05da15/Quasi-Two-Dimensional-Resonant-Bound-Polarons.pdf)

**1986**

1. Dybko, K.; Knap, W.; Gornik, E., **Application of Landau emission for far infrared spectroscopy of shallow donors in InP.** *Acta Physica Polonica, Series A* 1986,*69* (5), 765-768.

**1985**

1. [Knap, W.; Stȩpniewski, R.; Fantner, E., **Optically Induced Nernst‐Ettinghausen Effect in the Far Infrared and Strong Magnetic Fields in HgTe and InSb.** *physica status solidi (b)* 1985,*132* (1), 133-140.](https://sci-hub.se/10.1002/pssb.2221320113)
2. [Helm, M.; Knap, W.; Seidenbusch, W.; Lassnig, R.; Gornik, E.; Triboulet, R.; Taylor, L. L., **POLARON CYCLOTRON RESONANCE IN n-CdTe AND n-InP** *Solid State Communications* 1985,*53* (6), 547-550.](https://sci-hub.se/10.1016/0038-1098(85)90189-9)

**1984**

1. [Knap, W.; Kossut, J.; Mycielski, J., **Photoelectromagnetic effect and photoconductivity in quantizing magnetic fields.** *physica status solidi (b)* 1984,*122* (2), 761-773.](https://sci-hub.se/10.1002/pssb.2221220242)
2. [Górska, M.; Wojtowicz, T.; Knap, W., **Cyclotron resonance in Pb1−xMnxTe.** *Solid State Communications* 1984,*51* (2), 115-118.](https://sci-hub.se/10.1016/0038-1098(84)90247-3)

**1980**

1. [Wittlin, A.; Knap, W.; Wilamowski, Z.; Grynberg, M., **Evidence for the spin-dependent scattering of conduction electrons on Mn2+ ions in Hg1− xMnxTe and Cd1− xMnxSe mixed crystals.** *Solid State Communications* 1980,*36* (3), 233-236.](https://sci-hub.se/10.1016/0038-1098(80)90266-5)

List of invited papers followed by Journal papers and Conference papers:

**1.2 INVITED and TUTORIAL (117)**

1. *(tutorial)*W. Knap, et al, **"Transistors based THz detectors - from basic physics to first real world applications."**, European Solid Deuce Research Conference, Cracow, Poland, 22–26 September, 2019
2. *(tutorial)*W. Knap, et al, **"Terahertz Plasma Oscillations in Field Effect Transistors: from Basic Physics to Applications (>25 Years History)."**, 8th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & GDR-I FIR-LAB Workshop Nizhny Novgorod, Nizhny Novgorod, Russia, 8 August, 2019
3. *(invited)*W. Knap, et al, **"THz cyclotron emission from bulk HgCdRe alloys."**, 29th International Travelling Summer School (ITSS) on Microwaves and Lightwaves, Frankfurt, Germany, 13–19 July, 2019
4. *(invited)*W. Knap, et al, **"THz cyclotron emission from Dirac-like fermions in bulk HgCdTe."**, International Workshop of FIR-LAB network, Nizhny Novgorod, Russia, 7 July, 2019
5. *(tutorial)*W. Knap, et al, **"Tutorial Terahertz plasma oscillations in Nanotransistors-Basic Science and Applications."**, XXIII International Symposium "Nanophysics & Nanoelectronics" Nizhny Novgorod, Nizhny Novgorod, Russia, 10–14 March, 2019
6. *(invited)*W. Knap, et al, **"Field Effect Transistors Based Terahertz Detectors 25 Years History, State of the Art and Future Directions."**, 43rd International Conference on Infrared, Milimeter and Terahertz Waves, Nagoya, Japan, 9–14 September, 2018
7. *(invited)*W. Knap, et al, **"New GaN FETs and Silicon Junctionless Field Effect Transistor Terahertz Detectors."**, Frontiers of photonics, plasmonics and electronics with 2D nanosystems, Erice, Italy, 14–20 July, 2018
8. *(invited)*W. Knap, et al, **"New GaN and Silicon Junctionless Field Effect Transistor Terahertz Detectors."**, 9th International Conference Materials Science and Condensed Matter Physics, Chisinau, Republic of Moldova, 25–28 September, 2018
9. *(oral)*W. Knap, et al, **"Topological Phases of HgTe Quantum Wells for QHE resistance standard applications."**, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop, Warsaw, Poland, 17–21 September, 2018
10. *(oral)*W. Knap, et al, **"EdgeFET Based on AlGaN/GaN with Two Lateral Schottky Barrier Gates Towards Resonant Terahertz Detection."**, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop, Warsaw, Poland, 17–21 September, 2018
11. *(invited)*W. Knap, et al, **"Terahertz Vision Using Field Effect Transistors Detectors Arrays"**, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May, 2018
12. *(invited)*W. Knap, et al, **"Terahertz imaging and wireless communication with nanometer field effect transistor arrays"**, International Symposium on Photonics and Optical Communications (ISPOC 2017) Katahira - Sendai - Japan, 25-26 October, 2017
13. *(invited)*W. Knap, et al, **“Terahertz Imaging With GaAs and GaN Plasma Field Effect Transistors Detectors Arrays”**, 4th International Symposium on Microwave and Terahertz Science and Applications 2017, Okayama- Japan, November 19-23, 2017
14. *(plenary)*W. Knap, et al, **“Terahertz Imaging and Wireless Communication with Nanometer Field Effect Transistor Arrays”**, 17 th International Conference on Emerging Technologies ETMOS , Warsaw, May 28 - 30, 2017
15. *(invited)*W. Knap, D. But, F. Teppe J. Suszek, A. M. Siemion, M. Sypek, G. Cywinski, **“Terahertz Plasma Field Effect Transistors: From Basic Physics to First Postal Scanners Imaging Applications”**, 46rd European Microwave Conference 2016, London, October 3-7, 2016
16. *(plenary)*W. Knap, et al **“PLASMA FIELD EFFECT TRANSISTOR ARRAYS FOR IMAGING IN SUB-THZ ATMOSPHERIC WINDOWS”**, 5th Russia-Japan-USA-Europe Symposium on Fundamental and Applied Problems of Terahertz Devices and Technologiers RJUSE TeraTech 2016, Sendai- Japan , Oct 31-Nov 1 June, 2016
17. *(plenary)*W. Knap et al., **“Terahertz Plasma FETs - First Imaging Applications”**, Emerging Technologies 2016 Conference, Montreal, May 25 – 27, 2016
18. *(plenary)*W. Knapet al., **“Terahertz Plasma Field Effect Transistors: From Basic Physics to First Imaging Applications”**, International Workshop on "Terahertz Science, Nanotechnologies and Applications" – Erice (Sicily), Italy - July 16-22, 2016
19. *(invited)*W. Knap, N. Dyakonova, D. But, F. Teppe J. Suszek, A. M. Siemion, M. Sypek, G. Cywinski, K. Szkudlarek, I. Yahniuk, **“Terahertz Imaging With GaAs and GaN Plasma Field Effect Transistors Detectors Arrays”**, 23rd International Conference Mixed Design of Integrated Circuits and Systems MIXDES 2016, Lodz, 23-25 June, 2016
20. *(plenary)* W. Knap, B. Moulin, M. Sypek, D. Coquillat, G. Cywinski, J. Suszek, M. Triki, D. But, A.Siemion, K. Szkudlarek, C. Archier, N. Dyakonova, T. Antonini, F. Teppe **“Plasma Field Effect Transistors Arrays for Amplitude and Polarization Imaging in THz Range”**, 8th International Conference on Materials Science and Condensed Matter Physics, September 12-16, 2016, Chisinau, Moldova
21. W. Knap, D. But, D. Coquillat, N. Dyakonova, F. Teppe, **“Terahertz Imaging by Field Effect Transistors”**, Conference 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, May 9-11, Krakow, 2016
22. W. Knap, N. Dyakonova, D. But, F. Teppe, M. Sypek, J. Suszek, A. Wolos, G. Cywinski, K.Szkudlarek, I.Yahniuk, **“Physics and Applications of Field Effect Transistors for Terahertz Imaging”**,Energy Materials Nanotechnology Meeting on Terahertz 2016 San Sebastian, Spain, May 14-18, 2016
23. W. Knap, M. Sypek, D. B. But, N. Dyakonova, D. Coquillat, F. Teppe, E. Kling, **“Terahertz Imaging with Nanometer Field Effect Transistors for Security Screening”**, Paris –OPTRO 7th International Symposium on Optronics in Defense and Security, Paris 2-4 February, 2016
24. W. Knapet al., **“Terahertz science and technology - achievements and future perspectives of French-Polish collaborative projects”**, French-Polish Forum of Research and Innovations, Krakow, 8 June, 2016.
25. W. Knap, D. B. But, N. Dyakonova, D. Coquillat, F. Teppe, M. Vitiello, S. D. Ganichev, M. Sypek, **“Terahertz Detectors Based on Plasma Oscillations in Nanometer Field Effect Transistors”**, 9th Workshop on Frontiers in Electronics (WOFE-2015) will be held on December 15-18, 2015, in the Caribe Hilton Hotel, San Juan, Puerto Rico, USA.
26. W. Knap, J. Suszek, D. Coquillat, G. Cywinski, N. Dyakonova, F. Teppe, M. Sypek, **“Terahertz Plasma FETs from Basic Physics to First Fast Terahertz Scanners for Detection of Explosives and CBRN”**, NATO ARW on THz Diagnostics of CBRN effects and Detection of Explosives & CBRN, Izmir, Turkey, 3-6 November 2015
27. W. Knap, and M. Sypek **“Terahertz Imaging with Field Effect Transistors”,**European Microwave Week EuMW Paris September 6-11, 2015
28. *(plenary)* W. Knap **“Terahertz Imaging and Broadband Wireless Communication Using Plasma Oscillations in Nanometer Field Effect Transistors”**, 2nd International Conference on Applied Science and Environmental Technology, Bangkok, Thailand, August 2015
29. *(plenary)*W. Knap et al **“From Basic Physics to Applications of THz Nanotransistors”**,4th Russian-Japan-USA Symposium (RJUS-2015) on Fundamental & Applied Problems of Terahertz Devices & Technologies "RJUS TeraTech-2015", Chernogolovka, Russia, June 9-12, 2015
30. *(plenary)* W. Knap **“Terahertz Excitations in Terahertz Nanotransistors”**, 19th Symposium on Nanophysics an Nanotechnology, Nizhny Novgorod, Russia, March 10-14, 2015
31. W. Knap et al **“Plasma Oscillations in Field Effect Transistors for Room Temperature Terahertz Imaging Applications”**, 3rd International Symposium on Microwave/THz Science and Technology MTSA 2015, Okinawa, Japan, June 30 – July 4, 2015
32. W. Knap et al **“Terahertz Detection by Plasma Waves Nonlinearities – in semiconductors and topological insulator systems”**, Russian Conference on Semiconductor Photonic Problems, Novosibirsk, Russia, October 12-16, 2015
33. W. Knap et al **“Terahertz Communication with Nanometer Field Effect Transistors – project WITH”**, 11th Japan-French Workshop on Nanomaterials, Rennes, France, 27-30 May, 2015
34. W. Knap **“Physics of Terahertz Field Effect Transistor Detectors”**, European Optical Society (EOS) organizes the 4th topical meeting on Terahertz Science & Technology in Camogli (Italy), 11–14 May, 2014
35. W. Knap, D. But, N. Diakonova, F. Teppe, D. Coquillat, **“Terahertz FETs for Laser Aplications”**, International Conf. on Advanced Laser Technologies, Cassis, France, October, 2014
36. (plenary) W. Knap , N. Diakonova et al **“THz plasma oscillations in semiconductor nanostructures: physics and applications”**, 7th International Conference on Materials Science and Condensed Matter Physics (MSCMP 2014), Kishiniev, Moldavia, Sept. 16-19, 2014
37. W. Knap et al **“Physics of THz excitation in Nanometric Semiconductor Structures”**, International Training School in Terahertz, Infrared and Millimeter-Wave technology and its Application to Sensing and Imaging School of Electronic and Electrical Engineering, University of Leeds, UK, 14 - 16 July, 2014
38. W. Knap, D. But, N. Diakonova, F. Teppe, D. Coquillat **“Physical Limits of Terahertz Plasma Transistors”**, 5th Int. Symposium on Terahertz Nanoscience, Martinique, December, 2014
39. W. Knap, D. But, A. El Fatimy, P. Buzatu, O. Klimenko, N. Diakonova, **”Temperature limitations of THz plasma detectors”**, European Microwave Week, Rome, Italy, October, 2014
40. W. Knap et al **“Nanotransistor based THz plasma detectors: low temperatures, graphene, linearity, and circular polarization studies”**, SPIE, San Diego, USA, August, 2013
41. W. Knap **“THz imaging with Field Effect transistors – limits of temperature improvements”**, European Microwave Week, Nurnberg, Germany 6-11, October, 2013
42. W. Knap, S. Rumyantcev **“Physical limitations of Terahertz Detectors based on FETs”**, International Workshop on Optical Terahertz Science and Technology OTST Kyoto, Japan, April, 2013
43. Knap **“Overview on physical limits of Terahertz Field Effect Transistors”**, 38th Int. Conf. on Infrared, Millimeter and THz Waves, Mainz –Germany, Sept. 1-6, 2013
44. W. Knap **“Natrasistors for THz imaging and communication”**, 21 Int. Conf. on Applied Electromagnetics &Communication ICECom, Dubrownik, Croatia, October 14-16, 2013
45. Knap W. et al **“Limits of Broadband THz Detectors Based on Plasma Oscillations in Field Effect Transistors”**, SMMO&COST Conference, Warsaw, Poland, April 2013
46. Knap, W. But, D, S. Rumyantsev, M.S. Vitiello et al **"Recent Developments in THz Rectification by Plasma Nanotransistors : Helicity, Temperature and Power Dependence Studies"**, International Workshop on Frontiers in Electronics WOFE, December 17 – 20, 2013, San Juan, Puerto Rico
47. Knap, W. **"Silicon nanotransistors for Terahertz detection"**, International workshop on advanced process and device integration in nanoelectronics, Kiev (UA), 9-11 April, 2013.
48. Knap, W. **"Terahertz plasma oscillations in semiconductor nanostructures: basic physics and applications"**, TERA-MIR radiation: Materials, Generation, Detection and Applications, Cortona (IT), 20-24 May, 2013.
49. Knap, W. **"THz detection and imaging with silicon nanotransistors"**, Thz NATO advanced Research Workshop on THz and security applications, Kiev (UA), 26-29 May, 2013.
50. Knap, W. **"Terahertz plasma instabilities in nanometer size semiconductor structures"**, International conference on physics of semiconductors, Wisla (PL), 23-28 June, 2013.
51. Knap, W. **"THz Plasma Nonlinearities in Field Effect Transistors"**, 2-nd InternationalConference on Terahertz and Microwave radiations, Moscow (RU), 20-22, (2012)
52. Knap, W. **"Physics and Applications of Plasma Excitations in nanometer Field Effect Transistors"**, The International Winter School on Semiconductor Physics, St. Petersburg (RU), 24 – 27, 2012.
53. Knap, W. **"Field Effect Transistors for THz imaging and wireless communication applications"**, 19th International Conference on Microwaves, Radar and Wireless Communications, Warsaw, (PL), May 21-23, 2012.
54. Knap, W. **"Plasma wave generation in Field Effect Transistors"**, National Electronic Symposium, Darlowek (PL), June 11-14, 2012.
55. Knap, W. **"Terahertz Generation , Detection & Imaging by Nanometer Field Effect Transistors"**, International Microwave Symposium, Montreal (CA), June 17 -22, 2012.
56. Knap, W. **"THz Plasma Nonlinearities in Field Effect Transistors"**, MRS Symposium on Group IV Photonics for Sensing and Imaging, San Francisco, California, (US), April 9-13, 2012.
57. Knap, W. **"Field Effect Transistors for Terahertz Applications"**, International Workshop on Future Trends in Microelectronics, Corsica, (FR), June 25-29, 2012.
58. Knap, W. **"Terahertz detection and emission by field-effect transistors"**, SPIE, TERAHERTZ EMITTERS, RECEIVERS, AND APPLICATIONS III, San Diego, California (US), 12 - 16 August, 2012.
59. Coquillat, D., Diakonova, N., Poumirol, J., Goiran, M., Escoffier, W., Raquet, B., Teppe, F., Dyakonov, M. and Knap, W. **"Terahertz radiation rectification as a probe of universal conductance fluctuations in graphene”**, Teranano 2011, Extended Abstract 1(1) 25I-N-10 (2011).", International TeraNano & GDR-I THz Workshop, Osaka (JP), November 24-29, 2011.
60. Knap, W. **"Generation and Detection of Terahertz Radiation by Field Effect Transistors"**, PIERS 2011 Progress In Electromagnetics Research Symposium, Marrakesh (MA), March 20-23, 2011.
61. Knap, W. **"Silicon Field Effect Transistors for Terahertz Detection and Imaging"**, European Conference on Antennas and Propagation, Roma (IT), April 11-15, 2011.
62. Knap, W. **"Terahertz Detection and Emission by Field effect Transistors"**, 3rd International Workshop on THz Radiation: Basic Research &Applications, Kharkov (UA), September 4-8, 2011.
63. Knap, W. **"Nanotransistors for Terahertz Detection and Imaging."**, The 8th Spanish Conference on Electron Devices (CDE 2011), Palma de Mallorca (ES), Feb. 8-11, 2011.
64. Knap, W. **"Terahertz Detection and Emission by Field Effect Transistors"**, 10th Russian Conference on Physics of Semiconductors, N. Novgorod (RU), September 19-23, 2011.
65. Knap, W. **"Teraherz Emitters based on GaN Field Effect Transistors"**, International School and Conference on the Physics of Semiconductors, Krynica (PL), June 27 – July 1, 2011.
66. Knap, W. **"Plasma waves in Field Effect Transistors for THZ detection and generation"**, 6th International Optoelectronics and Photonics Winter School, Trento (IT), February 20-27, 2011.
67. Knap, W. **"Plasma Excitations in Field Effect Transistors: Physics and Aplications"**, International School and Conference on the Physics of Semiconductors, Krynica (PL), June27-July1st 2010
68. Knap, W., Diakonova, N., Videlier, H., Boubanga Tombet, S., Coquillat, D., Teppe, F., Karpierz, K. and Lusakowski, J. **"Field Effect Transistors for Terahertz Detection"**, The XIV Nanophysics and Nanoelectronics Symposium, Niznij Novgorod (RU), March 15 - 19, 2010.
69. W. Knap, D. Coquillat, N. Dyakonova, F. Teppe, K. Karpierz , J. Łusakowski, S. Monfray and T.Skotnicki, **“Field Effect Transistors For Terahertz Detection and Imaging”**, International Conference on Semiconductor Mid-IR Materials and Optics SMMO 2010, October 21th - 23th , 2010. Warsaw, Poland
70. W. Knap, D. Coquillat, N. Dyakonova, F. Teppe **“Silicon versus III-V semiconductor material choice for terahertz imaging with nanometerfield effect transistors based detectors”** 5th Int. Conference on Materials Science and Condensed Matter Physics MSCMP 2010, September 13-17, 2010, CHISINAU, MOLDOVIA
71. W. Knap, O. Klimenko, F. Schuster, N. Dyakonova, D. Coquillat, F. Teppe, B. Gifard **“Field Effect Transistors for Terahertz Detection and Emission”** 20th International Conference on Applied Electromagnetics and Communications, 20 – 23 September, 2010, Dubrovnik, CROATIA
72. W. Knap. D. Coquillat. F. Teppe.N. Dyakonova, **“Terahertz Detection and Emission by Field Effect Transistors: influence of transistor geometry and high magnetic fields”**, Invited key note Paper, Int. Conference on Infrared Millimeter and Terahertz Waves (IRMMW) 2010 Rome, Italy, 5-10 Sept., 2010
73. W. Knap, S. Nadar, H. Videlier, S. Boubanga-Tombet, D. Coquillat, N. Dyakonova, F. Teppe, D. Seliuta, I. Kasalynas, G. Valušis, K. Karpierz , J. Łusakowski, M. Sakowicz, S. Monfray and T. Skotnicki, **“Field Effect Transistors for Fast Terahertz Detection and Imaging”**, Invited –Pleanary paper 18th International Conference on Microwaves, Radar and Wireless Communications (MIKON-2010), Vilnius, Lithuania, June 14-18, 2010.
74. Taiichi Otsuji, Tsuneyoshi Komori, Takayuki Watanabe, Tetsuya Suemitsu, Dominique Coquillat, and Wojciech Knap, **“Plasmon-resonant microchip emitters and detectors for terahertz sensing and spectroscopic applications”**, Invited Paper, Proc. SPIE 7671, 767102, April 5-9, 2010
75. W. Knap, H. Videlier, S. Boubanga-Tombet , F. Teppe, D. Coquillat, N. Dyakonova, J. Łusakowski, K. Karpierz, **“Influence of High Magnetic Field and Gate Length on Terahertz Detection by Field Effect Transistors”**, NATO Vilnius 3&4 May2010, Invited Paper, SET159 Specialists Meeting on Terahertz and Other Electromagnetic Wave Techniques for Defence and Security", 3-4 May, 2010, Lithuania.
76. W. Knap, S. Nadar, H. Videlier, S. Boubanga-Tombet, M. Sakowicz, D. Coquillat, N. Dyakonova, F. Teppe, A. El Fatimy, T. Otsuji, Y. M. Meziani, K. Karpierz, J. Lusakowski, D. Seliuta, I. Kasalynas, G. Valusis, G. M. Tsymbalov, and V. V. Popov **“Field Effect Transistors for Terahertz Detection”** Invited paper TeraTech'09: The Int. Workshop on Terahertz Technology 2009, Osaka, Japan, Nov. 30-Dec. 3, 2009.
77. W. Knap, J. Lusakowski **“Comparison of silicon versus III-V semiconductor material choice for terahertz imaging with fast field effect transistors based detectors”** 2009 E-MRS Fall Meeting, Warsaw, Poland September, 2009
78. W. Knap **“Bulk nitrides based heterojunctions for Terahertz detection and emission”** 6th International Workshop on Bulk Semiconductors Galindia, Poland, August 2009
79. Knap W., Popov V. **“Terahertz Nanotransistors”** 15th Int. Symposium,on Nano Structures Physics, Novosibirsk, Russia 25-29 June, 2007
80. W. Knap **“Nanotransistors for Plasmonics Tutorial”** - International Conf. on Physics of Semiconductors Jaszowiec Poland June 2009
81. W. Knap **“Field Effect Transistors for Terahertz Imaging”** 15th Semiconducting and Insulating Materials Conference, June 15-19, 2009, Vilnius, Lithuania.
82. K. K. Oh, M. F. Chang, M. Shur, W. Knap **"Sub-Millimeter Wave Signal Generation and Detection in CMOS"** International Microwave Symposium 2009 (IMS 2009) Boston, Massachusetts, June 2009
83. D. Shim, C. Mao, R. Han, S. Sankaran, E. Seok, C. Cao, W. Knap, **“Paths to Terahertz CMOS Integrated Circuits”** 2009 IEEE Custom Integrated Circuits Conference -CICC 2009 San Jose, USA, September 2009
84. W. Knap **“Plasma waves in nanotransistors working as terahertz detectors and emitters”**, International Workshop on Semiconductor and Carbon based nanostructures in magnetic fields Grenoble, November 2008
85. W. Knap, T. Otsuji **“Terahertz detector and sources based on nanotransitors and multigrating structures”** The International Conference on Lasers and Electro-Optics (CLEO) San José, 4-8 may, 2008
86. W. Knap, T. Otsuji, Y. Mezziani **“Nanotransistors for Terahertz Integrated Sources and Detectors”** Int. Conf. on Integrated Quantum Electronics (RCIQE), Hokkaido University, Sapporo, Japan, March 2008.
87. W. Knap **“Review on Terahertz Nanotransistors”** International Workshop of Semiconductor, Ekaterinburg, Russia 2006
88. W. Knap **“Nitrides based nanotransistors for Terahertz applications”** European Conf. on III-Nitride Semiconductor Materials and Devices, Crete, Grece, 2006
89. W. Knap **“Nanostructures for Terahertz emission and imaging”** 16th International Conference on Microwaves, Radar and Wireless Communications (MIKON-2006), Krakow, Poland, May, 2006
90. KNAP W. **“Plasma oscillations in submicron field effect transistors for THz detection”** International Conf. on Nanophotonics-2003, Nizhny Novgorod, Russia, 17-20 March, 2003
91. KNAP W., SHUR M. **“Terahertz plasma wave electronics”** SPIE-East Meeting, Philadelphia, October 25-29, 2004.
92. KNAP W. **“Terahertz generation and detection by plasma waves in nanometer gate high electron mobility transistors”** 12th International Symposium on Ultrafast Phenomena in Semiconductors, Vilnius, Lithuania, August, 22-25, 2004.
93. LUSAKOWSKI J., KNAP W. **“Semiconductor nanometric transistors for terahertz oscillations”** The 7-th International Conference-School on Advanced Materials and Technologies, August 27-31, 2005, Palanga, Lithuania
94. KNAP W., LUSAKOWSKI J., TEPPE F., DYAKONOVA N. **„Terahertz emission by plasma waves in high electron mobility transistors”** Topical Workshop on Heterostructure Microelectronics ,Hyogo, Japon August 22-25, 2005
95. KNAP W. **“Terahertz Nanotransistors”** 14th International Conference on Nonequilibrium Carrier Dynamics in Semiconductors (HCIS 14), Chicago, July 24-29, 2005
96. LUSAKOWSKI J., KNAP W., DYAKONOVA N. **„Nanometre Transistors for Emission and Detection of THz Radiation”** 3rd International Conference on Materials for Advanced Technologies (ICMAT 2005) and 9th International Conference on Advanced Materials (ICAM 2005), 3-8 July 2005, Singapore
97. W. Knap **“Terahertz nanotransistors: plasma oscillations and ballistic effects”** Russian-French Workshop on Nanosciences and Nanotechnolgies, Lille, August 2005
98. W. Knap Nanometer **“Silicon MOSFET Transistors for Terahertz detection”** MRS, Boston, November 2006, USA.
99. W. KNAP **“Terahertz Emission and detection from Nanotransistors”** Keynote International Conference on Infrared and Millimetre Waves, Shanghai, China, September 2006.
100. KNAP W. ,SKIERBISZEWSKI C. **“Plasma oscillations in 2 DEG in GaN /AlGaN heterojunctions”** International Conference on bulk III-N Semiconductors, Brasil, July 2007.
101. W. Knap **“Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures”** 2002 E-MRS Fall Meeting and 5th International Workshop on Molecular Beam Epitaxy & Vapor Phase Epitaxy Growth Physics and Technology, Warsaw, Poland, 15-19 September, 2002.
102. W. Knap **“Nanometre scale silicon FETs - Physical versus technological limits”** French-Russian Seminars on Nanotechnologies, Moscow, June 2004
103. W. Knap **“High magnetic field studies of GaN/AlGaN heterostructures on bulk substrates”** International Conf. on bulk III-N Semiconductors – Zakopane, Poland, September 2004
104. W. Knap **“Magneto-transport Characterization of the nanometer silicon MOSFETs”** Workshop ST-CNRS on Micro and Nanotechnologies, Crolles, December 2003..
105. KNAP W., SKIERBISZEWSKI C., DYBKO K., LUSAKOWSKI J., SIEKACZ M., GRZEGORY I., POROWSKI S. **„Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures”** International Workshop on Bulk Nitride Semiconductors, Amazonas, Brazil, 18-23/05/2002
106. W. Knap **“Conduction band Energy Spectrum of Two Dimensional Electrons in GaN/AlGaN Heterojunctions”** The Third International Conference on Nitride Semiconductors ICNS3, Montpellier France, July 1999.
107. W. Knap **“Cyclotron resonance emission and absorption in 2D gas in GaN/GaAlN heterostructures - nonparabolicity and polaron effects”** INTERNATIONAL WORKSHOP ON NANOFOTONICS, Nizhny Novgorod, Russia, 15-18 March, 1999
108. W. Knap, E. Borovitskaya, M. Shur, and R. Gaska G. Karczewski B. Brandt et al **“HIGH MAGNETIC FIELD STUDIES OF AlGaN/GaN HETEROSTRUCTURES GROWN ON BULK GaN, SiC, AND SAPPHIRE SUBSTRATES”** Material Research Society Meeting MRS, Boston, November 2000
109. P. Perlin, W. Knap, A. Polian, J. L. Chervin, J. Camassel et al **“Metal - Insulator Transition in GaN crystals”** 7th Int. Conf. on High Pressure in Sem. Physics, Schwabisch Gmund, Germany 1996
110. W. Knap, A. Zduniak, L.H. Dmowski, M. Dyakonov, S. Contreras **“Study of Quantum and Classical Scattering Times in Pseudomorphic AlGaAs/InGaAs/GaAs by Means of Pressure”** 7th Int.Conf.on High Pressure in Sem. Physics, Schwabisch Gmund, Germany 1996
111. W. Knap. C. Skierbiszewski, C. Chaubet, M. Goiron, J. Leotin **“Cyclotron resonance emission and absorption in 2D gas in GaN/GaAlN heterostructures - nonparabolicity and polaron effects”** International Workshop on NANOFOTONICS, Nizhny Novgorod, Russia, 15-18 March, 1999
112. W. Knap, G.E. Pikus, A.L. Barra, G. Martinez **“Dynamic Nuclear Polarisation in High Field EPR in Si:P”** International Workshop on High-Field Electron Paramagnetic Resonance, Aussois (Savoie), April 11-13, 1996
113. E. Gornik, M. Witzany, K. Unterrainer, W. Knap **“FIR emission spectroscopy: history, state of the art and future aspects”** 14th International Conference on Infrared and Millimeter Waves, Wurzburg, Germany (1989)
114. S. Huant, S.P. Najda, W. Knap, G. Martinez, B. Etienne **„Impurity States and Phenomena in Quantum Wells: Two Dimensional D centers and Tunable Resonant Polaron Strenght”** 20-th Inernational Conference on the Physics of Semiconductors, Thesaloniki, Grece, 1990,
115. A. Raymond, C. Chauvet, D. Dur, W. Knap,W. Zawadzki **“Far infrared properties of GaAs GaAlAs heterojunctions controlled by metastable states under pressure”** V Int. Conf. on High Pressure in Semiconductor Physics, HPSP, Kyoto, Japan, 1992
116. J. Leotin, W. Knap, G. Sirmain, C. Meny, P. Etieve **“Far infrared photoconductors for spaceborn experiments”** Int. Conf. on Millimeter Wawes and Far Infrared Technology, Beijing, Chine, 1992
117. W. Knap, D. Dur, A. Raymond **“Far infrared spectroscopy based on magnetically tunable emitters, filters and detectors”** 18-th Int. Conf. on Infrared and Millimeter Waves, Colchester, Great Britain, 1992

**5.3 CONFERENCES (296)**

**2020**

1. Dub, M.; Sai, P.; But, D.B.; Jorudas, J.; Kašalynas, I.; Sakowicz, M.; Cywinski, G.; Rumyantsev, S.; Knap, W. In ***Anomalous sub-THz detection by GaN/AlGaN FinFETs***, 23rd International Microwave and Radar Conference (MIKON), Warsaw, Poland, 5–8 Octobre 2020.
2. But, D.B.; Javadi, E.; Knap, W.; Ikamas, K.; Lisauskas, A. In ***Silicon based resonant power detector for 620 GHz***, 23rd International Microwave and Radar Conference (MIKON), Warsaw, Poland, 5–8 Octobre 2020.
3. Gorbenko, I.V.; Kachorovskii, V.Y.; Knap, W. In ***Current-driven optical response of plasmonic crystal: From dissipation to amplification***, XVIII Plasmonics: Design, Materials, Fabrication, Characterization, and Applications, Virtual/Online, United States, 24 August – 4 September 2020.
4. Boubanga-Tombet, S.A.; Yadav, D.; Satou, A.; Knap, W.; Popov, V.V.; Otsuji, T. In ***Terahertz gain and amplification in current-driven metasurfaces of graphene Dirac plasmons***, Terahertz Photonics, Virtual/Online, France; 6–10 April 2020.
5. Sai, P.; But, D.B.; Cywinski, G.; Dub, M.; Sakowicz, M.; Prystawko, P.; Rumyantsev, S.; Knap, W. In ***Sub-terahertz detection by fin-shaped GaN/AlGaN transistors***, XIII Terahertz, RF, Millimeter, and Submillimeter-Wave Technology and Applications, San Francisco, United States, 3–6 February 2020.
6. Wu, K.; Shafee, M.; Le Bars, P.; Sahyoun, W.; Blin, S.; Ducournau, G.; Knap, W.; Hella, M.M. In ***A 300 GHz Data Communication Receiver Using Plasma-Wave FET Detector in 65nm CMOS***, 2020 IEEE Radio and Wireless Symposium (RWW 2020), San Antonio; United States, 26–29 January 2020.

**2019**

1. Boubanga-Tombet, S.; Yadav, D.; Watanabe, T.; Satou, A.; Knap, W.; Popov, V. V.; Ryzhii, V.; Otsuji, T. In ***Terahertz Light Amplification of Stimulated Emission of Radiation in Current-Injection Graphane Channel Transistor***, Micro- and Nanotechnology (MNT) Sensors, Systems, and Applications XI Conference, Baltimore, United States, 14–18 April 2019.
2. Skotnicki, T.; Knap, W. In ***Terahertz technologies and applications***, 26th International Conference "Mixed Design of Integrated Circuits and Systems" (MIXDES), Rzeszów, Poland, 27–29 June 2019.
3. Zagrajek, P.; Danilov, S.; Marczewski, J; Zaborowski, M.; Kolacinski, C.; Obrebski, D.; Kopyt, P.; But, D.; Knap, W.; Ganichev, S. In ***Time Resolution and Power Dependence of Transistor Based Terahertz detectors***, 44th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Paris, France, 1–6 September 2019.
4. Zhao, Y.; But, D. B.; Georges, M.; Knap, W. In ***Terahertz Digital Holography Using Field-Effect Transistor Detectors***, 44th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Paris, France, 1–6 September 2019.
5. Sai, P.; But, D. B.; Dub, M.; Sakowicz, M.; Grzywacz, B.; Prystawko, P.; Cywinski, G.; Knap, W.; Rumyantsev, S. In ***Electrical and noise characterystics of fin-shaped GaN/AlGaN devices for high frequency operation***, 49th European Solid-State Devices Research Conference (ESSDERC), Cracow, Poland, 23–26 September 2019.
6. *(oral)*W. Knap, et al, ***"Towards Resonant THz Detectors Devices Based on Schottky Diodes to 2DEG GaN/AlGaN"***, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May 2018
7. *(oral)* W. Knap, et al, ***"AlGaN/GaN field effect transistor with lateral Schottky barrier gate as sub-millimeter detector"***, 47th International School & Conference on the Physics of Semiconductors Jaszowiec, Szczyrk, Poland, 16–22 June 2018
8. *(oral)*W. Knap, et al, ***"Millimeter Band Detectors Based on GaN/AlGaN HEMT"***, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May 2018
9. *(oral)*W. Knap, et al, ***"Millimeter and Submillimeter Range Detector Based on Graphene Ballistic Rectifiers"***, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May 2018
10. *(oral)*W. Knap, et al, ***"Magneto-optics of electrons in conical bands"***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop, Warsaw, Poland, 17–21 September 2018
11. *(oral)*W. Knap, et al, ***"Massless Dirac fermions in III-V semiconductor quantum wells"***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop, Warsaw, Poland, 17–21 September 2018
12. *(oral)* **W. Knap**, et al, ***"Temperature-dependent Landau level spectroscopy of HgCdTe and InAs/GaSb based topological materials"***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop, Warsaw, Poland, 17–21 September 2018
13. *(invited)* W. Knap et al. ***"Presentation of IRAP CENTERA"****,* CENTERA THz DAYS, French-Polish THz Science and Technology Meeting Warsaw, Poland, 15–16 October 2019

**2018**

1. Cywiński, G.; Sai, P.; But, D. B.; Yahniuk, I.; Grabowski, M.; Sakowicz, M.; Kruszewski*,* P. et al. In ***GaN-Based Transistors for Thz Radiation Detection***, XXII Symposium “Nanophysics and Nanoelectronics”, Nizhny Novgorod, Russia, 12–15 March, 2018.
2. But, D. B.; Auton, G.; Consejo, C.; Zhang, J.; Hill, E.; Coquillat, D.; Teppe, F.; Knap, W.; Varani, L.; Torres, J.; Song, A. In ***Millimeter range detector based on Graphene Ballistic Rectifiers***, 6th EOS Topical Meeting on Terahertz Science & Technology (TST 2018), Berlin, Germany, 6–9 May 2018.
3. Sai, P.; Cywiński, G.; Yahniuk, I.; But, D. B.; Przybytek, J.; Nowakowski-Szkudlarek, K.; Prystawko, P.; Knap, W.; Simin, G. S.; Wiśniewski, P.; Stonio, B.; Rumyantsev, S. L. In ***Towards electrically driven sub-THz GaN/AlGaN based detector***, 6th EOS Topical Meeting on Terahertz Science & Technology (TST 2018), Berlin, Germany, 6–9 May 2018.
4. Boubanga-Tombet, S.; Yadav, D.; Knap, W.; Popov, V. V.; Otsuji, T. In ***Terahertz light amplification by current-driven plasmon instabilities in graphene***, CLEO: Science and Innovations, San Jose, United States, 13–18 May 2018.
5. But, D. B.; Auton, G.; Consejo, C.; Zhang, J.; Hill, E.; Coquillat, D.; Teppe, F.; Knap, W.; Varani, L.; Torres, J.; Song, A. In ***Millimeter and submillimeter range detector based on Graphene Ballistic Rectifiers***, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May 2018.
6. But, D. B.; Cywiński, G.; Sai, P.; Yahniuk, I.; Dyakonova, N.; Knap, W.; Bo-Wen, Z.; Wei, Y.; Zhao-Feng, L.; Fu-Hua, Y. In ***Millimetre band detectors based on GaN/AlGaN HEMT***, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May 2018.
7. Cywiński, G.; Sai, P.; Yahniuk, I.; Kruszewski, P.; Grzywacz, B.; Przybytek, J.; Prystawko, P.; Khachapuridze, A.; Wiśniewski, P.; Stonio, B.; Simin, G. S.; Nowakowski-Szkudlarek, K.; Rumyantsev, S. L.; Knap, W. In ***Towards Resonant THz Detector: Devices Based on Schottky Diodes to 2DEG GaN/AlGaN***, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland 15–17 May 2018.
8. Dyakonova, N.; Coquillat, D.; Teppe, F.; Suszek, J.; Siemion, A.; Sypek, M.; But, D. B.; Sai, P.; Yahniuk, I.; Cywiński, G.; Marczewski, J.; Zaborowski, M.; Tomaszewski, D.; Zagrajek, P.; Knap, W. In ***Terahertz Vision Using Field Effect Transistors Detectors Arrays***, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May 2018.
9. Sai, P.; But, D.B.; Prystawko, P.; Yahniuk, I.; Nowakowski-Szkudlarek, K.; Przybytek, J.; Rumyantsev, S.L.; Knap, W.; Cywiński, G. In ***AlgaN/GaN Field Effect Transistor with Lateral Schottky Barrier Gate as Sub-Millimeter Detector***, 47th International School & Conference on the Physics of Semiconductors Jaszowiec, Szczyrk, Poland, June 16–22 June 2018.
10. Yahniuk, I.; Krishtopenko, S.S.; Grabecki, G.; Teppe, F.; Jouault, B.; But, D.; Cywiński, G., Knap, W.; Przybytek, J.; Majewicz, M.; Gavrilenko, V.I.; Dvoretsky, S. A., Mikhailov, N. N.; Wróbel, J.; Dietl, T. In ***Pressure-Induced Topological Phase Transition in Hgte Quantum Wells***, 47th International School & Conference on the Physics of Semiconductors, Jaszowiec, Szczyrk, Poland, 16–22 June, 2018.
11. Bąk, M.; Yavorskiy, D.; Karpierz, K.; Łusakowski, J.; But, D.; Przybytek, J.; Yahniuk, I.; Cywiński, G.; Knap, W.; Teppe, F.; Krishtopenko, S.; Mikhailov, N. N.; Dvoretsky, S. A.; Gavrilenko, V. I. In ***Magnetocondutivity of a Resonant Terahertz Detector Based on a Mercury Cadmium Telluride Epitaxial Layer***, 47th International School & Conference on the Physics of Semiconductors, Jaszowiec, Szczyrk, Poland, 16–22 June, 2018.
12. Majewicz, M.; Wróbel, J.; Grabecki, G.; Nowicki, P.; Szyller; Ł.; Mikhailov, N. N.; Dvoretskii, S. A.; Knap, W.; Teppe, F.; Dietl, T. In ***Influence of the Microstructure Shape on Edge Channel Resistance in HgTe/(Hg,Cd)Te Quantum Wells***, 47th International School & Conference on the Physics of Semiconductors, Jaszowiec, Szczyrk, Poland, 16–22 June, 2018.
13. Boubanga -Tombet, S.; Yadav, D.; Knap, W.; Popov, V. V.; Otsuji, T. In ***Graphene-Channel-Transistor Terahertz Amplifier***, 76th Device Research Conference (DRC), Santa Barbara, United States, 24–27 June 2018.
14. Abbès, A.; Paquet, R.; Chomet, B.; Garnache, A.; Myara, M.; Nouvel, P., Pénarier, A. Beaudoin, G.; Sagnes, I.; Coquillat, D.; Knap, W.; Blin, S. In ***Towards Wireless Thz Communications: Photonic-Driven Source and Transistor-Based Detector***, 25th International Conference on Telecommunications (ICT), Saint Malo, France, 26–28 June 2018.
15. Cywiński, G.; Yahniuk, I.; Kruszewski, P.; Grabowski, M.; Nowakowski-Szkudlarek, K.; Prystawko, P.; Sai, P.; Knap, W.; Simin, G. S.; Rumyantsev, S. L. In ***Low Frequency Noise in Wire-Channel GaN/AlGaN Transistors***, 8th International Conference on Unsolved Problems on Noise, Gdańsk University of Technology, Gdańsk, Poland 9–13 July 2018.
16. Knap, W. In ***New GaN FETs and Silicon Junctionless Field Effect Transistors as Terahertz Detectors***, International Workshop on frontiers of photonics, plasmonics and electronics with 2D nanosystems, Erice, Sicily, Italy, 14–20 July, 2018.
17. Boubanga-Tombet, S.; Yadav, D.; Knap, W.; Popov, V. V.; Otsuji, T. In ***Terahertz Light Amplification by Instability-Driven Stimulated Emission of Graphene Plasmon Polaritons***, 43rd International Conference on Infrared, Millimeter and Terahertz Waves (IRMMW - THz 2018), Nagoya, Japan, 9–14 September 2018.
18. Kadykov, A. M.; Krishtopenko, S. S.; Jouault, B.; Desrat, W.; Marcinkiewicz, M.; Ruffenach, S.; Consejo, C.; Torres, J.; Morozov, S. V.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretskii, S. A.; Knap, W.; Teppe, F. In ***Spectroscopy of Temperature-Driven Single Valley Dirac Fermions in HgTe/CdHgTe Quantum Wells****,* 43rd International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Nagoya, Japan, 9–14 September 2018.
19. Knap, W.; Marczewski, J.; Zaborowski, M.; Tomaszewski, D.; Zagrajek, P.; But, D. B.; Sai, P.;Yahniuk, I.; Dyakonova, N.; Coquillar, D.; Teppe, F.; Cywiński, G. In ***Field Effect Transistors Based Terahertz Detectors 25 Years History, State of the Art and Future Directions***, 43rd International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Nagoya, Japan, 9–14 September 2018.
20. Auton, G.; But, D.; Zhang, J.; Hill, E.; Coquillat, D.; Consejo, C.; Nouvel, P.; Knap, W.; Varani, L.; Teppe, F.; Torres, J.; Song, A. In ***Graphene Ballistic Rectifiers for Thz Detection and Imaging***, 43rd International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Nagoya, Japan, 9–14 September 2018.
21. Coquillat, D.; Dyakonova, N.; Consejo, C.; Meriguet, Y.; Torres, J.; Teppe, F.; Nodjiadjim*,* V. Konczykowska, A.; Riet, M.; Verdeil, J.-L.; Knap, W. In ***Terahertz InP DHBT-Based Detectors for Studies of Water Status of Sorghum Leaves***, 43rd International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Nagoya, Japan, 9–14 September 2018.
22. Sai, P.; But, D. B.; Nowakowski-Szkudlarek, K.; Przybytek, J.; Prystawko, P.; Yahniuk, I.; Wisniewski*,* P.; Stionio, B.; Slowikowski, M.; Rumyantsev, S. L.; Knap, W.; Cywiński, G. In ***AlGaN/GaN Field Effect Transistors Based on Lateral Schottky Barrier Gates as Millimeter Wave Detectors***, 43rd International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Nagoya, Japan 9–14 September 2018.
23. Krishtopenko, S. S.; Desrat, W.; Consejo, C.; Ruffenach, S.; Jouault, B; Knap, W.; Zaknoune, M.; Gonzalez-Posada, F.; Boissier, G.; Torres, J.; Spirin, K. E.; Maremyanin, K. V.; Gavrilenko, V. I.; Tounie, E.; Teppe, F. In ***Massless Dirac Fermions in III-V Semiconductor Quantum Wells***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop (RJUSE 2018), Warsaw, Poland, 17–21 September 2018.
24. Orlita, M.; Faugeras, C.; Potemski, M.; Mittendorff, M.; Winnerl, S.; Heml, M. But, D.; Consejo, C.; Teppe, F.; Knap, W.; Mikhailov, N.; Dvoretskii, S.; Berger, C.; de Heer, W. A. In ***Magneto-Optics of Electrons in Conical Bands***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop (RJUSE 2018), Warsaw, Poland, 17–21 September 2018.
25. Otsuji, T.; Yadav, D.; Boubanga-Tombet, S.; Watanabe, T.; Satou, A.; Dubinov, A. A.; Ryzhii*,* M.; Popov, V. V.; Knap, W.; Mitin, V.; Shur, M. S.; Ryzhii, V. In ***Emission and Amplification of Terahertz Radiation Using Dirac Fermions and Plasmons in Graphene***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop (RJUSE 2018) Warsaw, Poland, 17–21 September 2018.
26. Sai, P.; But, D. B.; Nowakowski-Szkudlarek, K.; Przybytek, J.; Prystawko, P.; Yahniuk, I.; Stonio*,* B.; Słowikowski, M.; Rumyantsev, S. L.; Knap, W.; Cywiński, G. In ***EdgeFET Based on AlGaN/GaN with Two Lateral Schottky Barrier Gates Towards Resonant Terahertz Detection***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop (RJUSE 2018) Warsaw, Poland, 17–21 September 2018.
27. Teppe, F.; Krishtopenko, S. S.; Ruffenach, S.; Marcinkiewicz, M.; Kadykov, A.; Jouault, B.; Desrat*,* W.; Consejo, C.; Fadeev, M.; Orlita, M.; Torres, J.; Maussang, K.; Gonzalez-Posada, F.; Boissier, G.; Morozov, S. V.; Gavrilenko, V. I.; Michailov, N. N.; Dvoretskii, S. A.; Zaknoune, M.; Knap, W.; Tournie, E. In ***Landau Level Spectroscopy of HgCdTe and InAs/GaSb Based Topological Materials***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop (RJUSE 2018) Warsaw, Poland, 17–21 September 2018.
28. Yahniuk, I.; Krishtopenko, S.; Grabecki, G.; Consejo, C.; Jouault, B.; Kadykov, A. M.; Majewicz*,* M.; Cywiński, G.; Wróbel, J.; Gavrilenko, V. I.; Dietl, T.; Dvoretsky, S. A.; But, D. B.; Przybytek, J.; Teppe, F.; Knap, W. In ***Topological Phases of HgTe Quantum Wells for Qhe Resistance Standard Applications***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop (RJUSE 2018) Warsaw, Poland, 17–21 September 2018.

Zagrajek, P.; Marczewski, J.; Zaborowski, M.; Kopyt, P.; Kucharski, K.; Pałka, N.; Knap, W. In ***Terahertz Activity in Warsaw: Detectors, Spectroscopy, Imaging***, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop (RJUSE 2018) Warsaw, Poland, 17–21 September 2018.Skotnicki, T,; Knap, W. In ***Emerging Terahertz Technologies for Security, Quality Control, Vision and Medical Applictions***, 14th IEEE International Conference on Solid-State and Integrated Circuit Technology (ICSICT), Qingdao, China, 31 October–3 November 2018.

**2017**

1. Cywiński, G.; Yahniuk, I.; Szkudlarek, K.; Kruszewski, P.; Muzioł, G.; Skierbiszewski, C.; Khachapuridze, A.; Knap, W.; But, D.; Rumyantsev, S. L. In ***Noise limitations of GaN lateral Schottky diodes for THz applications***, 2017 International Conference on Noise and Fluctuations (ICNF), Vilnius, Lithuania 20-23 June 2017.
2. Dyakonova, N.; Coquillat, D.; But, D.; Consejo, C.; Teppe, F.; Knap, W.; Varani, L.; Blin, S.; Nodjiadjim, V.; Konczykowska, A.; Riet, M. In ***Reducing noise equivalent power in InP DHBT terahertz detector by biasing the collector***, International Conference on Noise and Fluctuations Vilnius, Lithuania 20-23 June 2017.
3. Knap, W.; Cywinski, G.; Sypek, M.; Dyakonova, N.; Coquillat, D.; Szkudlarek, K.; Yahniuk, I.; Archier, C.; Moulin, B.; Triki, M.; Hella, M. M.; Nodjiadjim, V.; Riet, M.; Konczykowska, A. In ***THz imaging and wireless communication using nanotransistor based detectors: From basic physics to first real world applications***, 19th International Conference on Transparent Optical Networks (ICTON), , Girona, Spain, 2-6 July 2017.

**2016**

1. But, D. B.; Consejo, C.; Krishtopenko, S. S.; Dyakonova, N.; Kadykov, A. M.; Michailov, N. N.; Dvoretskii, S. A.; Gavrilenko, V. I.; Morozov, S. V.; Teppe, F.; Knap, W. In ***Terahertz cyclotron emission from HgCdTe bulk films***, 41st International Conference on Infrared, Millimeter, and Terahertz Waves, IRMMW-THz, Copenhagen, DENMARK, SEP 25-30, 2016.
2. But, D. B.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Ruffenach, S.; Knap, W.; Kopyt, P.; Marczewski, J. In ***Substrate optimization for a planar antenna of terahertz Si field effect transistor detectors***, 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, Krakow, POLAND, MAY 09-11, 2016.
3. Ceolato, R.; Tanguy, B.; Martin, C.; Huet, T.; Chervet, P.; Durand, G.; Riviere, N.; Hespel, L.; Diakonova, N.; But, D.; Knap, W.; Meilhan, J.; Delplanque, B.; Oden, J.; Simoens, F. In ***Performance evaluation of active sub-Terahertz systems in Degraded Visual Environments (DVE)***, Conference on Degraded Visual Environments - Enhanced, Synthetic, and External Vision Solutions, Baltimore, MD, APR 19-20, 2016.
4. Cywiński, G.; Szkudlarek, K.; Yahniuk, I.; Yatsunenko, S.; Kruszewski, P.; Muziol, G.; Skierbiszewski, C.; Knap, W.; Rumyantsev, S.; But, D. In ***GaN/AlGaN lateral schottky barrier diodes for high frequency applications***, 2016 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, Krakow, POLAND, 9-11 May 2016.
5. Cywiński, G.; Szkudlarek, K.; Yahniuk, I.; Yatsunenko, S.; Siekacz, M.; Skierbiszewski, C.; But, D. B.; Coquillat, D.; Dyakonova, N.; Knap, W. In ***GaN/AlGaN based transistors for terahertz emitters and detectors***, 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, Krakow, Poland 9-11 May 2016.
6. Cywinski, G.; Yahniuk, I.; Szkudlarek, K.; Kruszewski, P.; Yatsunenko, S.; Muzioł, G.; Skierbiszewski, C.; But, D.; Knap, W. In ***Lateral Schottky barrier diodes based on GaN/AlGaN 2DEG for sub-THz detection***, Proceedings of the 23rd International Conference Mixed Design of Integrated Circuits and Systems, MIXDES 2016, Lodz, POLAND, JUN 23-25, 2016.
7. Dyakonova, N.; Coquillat, D.; But, D. B.; Teppe, F.; Knap, W.; Faltermeier, P.; Olbrich, P.; Ganichev, S. D.; Szkudlarek, K.; Cywinski, G. In ***Terahertz detection by AlGaN/GaN HEMTs at high intensity***, 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, Krakow, POLAND, MAY 09-11, 2016.
8. Gayduchenko, I. A.; Fedorov, G. E.; Stepanova, T. S.; Titova, N.; Voronov, B. M.; But, D.; Coquillat, D.; Diakonova, N.; Knap, W.; Goltsman, G. N. In ***Asymmetric devices based on carbon nanotubes as detectors of sub-THz radiation***, 3rd International School and Conference on Optoelectronics, Photonics, Engineering and Nanostructures (Saint Petersburg OPEN), Russian Acad Sci, St Petersburg Acad Univ, St Petersburg, RUSSIA, MAR 28-30, 2016.
9. Knap, W.; But, D.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Sypek, M.; Suszek, J.; Cywinski, G.; Szkudlarek, K.; Yahniuk, I.; Yatsunenko, S. In ***Terahertz imaging by field effect transistors***, 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, Krakow, POLAND, MAY 09-11, 2016.
10. Knap, W.; But, D. B.; Dyakonova, N.; Coquillat, D.; Teppe, F.; Suszek, J.; Siemion, A. M.; Sypek, M.; Szkudlarek, K.; Cywinski, G.; Yahniuk, I. In ***Terahertz imaging with GaAs and GaN plasma field effect transistors detectors***, 23rd International Conference Mixed Design of Integrated Circuits and Systems, MIXDES 2016, Lodz, POLAND, JUN 23-25, 2016.
11. Knap, W.; Sypek, M.; But, D.; Coquillat, D.; Suszek, J.; Szkudlarek, K.; Siemion, A.; Cywinski, G.; Dyakonova, N.; Teppe, F. In ***Terahertz imaging with arrays of plasma field effect transistors detectors***, 41st International Conference on Infrared, Millimeter, and Terahertz Waves, IRMMW-THz, Copenhagen, DENMARK, SEP 25-30, 2016.
12. Marcinkiewicz, M.; Krishtopenko, S. S.; Ruffenach, S.; Consejo, C.; But, D.; Kadykov, A. M.; Fadeev, A. M.; Morozov, S. V.; Michailov, N. N.; Dvoretskii, S. A.; Gavrilenko, V. I.; Knap, W.; Teppe, F. In ***THz magnetospectroscopy of double HgTe quantum well***, International Conference on Infrared, Millimeter, and Terahertz Waves, IRMMW-THz, Copenhagen, DENMARK, SEP 25-30, 2016.
13. Suszek, J.; Sypek, M.; Siemion, A.; Nowakowska-Siwińska, A.; Zagrajek, P.; Cywinski, G.; Szkudlarek, K.; Yahniuk, I.; Yatsunenko, S.; But, D. B.; Coquillat, D.; Knap, W. In ***Diffractive optics for GaN terahertz detectors arrays***, 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, Krakow, POLAND, MAY 09-11, 2016.
14. Teppe, F.; Marcinkiewicz, M.; Krishtopenko, S. S.; Ruffenach, S.; Consejo, C.; Kadykov, A. M.; Desrat, W.; But, D.; Knap, W.; Ludwig, J. In ***Temperature-driven massless Kane fermions in HgCdTe crystals***, 41st International Conference on Infrared, Millimeter, and Terahertz Waves, IRMMW-THz, Copenhagen, DENMARK, SEP 25-30, 2016.
15. Triki, M.; Duhant, A.; Poulin, C.; Moulin, B.; Archier, C.; Antonini, T.; Teppe, F.; Knap, W. In ***Real-time nondestructive imaging with THz waves***, 21st International Conference on Microwave, Radar and Wireless Communications (MIKON), Krakow, POLAND, 9-11 May 2016.
16. Viti, L.; Hu, J.; Coquillat, D.; Politano, A.; Consejo, C.; Knap, W.; Vitiello, M. S. In ***Black phosphorus and hybrid van der wall heterostructured terahertz photodetectors***, International Conference on Infrared, Millimeter, and Terahertz Waves, IRMMW-THz, Copenhagen, DENMARK, SEP 25-30, 2016.

**2015**

1. Bovkun, L. S.; Krishtopenko, S. S.; Zholudev, M. S.; Ikonnikov, A. V.; Spirin, K. E.; Dvoretsky, S. A.; Mikhailov, N. N.; Teppe, F.; Knap, W.; Gavrilenko, V. I. In ***Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells***, XIX Symposium “Nanophysics and Nanoelectronics”, Nizhny Novgorod, RUSSIA, MAR 10-14, 2015.
2. Coquillat, D.; Marczewski, J.; Kopyt, P.; Dyakonova, N.; Ruffenach, S.; But, D.; Teppe, F.; Schuster, F.; Giffard, B.; Knap, W. In ***Experimental and theoretical investigations of the responsivity of field effect transistors based Terahertz detectors versus substrate thickness***, 40th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Chinese Univ Hong Kong, Hong Kong, PEOPLES R CHINA, AUG 23-28, 2015.
3. Coquillat, D.; Nodjiadjim, V.; Konczykowska, A.; Dyakonova, N.; Consejo, C.; Ruffenach, S.; Teppe, F.; Riet, M.; Muraviev, A.; Gutin, A.; Shur, M.; Godin, J.; Knap, W. In ***InP double heterojunction bipolar transistor for detection above 1 THz***, 40th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Chinese Univ Hong Kong, Hong Kong, PEOPLES R CHINA, AUG 23-28, 2015.
4. Desrat, W.; Consejo, C.; Teppe, F.; Contreras, S.; Marcinkiewicz, M.; Knap, W.; Nateprov, A.; Arushanov, E. In ***Non-trivial Berry phase in the Cd 3 As 2 3D Dirac semimetal***, 19TH INTERNATIONAL CONFERENCE ON ELECTRON DYNAMICS IN SEMICONDUCTORS, OPTOELECTRONICS AND NANOSTRUCTURES (EDISON' 19), JUN 29-JUL 02, 2015.
5. Fedorov, G. E.; Gaiduchenko, I. A.; Golikov, A. D.; Rybin, M. G.; Obraztsova, E. D.; Voronov, B. M.; Coquillat, D.; Diakonova, N.; Knap, W.; Goltsman, G. N. In ***Response of Graphene Based Gated Nanodevices Exposed to THz Radiation***, XII International Workshop on Quantum Optics (IWQO-2015) Moscow, RUSSIA, AUG 11-16, 2015.
6. Kadykov, A.; Consejo, C.; Teppe, F.; Desrat, W.; Viti, L.; Vitiello, M. S.; Coquillat, D.; Ruffenach, S.; Morozov, S.; Kristopenko, S.; Marcinkiewicz, M.; Dyakonova, N.; Knap, W.; Gavrilenko, V.; Michailov, N. N.; Dvoretskii, S. A. In ***Terahertz excitations in HgTe-based field effect transistors***, 19th International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON '19), Universidad Salamanca, Hospederia Fonseca, Salamanca, SPAIN, JUN 29-JUL 02, 2015.
7. Kadykov, A. M.; Consejo, C.; Marcinkiewicz, M.; Viti, L.; Vitiello, M. S.; Krishtopenko, S. S.; Ruffenach, S.; Morozov, S. V.; Desrat, W.; Dyakonova, N.; Knap, W.; Gavrilenko, V. I.; Mikhailov, N. N.; Dvoretsky, S. A.; Teppe, F. In ***Observation of topological phase transition by terahertz photoconductivity in HgTe-based transistors***, 17th International Conference on II-VI Compounds and Related Materials (II-VI), Paris, FRANCE, SEP 13-18, 2015.
8. Kasuya, F.; Kawasaki, T.; Hatakeyama, S.; Tombet, S. B.; Suemitsu, T.; Otsuji, T.; Ducournau, G.; Coquillat, D.; Knap, W.; Takida, Y.; Ito, H.; Minamide, H.; Fateev, D. V.; Popov, V. V.; Meziani, Y. M.; Satou, A. In ***Broadband characteristics of ultrahigh responsivity of asymmetric dual-grating-gate plasmonic terahertz detectors***, 40th International Conference on Infrared, Millimeter, and Terahertz waves (IRMMW-THz), Chinese Univ Hong Kong, Hong Kong, PEOPLES R CHINA, 23-28 Aug. 2015.
9. Knap, W.; Coquillat, D.; Nodjiadjim, V.; Konczykowska, A.; Dyakonova, N.; Consejo, C.; Ruffenach, S.; Teppe, F.; Riet, M.; Muraviev, A.; Gutin, A.; Shur, M.; Godin, J. In ***InP Double Heterojunction Bipolar Transistor for broadband terahertz detection and imaging systems***, 19th International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON '19), Universidad Salamanca, Hospederia Fonseca, Salamanca, SPAIN, JUN 29-JUL 02, 2015.
10. Kowalski, M.; Coquillat, D.; Zagrajek, P.; Knap, W. In ***Improvement of terahertz imaging using lock-in techniques***, 40th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Conference Location: Chinese Univ Hong Kong, Hong Kong, PEOPLES R CHINA, AUG 23-28, 2015.
11. Marcinkiewicz, M.; Teppe, F.; Consejo, C.; Dyakonova, N.; Desrat, W.; Coquillat, D.; Ruffenach, S.; Knap, W.; Mikhailov, N. N.; Dvoretskii, S. A.; Gonzalez-Posada, F.; Rodriguez, J. B.; Tournié, E. In ***Terahertz studies of 2D and 3D topological transitions***, 19th International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON '19), Universidad Salamanca, Hospederia Fonseca, Salamanca, SPAIN, JUN 29-JUL 02, 2015.
12. Nahar, S.; Blin, S.; Pénarier, A.; Coquillat, D.; Knap, W.; Hella, M. M. In ***Characterization of integrated antenna-coupled plasma-wave detectors with wide bandwidth amplification in 130nm*** *CMOS*, IEEE MTT-S International Microwave Symposium (IMS), Phoenix, AZ, MAY 17-22, 2015.
13. Nahar, S.; Blin, S.; Pénarier, A.; Nouvel, P.; Coquillat, D.; Knap, W.; Hella, M. M. In ***Plasmonic detection of wide band modulated THz radiations in GaAs technology***, 40th International Conference on Infrared, Millimeter, and Terahertz waves (IRMMW-THz), Chinese Univ Hong Kong, Hong Kong, 23-28 Aug. 2015.
14. Spirin, K. E.; Krishtopenko, S. S.; Sadofyev, Y. G.; Drachenko, O.; Helm, M.; Teppe, F.; Knap, W.; Gavrilenko, V. I. In ***Cyclotron resonance in InAs/AlSb quantum wells in magnetic fields up to 45 T***, XIX Symposium “Nanophysics and Nanoelectronics”, Nizhny Novgorod, MAR 10-14, 2015.
15. Suszek, J.; Siemion, A.; Coquillat, D.; Nodjiadjim, V.; Konczykowska, A.; Riet, M.; Sobczyk, A.; Zagrajek, P.; Palka, N.; Czerwińska, E.; Błocki, N.; Kolodziejczyk, A.; Dyakonova, N.; Teppe, F.; Consejo, C.; Knap, W.; Sypek, M. In ***3D printed flat optics and InP heterojunction bipolar transistor based-detector for THz imaging***, 40th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Chinese Univ Hong Kong, Hong Kong, AUG 23-28, 2015.
16. Watanabe, T.; Kawasaki, T.; Satou, A.; Tombet, S. B.; Suemitsu, T.; Ducournau, G.; Coquillat, D.; Knap, W.; Minamide, H.; Ito, H.; Popov, V. V.; Meziani, Y. M.; Otsuji, T. In ***Room-temperature zero-bias plasmonic THz detection by asymmetric dual-grating-gate HEMT***, Conference on Terahertz, RF, Millimeter, and Submillimeter-Wave Technology and Applications VIII, San Francisco, CA, FEB 10-12, 2015.

**2014**

1. But, D. B.; Sakhno, M. V.; Oden, J.; Notake, T.; Dyakonova, N. V.; Coquillat, D.; Teppe, F.; Minamide, H.; Otani, C.; Knap, W. In ***Detection of high intensity thz radiation by field effect transistors***, 26th Int. Conf. on Indium Phosphide and Related Materials, Montpellier, France, , MAY 11-15, 2014.
2. Consejo, C.; Teppe, F.; Dyakonova, N.; Desrat, W.; Ruffenach, S.; Coquillat, D.; Knap, W.; Zholudev, M.; Rumyantsev, V.; Gavrilenko, V.; Morozov, S.; Mikhailov, N. N.; Dvoretskii, S. A. In ***Sub-terahertz photoconductivity of HgxCd1−xTe crystals with composition close to semiconductor-to-semimetal topological transition***, 39th International Conference Infrared, Millimeter, and Terahertz waves (IRMMW-THz), Tucson, AZ, USA 14-19 Sept. 2014.
3. Coquillat, D.; Nodjiadjim, V.; Konczykowska, A.; Riet, M.; Dyakonova, N.; Consejo, C.; Teppe, F.; Godin, J.; Knap, W. In ***InP double heterojunction bipolar transistor as sub-terahertz detector***, 39th International Conference Infrared, Millimeter, and Terahertz waves (IRMMW-THz), Tucson, AZ, USA SEP 14-19, 2014.
4. Coquillat, D.; Zagrajek, P.; Dyakonova, N.; Chrzanowski, K.; Marczewski, J.; Kurita, Y.; Satou, A.; Kobayashi, K.; Tombet, S. B.; Popov, V. V.; Suemitsu, T.; Otsuji, T.; Knap, W. In ***Detection of terahertz and mid-infrared radiations by InP-based asymmetric dual-grating-gate HEMTs***, The 39th International Conference Infrared, Millimeter, and Terahertz waves (IRMMW-THz), Tucson, AZ, USA, SEP 14-19, 2014.
5. Grigelionis, I.; Bialek, M.; Grynberg, M.; Czapkiewicz, M.; Kolkovski, V.; Wiater, M.; Wojciechowski, M.; Wróbel, J.; Wojtowicz, T.; Diakonova, N.; Knap, W.; Łusakowski, J. In ***Terahertz magnetospectroscopy of a point contact based on CdTe/CdMgTe quantum well***, Conference on Terahertz Emitters, Receivers, and Applications V, San Diego, CA, AUG 17-18, 2014.
6. Gutin, A.; Muraviev, A. V.; Kamaraju, N.; Shen, X.; Yamaguchi, Y.; Shur, M. S.; But, D.; Dyakonova, N.; Knap, W.; Rudin, S.; Rupper, G. In ***Application of plasma-wave detectors for ultra-short pulse terahertz radiation***, 39th International Conference Infrared, Millimeter, and Terahertz waves (IRMMW-THz), Tucson, AZ, USA, SEP 14-19, 2014.
7. Viti, L.; Coquillat, D.; Ercolani, D.; Knap, W.; Sorba, L.; Vitiello, M. S. In ***High-performance room-temperature THz nanodetectors with a narrowband antenna***, Conference on Terahertz, RF, Millimeter, and Submillimeter-Wave Technology and Applications VII, San Francisco, CA FEB 04-06, 2014.

**2013**

1. But, D. B.; Diakonova, N.; Drexler, C.; Drachenko, O.; Romanov, K.; Golenkov, O. G.; Sizov, F. F.; Gutin, A.; Shur, M.; Ganichev, S. D. In ***The dynamic range of THz broadband FET detectors***, Conference on Terahertz Emitters, Receivers, and Applications IV, San Diego, CA, AUG 25-26, 2013.
2. But, D. B.; Drexler, C.; Dyakonova, N.; Drachenko, O.; Ganichev, S. D.; Knap, W. In ***Nonlinear photoresponse of FET THz broadband detectors at high power irradiation***, 38th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Mainz, Germany, SEP 01-06, 2013.
3. Coquillat, D.; Kurita, Y.; Kobayashi, K.; Teppe, F.; Dyakonova, N.; Consejo, C.; But, D.; Tohme, L.; Nouvel, P.; Blin, S.; Torres, J.; Pénarier, A.; Otsuji, T.; Knap, W. In ***Contribution of the gate leakage current to terahertz detection by asymmetric dual-grating gate HEMT structures***, 38th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Mainz, Germany, SEP 01-06, 2013.
4. Di Gaspare, A.; Gilibertia, V.; Casinia, R.; Giovinea, E.; Evangelistic, F.; Coquillatd, D.; Knape, W.; Sadofevf, S.; Calarcof, R.; Dispenzag, M. In ***Antenna-coupled heterostructure field effect transistors for integrated terahertz heterodyne mixers***, Conference on Terahertz, RF, Millimeter, and Submillimeter-Wave Technology and Applications VI, San Francisco, CA, FEB 05-07, 2013.
5. Knap, W.; But, D.; Bawedin, M.; Chang, S.; Klimenko, O.; Dyakonova, N.; Coquillat, D.; Fatimy, A. E.; Teppe, F.; Gutin, A.; Nagatsuma, T.; Cristoloveanu, S. In ***Temperature, back gate and polarization studies in nanotransistor based THz plasma detectors***, 21st International Conference on Applied Electromagnetics and Communications (ICECom), , Dubrovnik, Croatia OCT 14-16, 2013.
6. Knap, W.; Dyakonova, N.; Coquilliat, D.; But, D.; Teppe, F. In *A* ***Terahertz plasma oscillations in nanometer field effect transistors for Terahertz radiation rectification***, 38th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Mainz, GERMANY, SEP 01-06, 2013.
7. Knapa, W.; Buta, D.; Vitiellod, N. D. D. C. M. S.; Bline, S.; El Fatimya, A.; Teppea, F.; Tredicuccid, A.; Nagatsumaf, T.; Ganichev, S. In ***Nanotransistor based THz plasma detectors: low temperatures, graphene, linearity, and circular polarization studies***, Conference on Terahertz Emitters, Receivers, and Applications IV, San Diego, CA, AUG 25-26, 2013.
8. Kurita, Y.; Kobayashi, K.; Otsuji, T.; Ducournau, G.; Meziani, Y. M.; Popov, V. V.; Knap, W. In ***Extremely-high sensitive terahertz detector based on dual-grating gate InP-HEMTs***, 2013 International Conference on Indium Phosphide and Related Materials (IPRM),, Kobe, Japan, MAY 19-23, 2013.
9. Meziani, Y. M.; Velázquez-Pérez, J. E.; Coquillat, D.; Dyakonova, N.; Knap, W.; Grigelionis, I.; García-García, E.; Fobelets, K. In ***Terahertz detection using Si-SiGe MODFETs***, Spanish Conference on Electron Devices (CDE), 2013 Valladolid, Spain FEB 12-14, 2013; Valladolid, Spain 2013.
10. Otsuji, T.; Watanabe, T.; Boubanga-Tombet, S.; Suemitsu, T.; Coquillat, D.; Knap, W.; Fateev, D.; Popov, V. In ***Asymmetric dual-grating gate InGaAs/InAlAs/InP HEMTs for ultrafast and ultrahigh sensitive terahertz detection***, International Conference on Indium Phosphide and Related Materials (IPRM), 2013 Kobe, Japan MAY 19-23, 2013.
11. Otsuji, T.; Watanabe, T.; Tombet, S. A. B.; Satou, A.; Ryzhii, V.; Popov, V.; Knap, W. In ***Emission and detection of terahertz radiation using two-dimensional plasmons in semiconductor nanoheterostructures for nondestructive evaluations***, The Micro- and Nanotechnology Sensors, Systems, and Applications V, Baltimore, Maryland, USA, Baltimore, Maryland, USA, 2013.
12. Otsuji, T.; Watanabe, T.; Tombet, S. B.; Suemitsu, T.; Ryzhii, V.; Popov, V.; Knap, W. In ***Terahertz emission and detection using two dimensional plasmons in semiconductor nano-heterostructures for sensing applications***, 12th IEEE Sensors Conference, Baltimore, MD, USA NOV 03-06, 2013.
13. Romanov, K. S.; Dyakonova, N.; But, D. B.; Teppe, F.; Knap, W.; Dyakonov, M. I.; Drexler, C.; Olbrich, P.; Karch, J.; Schafberger, M. In ***Field effect transistor as detector of THz radiation helicity***, Conference on Terahertz Emitters, Receivers, and Applications IV, San Diego, CA, AUG 25-26, 2013.
14. Romeo, L.; Coquillat, D.; Viti, L.; Ercolani, D.; Sorba, L.; Knap, W.; Tredicucci, A.; Vitiello, M. S. In ***Room-temperature nanowire terahertz photodetectors***, Conference on Quantum Sensing and Nanophotonic Devices X, San Francisco, CA, FEB 03-07, 2013.
15. Shur, M.; Muraviev, A. V.; Rumyantsev, S. L.; Knap, W.; Liu, G.; Balandin, A. A. In ***Plasmonic and bolometric terahertz graphene sensors***, 12th IEEE Sensors Conference, Baltimore MD, USA NOV 03-06, 2013.
16. Teppe F., Z. M., Orlita M., Consejo C., Diakonova N., But D., Coquillat D., Knap W., Mikhailov N. N., Dvoretskii S. A., Aleshkin V., and Gavrilenko V. In ***Magnetospectroscopy of HgTe Based Topological Insulators***, SPIE Symposium on Spintronics VI, San Diego, California, United States AUG 25-29, 2013.
17. Tohmé, L.; Blin, S.; Nouvel, P.; Pénarier, A.; Torres, J.; Varani, L.; Ducournau, G.; Artillan, P.; Bollaert, S.; Roelens, Y.; Coquillat, D.; But, D.; Knap, W.; Teppe, F. In ***Signal-to-noise ratio in terahertz wireless communication using field-effect-transistors as detectors***, 22nd International Conference on Noise and Fluctuations (ICNF), 2013 Montpellier, France JUN 24-28, 2013.
18. Tohme, L.; Ducournau, G.; Blin, S.; Coquillat, D.; Nouvel, P.; Pénarier, A.; Knap, W.; Lampin, J. F. In ***0.2 THz wireless communication using plasma-wave transistor detector***, 38th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), 2013 Mainz, Germany 1-6 Sept. 2013.
19. Vitiello, M. S.; Coquillat, D.; Viti, L.; Romeo, L.; Vicarelli, L.; Ercolani, D.; Ferrari, A. C.; Polini, M.; Sorba, L.; Pellegrini, V.; Knap, W.; Tredicucci, A. In ***Fast, sensitive and low-noise nanowire and graphene field effect transistors for room-temperature detection of Terahertz quantum cascade laser emission***, 38th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), 2013 Mainz, Germany SEP 01-06, 2013.
20. Watanabe, T.; Kurita, Y.; Satou, A.; Suemitsu, T.; Knap, W.; Popov, V. V.; Otsuji, T. In ***Terahertz monochromatic coherent emission from an asymmetric chirped dual-grating-gate InP-HEMT with a photonic vertical cavity*,** 38th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Mainz, Germany 1-6 Sept. 2013.
21. Watanabe, T.; Satou, A.; Suemitsu, T.; Knap, W.; Popov, V. V.; Otsuji, T. In ***Plasmonic terahertz monochromatic coherent emission from an asymmetric chirped dual-grating-gate InP-HEMT with a photonic vertical cavity***, Conference on Lasers and Electro-Optics (CLEO), 2013 San Jose, CA, USA 9-14 June 2013.
22. Watanabe T., K. Y., Satou A., Suemitsu T., Knap W., Popov V. V., and Otsuji T. In ***Plasmonic terahertz monochromatic coherent emission from an asymmetric chirped dual-grating-gate InP-HEMT with a photonic vertical cavity***, the 71st Annual Device Research Conference (DRC), South Bend, Indiana, USA, JUN 23-26, 2013.
23. Zholudev, M.; Teppe, F.; Knap, W.; Orlita, M.; Aleshkin, V.; Gavrilenko, V.; Mikhailov, N.; Dvoretskii, S. In ***Terahertz magnetospectroscopy of narrow-gap HgCdTe-based structures***, 38th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), 2013, Mainz, Germany, SEP 01-06, 2013.

**2012**

1. Zholudev, M. S.; Teppe, F.; Orlita, M.; Aleshkin, V. Y.; Ikonnkov, A. V.; Gavrilenko, V. I.; Knap, W.; Mikhailov, N. N.; Dvoretskii, S. A. In ***Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields***, 15th Russian Youth Conference on Physics and Astronomy (PhysicA.SPb), Saint Petersburg, RUSSIA, OCT 23-24, 2012.
2. Boubanga-Tombet, S.; Tanimoto, Y.; Watanabe, T.; Suemitsu, T.; Yuye, W.; Minamide, H.; Ito, H.; Popov, V.; Otsuji, T. In *Asy****mmetric dual-grating gate InGaAs/InAlAs/InP HEMTs for ultrafast and ultrahigh sensitive terahertz detection***, 70th Device Research Conference, University Park, TX, USA 18-20 June 2012.
3. But, D.; Dyakonova, N.; Coquillat, D.; Teppe, F.; Knap, W.; Watanabe, T.; Tanimoto, Y.; Tombet, S. B.; Otsuji, T. In ***Terahertz radiation detection by double grating-gate transistors in high magnetic fields***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Wollongong, NSW, Australia SEP 23-28, 2012.
4. But, D.; Dyakonova, N.; Coquillat, D.; Teppe, F.; Knap, W.; Watanabe, T.; Tanimoto, Y.; Tombet, S. B.; Otsuji, T. In ***THz Double-Grating Gate Transistor Detectors in High Magnetic Fields***, The 41st International School and Conference on the Physics of Semiconductors (Jaszowiec), Krynica Zdroj, Poland JUN 08-15, 2012.
5. Coquillat, D.; Dyakonova, N.; Goiran, M.; Vitiello, M. S.; Vicarelli, L.; Poumiro, J. M.; Escoffier, W.; Raquet, B.; But, D.; Teppe, F.; Pellegrini, V.; Tredicucci, A.; Knap, W. In ***Terahertz rectification by graphene field effect transistors***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Wollongong, NSW, Australia SEP 23-28, 2012.
6. Coquillat, D.; Schuster, F.; Dyakonova, N.; Teppe, F.; Giffard, B.; Kopyt, P.; Takada, T.; Arakawa, K.; Hisatake, S.; Nagatsuma, T.; Knap, W. In ***Polarization and frequency studies of Si MOSFET terahertz detectors***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Wollongong, NSW, Australia SEP 23-28, 2012.
7. Coquillat, D.; Torres, J.; d'Yerville, M. L. V.; Cassagne, D.; Teppe, F.; Dyakonova, N.; Knap, W.; Rue, R. D. L.; Bouchoule, S.; Margeat, E.; Royer, C. In ***Second harmonic generation in GaN-based photonic crystals for single molecule investigations***, Conference on Gallium Nitride Materials and Devices VII, San Francisco, California, United States, JAN 23-26, 2012.
8. Drexler, C.; Dyakonova, N.; Olbrich, P.; Karch, J.; Schafberger, M.; Karpierz, K.; Mityagin, Y.; Lifshits, M. B.; Teppe, F.; Klimenko, O.; Meziani, Y. M.; Knap, W.; Ganichev, S. D. In ***Terahertz photon helicity sensitive photoresponse in GaAs/AlGaAs high electron mobility transistors***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Wollongong, NSW, Australia SEP 23-28, 2012.
9. Gaspare, A. D.; Casini, R.; Diakonova, N.; Drexler, C.; Giliberti, V.; Ortolani, M.; Coquillat, D.; Knap, W.; Ganichev, S. D. In ***Asymmetric double grating gate detector fabricated on industrial pseudomorphic AlGaAs/InGaAs/AlGaAs heterostructure***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), 2012 37th International Conference, Wollongong, NSW, Australia SEP 23-28, 2012.
10. Grigelionis, I.; Białek, M.; Grynberg, M.; Czapkiewicz, M.; Kolkovskiy, V.; Wiater, M.; Wojciechowski, T.; Wróbel, J.; Wojtowicz, T.; But, D. In ***Terahertz Response of a Point Contact Based on CdTe/CdMgTe Quantum Well in Magnetic Field***, The 41st International School and Conference on the Physics of Semiconductors (Jaszowiec), Krynica Zdroj, Poland JUN 08-15, 2012.
11. Klimenko, O. A.; Teppe, F.; Knap, W.; Iniguez, B.; Coquillat, D.; Mityagin, Y. A.; Dyakonova, N. V.; Videlier, H.; Lime, F.; Marczewski, J.; Kucharski, K. In ***Temperature dependence of terahertz radiation detection by field effect transistors***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Wollongong, NSW, Australia SEP 23-28, 2012.
12. Knap, W.; Coquillat, D.; Dyakonova, N.; Klimenko, O.; But, D.; Teppe, F.; Sakowicz, M.; Lusakowski, J.; Otsuji, T. In ***Plasma nonlinearities and terahertz detection by Field Effect Transistors***, 19th International Conference on Microwave Radar and Wireless Communications (MIKON), Warsaw, Poland MAY 21-23, 2012.
13. Knap, W.; Dyakonova, N. V.; Schuster, F.; Coquillat, D.; Teppe, F.; Giffard, B.; But, D. B.; Golenkov, O. G.; Sizov, F. F.; Watanabe, T.; Tanimoto, Y.; Otsuji, T. In ***Terahertz detection and emission by field-effect transistors***, Conference on Terahertz Emitters, Receivers, and Applications III,, San Diego, California, United States, AUG 12-13, 2012.
14. Meziani Y. M., G.-G. E., Velazquez-Perez J. E., Coquillat D., Dyakonova N., Knap W., Grigelionis I., and Fobelets K In ***Terahertz Imaging Using Strained-Si MODFETs as Sensors***, The International Conference Silicon-Germanium Technology and Device Meeting (ISTDM 2012), Berkeley, California, USA, JUN 04-06, 2012.
15. Otsuji, T.; Boubanga-Tombet, S.; Watanabe, T.; Tanimoto, Y.; Satou, A.; Suemitsu, T.; Wang, Y.; Minamide, H.; Ito, H.; Meziani, Y. M. In ***Ultrahigh sensitive plasmonic terahertz detectors based on an asymmetric dual-grating gate HEMT structure***, Conference on Terahertz Physics, Devices and Systems VI - Advanced Applications in Industry and Defense, Baltimore, Maryland, United States, APR 23-24, 2012.
16. Penot, A.; Torres, J.; Laurent, T.; Sharma, R.; Nouvel, P.; Blin, S.; Varani, L.; Knap, W.; Cordier, Y.; Chmielowska, M. In ***THz transmission modulated by a dc-bias through GaN quantum well structure***, Conference on Terahertz Technology and Applications V, San Francisco, CA, 2012.
17. Pitanti A., V. M. S., Romeo L., Coquillat D., Teppe F., Knap W., Ercolani D., Sorba L., and Tredicucci A In ***Semiconductor nanowire field-effect transistors: towards high-frequency THz detector***, Conference on The Terahertz Emitters, Receivers, and Applications III, San Diego, California, USA AUG 12-13, 2012.
18. Sakowicz, M.; Lifshits, M. B.; Klimenko, O. A.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Gaquière, C.; Poisson, M. A.; Delage, S.; Knap, W. In ***AlGaN/GaN based field effect transistors for terahertz detection and imaging***, Conference on Gallium Nitride Materials and Devices VII;, San Francisco, California, United States, JAN 23-26, 2012.
19. Teppe, F.; Blin, S.; Coquillat, D.; Dyakonova, N.; Tohme, L.; Chenaud, B.; Hisatake, S.; Arakawa, K.; Torres, J.; Consejo, C.; Nouvel, P.; Solignac, P.; Pénarier, A.; Nagatsuma, T.; Knap, W. In ***Plasma wave detectors for Terahertz wireless communication and fast imaging applications***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Wollongong, NSW, Australia SEP 23-28, 2012.
20. Teppe, F.; Zholudev, M.; Orlita, M.; Consejo, C.; Torres, J.; Wróbel, J.; Grabecki, G.; Czapkiewicz, M.; Mikhailov, N. N.; Dvoretskii, S. A.; Aleshkin, V.; Gavrilenko, V.; Knap, W. In ***Magnetospectroscopy of 2D HgTe based topological insulators***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves, Wollongong, NSW, Australia 23-28 Sept. 2012.
21. Vitiello M. S., C. D., Viti L., Ercolani D., Teppe F., Pitanti A., Beltram F., Sorba L., Knap W., and Tredicucci A. In ***Room Temperature Terahertz detectors based on semiconductor nanowire field effect transistors***, The Conference Lasers and Electro-Optics (CLEO 2012), San Francisco, California, USA, JAN 22-26, 2012.
22. Vitiello, M. S.; Coquillat, D.; Vicarelli, L.; Viti, L.; Romeo, L.; Ercolani, D.; Ferrari, A. C.; Scalari, G.; Faist, J.; Polini, M.; Beltram, F.; Sorba, L.; Pellegrini, V.; Knap, W.; Tredicucci, A. In ***Nanowire and graphene architectures for Room Temperature THz detection***, 37th International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), , Wollongong, NSW, Australia SEP 23-28, 2012.
23. Watanabe, T.; Tombet, S. A. B.; Tanimoto, Y.; Fukushima, T.; Otsuji, T.; Fateev, D.; Popov, V.; Coquillat, D.; Knap, W.; Meziani, Y. In ***Ultrahigh sensitive plasmonic terahertz detection using asymmetric dual-grating gate HEMT structures***, Conference on Lasers and Electro-Optics (CLEO), San Jose, CA, MAY 06-11, 2012.

**2011**

1. Dyakonova, N.; El Fatimy, A.; Meziani, Y.; Coquillat, D.; Knap, W.; Teppe, F.; Buzatu, P.; Diforte-Poisson, M. A.; Dua, C.; Piotrowicz, S. In ***THz Emission Related to Hot Plasmons and Plasma Wave Instability in Field Effect Transistors***, 40th “Jaszowiec” International School and Conference on the Physics of Semiconductor, Krynica-Zdroj, Poland JUN 25-JUL 01, 2011.
2. Knap, W.; Shuster, F.; Coquillat, D.; Teppe, F.; Videlier, H.; Coquillat, D.; Łusakowski, J.; Skotnicki, T. In ***Silicon field effect transistors for Terahertz detection and imaging***, Proceedings of the 5th European Conference on Antennas and Propagation (EUCAP), Rome, Italy 11-15 April 2011.
3. Knap, W.; Teppe, F.; Consejo, C.; Chenaud, B.; Torres, J.; Solignac, P.; Wasilewski, Z. R.; Zholudev, M.; Dyakonova, N.; Coquillat, D. In ***Terahertz detection by field effect transistors security imaging***, Terahertz Physics, Devices, and Systems V: Advance Applications in Industry and Defense, Orlando, Florida, United States, APR 25-26, 2011.
4. Łusakowski, J.; Białek, M.; Yavorskiy, D.; Marczewski, J.; Kopyt, P.; Gwarek, W.; Knap, W.; Kucharski, K.; Grodner, M.; Górska, M.; Grabiec, P. In ***Planar antennas for detection of 340 GHz band with single Si metal-oxide-semiconductor field-effect transistors***, 2011 International Conference on Infrared, Millimeter, and Terahertz Waves, Houston, TX, USA 2-7 Oct. 2011.
5. Nogajewski, K.; Karpierz, K.; Grynberg, M.; Knap, W.; Gaska, R.; Yang, J.; Shur, M. S.; Łusakowski, J. In ***Magnetooptical studies of resonant plasma excitations in grating-gate GaN/AlGaN-based field-effect transistors***, 2011 International Conference on Infrared, Millimeter, and Terahertz Waves, Houston, TX, USA 2-7 Oct. 2011.
6. Nogajewski, K.; Karpierz, K.; Grynberg, M.; Knap, W.; Gaska, R.; Yang, J.; Shur, M. S.; Łusakowski, J. In ***Magnetotransport properties of grating-gate THz detectors based on high electron mobility GaN/AlGaN heterostructures***, 2011 International Conference on Infrared, Millimeter, and Terahertz Waves, Houston, TX, USA 2-7 Oct. 2011.
7. Otsuji, T.; Watanabe, T.; Akagawa, K.; Tanimoto, Y.; Tombet, S. B.; Suemitsu, T.; Coquillat, D.; Knap, W.; Chan, S.; Ryzhii, V. In ***New semiconductor materials and devices for terahertz imaging and sensing***, 2011 IEEE SENSORS Proceedings, Limerick, Ireland 28-31 Oct. 2011.
8. Schuster, F.; Videlier, H.; Dupret, A.; Coquillat, D.; Sakowicz, M.; Rostaing, J. P.; Tchagaspanian, M.; Giffard, B.; Knap, W. In ***A broadband THz imager in a low-cost CMOS technology***, 2011 IEEE International Solid-State Circuits Conference, San Francisco, CA, USA 20-24 Feb. 2011.
9. Teppe, F.; Consejo, C.; Torres, J.; Chenaud, B.; Solignac, P.; Fathololoumi, S.; Wasilewski, Z. R.; Zholudev, M.; Diakonova, N.; Coquillat, D. In ***Terahertz Detection of Quantum Cascade Laser Emission by Plasma Waves in Field Effect Transistors***, 40th Jaszowiec International School and Conference on the Physics of Semiconductors, Krynica-Zdroj, Poland, JUN 25-JUL 01, 2011.
10. Tombet, S. A. B.; Otsuji, T.; Knap, W. In ***Coherent and tunable terahertz emission from nano-metric field effect transistor at room temperature***, The Conference Lasers and Electro-Optics (CLEO 2011), Baltimore, MD, USA MAY 01-06, 2011.
11. Videlier, H.; Dyakonova, N.; Teppe, F.; Consejo, C.; Chenaud, B.; Knap, W.; Lusakowski, J.; Tomaszewski, D.; Marczewski, J.; Grabiec, P. In ***Terahertz Photovoltaic Response of Si-MOSFETs: Spin Related Effect***, 40th “Jaszowiec” International School and Conference on the Physics of Semiconductor, Krynica-Zdrój, JUN 25-JUL 01, 2011.
12. Videlier, H.; Dyakonova, N.; Teppe, F.; Consejo, C.; Knap, W.; Lusakowski, J.; Tomaszewski, D.; Marczewski, J.; Grabiec, P. In ***Spin related effect in Terahertz photovoltaic response of Si-MOSFETs***, Progress in Electromagnetics Research Symposium (PIERS), Marrakesh, MOROCCO, MAR 20-23, 2011.
13. Videlier H., D. N., Teppe F., Consejo C., Chenaud B., Knap W., Lusakowski J., Tomaszewski D., Marczewski J., and Grabiec P. In ***Terahertz Photovoltaic Response of Si-MOSFETs***, The 40th Jaszowiec International School and Conference on the Physics of Semiconductors, Krynica-Zdroj, POLAND JUN 25-JUL 01, 2011.
14. Vitiello, M. S.; Pitanti, A.; Teppe, F.; Coquillat, D.; Viti, L.; Ercolani, D.; Sorba, L.; Knap, W.; Tredicucci, A. In ***Nanowire-based architectures for the detection of THz radiation***, 2011 International Conference on Infrared, Millimeter, and Terahertz Waves, Houston, TX, USA 2-7 Oct. 2011.
15. Watanabe, T.; Akagawa, K.; Tanimoto, Y.; Coquillat, D.; Knap, W. M.; Otsuji, T. In ***Terahertz imaging with InP high-electron-mobility transistors***, Conference on Terahertz Physics, Devices, and Systems V: Advance Applications in Industry and Defense;, Orlando, Florida, United States, APR 25-26, 2011.
16. Watanabe T., T. S. B., Tanimoto Y., Wang Y., Minamide H., Ito H., Fateev D., Popov V., Coquillat D., Knap W., and Otsuji T. In ***Ultrahigh sensitive plasmonic terahertz detector based on an asymmetric dual-grating gate HEMT structure***, The International Conference Semiconductor Device Research Symposium (ISDRS 2011), Maryland, USA APR 23-24, 2012.

**2010**

1. Boubanga-Tombet, S.; Knap, W.; Otsuji, T. In ***Field effect transistors for fast terahertz detection and imaging***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, Italy 5-10 Sept. 2010.
2. Drexler, C.; Dyakonova, N.; Schafberger, M.; Karpierz, K.; Karch, J.; Videlier, H.; Meziani, Y.; Olbrich, P.; Knap, W.; Ganichev, S. In *D****etection of high power THz radiation by GaAs High Electron Mobility and Si Field Effect Transistors***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, 5-10 Sept. 2010.
3. Dyakonova, N.; Fatimy, A. E.; Meziani, Y.; Otsuji, T.; Coquillat, D.; Knap, W.; Teppe, F.; Vandenbrouk, S.; Madjour, K.; Théron, D.; Gaquiere, C.; Poisson, M. A.; Delage, S. In ***Tunable room temperature THz emission from AlGaN/GaN high electron mobility transistors***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, 5-10 Sept. 2010.
4. El Moutaouakil, A.; Suemitsu, T.; Otsuji, T.; Videlier, H.; Boubanga‐Tombet, S. A.; Coquillat, D.; Knap, W. In ***Device loading effect on nonresonant detection of terahertz radiation in dual grating gate plasmon‐resonant structure using InGaP/InGaAs/GaAs material systems***, 37th International Symposium on Compound Semiconductors (ISCS), JAPAN, MAY 31-JUN 04, 2010.
5. G. Valusis, I. K., D. Seliuta, V. Tamosiunas, R. Simniskis, M. Dyakonov, D. Coquillat, F. Teppe, N. Dyakonova, S. Nadar, H. Videlier, W. Knap, M. Sakowicz, K. Karpierz, J. Lusakowski In ***Components for Compact Room Temperature Terahertz Imaging***, Specialists Meeting on "Terahertz and Other Electromagnetic Wave Techniques for Defence and Security, Lithuania, Lithuania, 3-4 May 2010.
6. Han, R.; Zhang, Y.; Coquillat, D.; Videlier, H.; Knap, W.; Brown, E.; K. K, O. In ***A 280-GHz Schottky Diode Detector in 130-nm Digital CMOS***, Custom Integrated Circuits Conference, San Jose, California, SEP 19-22, 2010.
7. Klimenko, O. A.; Mityagin, Y. A.; Videlier, H.; Boubanga-Tombet, S.; Teppe, F.; Dyakonova, N. V.; Nadar, S. H.; Savinov, S. A.; Consejo, C.; Murzin, V. N.; Knap, W. In ***Terahertz detection by InGaAs HEMTs in quantizing magnetic fields: Relation between magnetoresistance and photovoltaic response***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, 5-10 Sept. 2010.
8. O. Klimenko; Y.A. Mityagin; S.A. Savinov; V.N. Murzin; N.V. Dyakonova; P. Solignac; W. Knap In ***Terahertz spectroscopy based on tunable p-Ge laser operating in the cyclotron resonance mode***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves Rome, 5-10 Sept. 2010.
9. Knap, W.; Coquillat, D.; Teppe, F.; Dyakonova, N.; Schuster, F.; Klimenko, O. In ***Terahertz detection and emission by field effect transistors: Influence of high magnetic fields and channel geometry***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, 5-10 Sept. 2010.
10. Knap, W.; Nadar, S.; Videlier, H.; Boubanga-Tombet, S.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Karpierz, K.; Łusakowski, J.; Sakowicz, M.; Seliuta, D.; Kasalynas, I.; Valušis, G.; Monfray, S.; Skotnicki, T. In ***Field Effect transistors for fast terahertz detection and imaging***, 18-th INTERNATIONAL CONFERENCE ON MICROWAVES, RADAR AND WIRELESS COMMUNICATIONS, Vilnius, Lithuania 14-16 June 2010.
11. Knap, W.; Videlier, H.; Tombet, S. B.; Teppe, F.; Coquillat, D.; Diakonova, N.; Lusakowski, J.; Karpierz, K. In ***Influence of High Magnetic Field and Gate Length on Terahertz Detection by Field Effect Transistors***, Specialists Meeting on Terahertz and Other Electromagnetic Wave Techniques for Defence and Security, Vilnius, Lithuania, 3-4 May 2010.
12. Maremyanin, K. V.; Gavrilenko, V. I.; Morozov, S. V.; Ermolaev, D. M.; Zemlyakov, V. E.; Shapoval, S. Y.; Fateev, D. V.; Popov, V. V.; Maleev, N. A.; Teppe, F.; Knap, W. In ***Resonance detection of terahertz radiation in nanometer field-effect transistors with two-dimensional electron gas***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, 5-10 Sept. 2010.
13. Moutaouakil, A. E.; Suemitsu, T.; Otsuji, T.; Coquillat, D.; Knap, W. In ***Room temperature terahertz detection in high-electron-mobility transistor structure using InAlAs/InGaAs/InP material systems***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, Italy 5-10 Sept. 2010.
14. Nadar, S.; Coquillat, D.; Sakowicz, M.; Videlier, H.; Klimenko, O.; Teppe, F.; Dyakonova, N.; Knap, W.; Seliuta, D.; Kasalynas, I.; Valušis, G. In ***Room temperature imaging above one terahertz by field effect transistor as detector***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, Italy 5-10 Sept. 2010.
15. Nadar, S.; Klimenko, O.; Videlier, H.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Knap, W.; Madjour, K.; Ducournau, G.; Gaquière, C.; Poisson, M. A.; Torres, J.; Szczytko, J.; Dobroiu, A.; Otani, C. In ***Sub-terahertz imaging with AlGaN/GaN MISFETs***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, 5-10 Sept. 2010.
16. Otsuji, T.; Komori, T.; Watanabe, T.; Suemitsu, T.; Coquillat, D.; Knap, W. In ***Plasmon-resonant microchip emitters and detectors for terahertz sensing and spectroscopic applications***, Conference on Terahertz Physics, Devices, and Systems IV - Advanced Applications in Industry and Defence, Orlando, FL, APR 05-06, 2010.
17. Palma, F.; Teppe, F.; Fatimy, A. E.; Green, R.; Xu, J.; Vachontin, Y.; Tredicucci, A.; Goltsman, G.; Knap, W. In ***THz communication system based on a THz Quantum Cascade Laser and a Hot Electron Bolometer***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, Italy 5-10 Sept. 2010.
18. Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Grynberg, M.; Knap, W.; Köhler, K.; Valušis, G.; Gołaszewska, K.; Kamińska, E.; Piotrowska, A. In ***The Role of Gated and Ungated Plasma in THz Detection by Field Effect Transistors***, 29th International Conference on Physics of Semiconductors, Rio de Janeiro, BRAZIL, JUL 27-AUG 01, 2008.
19. Schuster, F.; Sakowicz, M.; Siligaris, A.; Dussopt, L.; Videlier, H.; Coquillat, D.; Teppe, F.; Giffard, B.; Dobroiu, A.; Skotnicki, T. In ***THz imaging with low-cost 130 nm CMOS transistors***, SPIE2010-Security and Defence SD108 Millimetre Wave and Terahertz Sensors and Technology, Toulouse, SEP 20-21, 2010.
20. Schuster, F.; Videlier, H.; Sakowicz, M.; Teppe, F.; Coquillat, D.; Dupont, B.; Siligaris, A.; Dussopt, L.; Giffard, B.; Knap, W. In ***Imaging above 1 THz limit with Si-MOSFET detectors***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, 5-10 Sept. 2010.
21. Videlier, H.; Dyakonova, N.; Teppe, F.; Consejo, C.; Knap, W.; Lusakowski, J.; Tomaszewski, D.; Marczewski, J.; Grabiec, P. In ***Spin related effect in Terahertz photovoltaic response of Si-MOSFETs***, 35th International Conference on Infrared, Millimeter, and Terahertz Waves, Rome, Italy 5-10 Sept. 2010.

**2009**

1. Boubanga-Tombet, S.; Nogajewski, K.; Teppe, F.; Knap, W.; Karpierz, K.; Lusakowski, J.; Grynberg, M.; Dyakonov, M. In ***High Magnetic Field Effects on Plasma Wave THz Detection in Field-Effect Transistors***, 4th Workshop on Quantum Chaos and Localisation Phenomena, Polish Acad Sci, Ctr Theoret Phys, Inst Phys, Warsaw, POLAND, MAY 22-24, 2009.
2. Boubanga-Tombet, S.; Teppe, F.; Knap, W.; Karpierz, K.; Lusakowski, J.; Grynberg, M.; Dyakonov, M. I.; Lyonnet, J.; Peiris, J. M. In ***Plasma waves Terahertz detection by field effect transistor in Quantinzing magnetic fields***, 6th International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON 16), Montpellier, FRANCE, AUG 24-28, 2009.
3. Coquillat, D.; Nadar, S.; Teppe, F.; Dyakonova, N.; Boubanga-Tombet, S.; Knap, W.; Nishimura, T.; Meziani, Y. M.; Otsuji, T.; Popov, V. V.; Tsymbalov, G. M. In ***Terahertz detection in a double-grating-gate heterotransistor***, 16th international conference on Electron Dynamics In Semiconductors, Optoelectronics and Nanostructures, Montpellier (France), AUG 24-28, 2009.
4. Fatimy, A. E.; Suemitsu, T.; Otsuji, T.; Dyakonova, N.; Knap, W.; Meziani, Y. M.; Vandenbrouk, S.; Madjour, K.; Théron, D.; Ch, G.; Prystawko, P.; Skierbiszewski, C. In ***Tunable room temperature terahertz sources based on two dimensional plasma instability in GaN HEMTs***, 16th International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON 16), Montpellier, FRANCE, AUG 24-28, 2009.
5. H. Videlier, S. N., N. Dyakonova, M. Sakowicz, T. Trinh Van Dam, F. Teppe, D. Coquillat, W. Knap, S. Denorme, T. Skotnicki, J. M. Peiris and J. Lyonnet In ***Silicon MOSFETs as Terahertz Plasma Wave Detectors***, 16th international conference on Electron Dynamics In Semiconductors, Optoelectronics and Nanostructures, Montpellier (France), AUG 24-28, 2009.
6. Ikonnikov A, K. S., Gavrilenko V, In ***Splitting of Cyclotron Resonance Line in InAs/AlSb QW Heterostructures in High Magnetic Fields: Effects of Electron-Electron and Electron-Phonon Interaction***, 9th International Conference on Research in High Magnetic Fields (RHMF 2009), Dresden, GERMANY, JUL 22-25, 2009.
7. K. K, O.; Chang, M. C. F.; Shur, M.; Wojciech, K. In ***Sub-millimeter wave signal generation and detection in CMOS***, 2009 IEEE MTT-S International Microwave Symposium Digest, Boston, MA, USA 7-12 June 2009.
8. Klimenko, O. A.; Yu, A. M.; Savinov, S. A.; Murzin, V. N.; Dyakonova, N. V.; Solignac, P.; Knap, W. In ***Terahertz wide range tunable cyclotron resonance p-Ge laser***, 16TH INTERNATIONAL CONFERENCE ON ELECTRON DYNAMICS IN SEMICONDUCTORS, OPTOELECTRONICS AND NANOSTRUCTURES (EDISON 16), Montpellier, FRANCE, AUG 24-28, 2009.
9. Knap, W.; Nadar, S.; Videlier, H.; Boubanga-Tombet, S.; Coquillat, D.; Dyakonova, N.; Teppe, F.; Karpierz, K.; Łusakowski, J.; Sakowicz, M.; Kasalynas, I.; Seliuta, D.; Valusis, G.; Otsuji, T.; Meziani, Y.; El Fatimy, A.; Vandenbrouk, S.; Madjour, K.; Théron, D.; Gaquière, C. In ***Field Effect Transistors for Terahertz Detection and Emission***, TeraTech'09: The Int. Workshop on Terahertz Technology Osaka, Japan, 2009.
10. Knap, W.; Valušis, G.; Łusakowski, J.; Coquillat, D.; Teppe, F.; Dyakonova, N.; Nadar, S.; Karpierz, K.; Bialek, M.; Seliuta, D. In ***Field effect transistors for terahertz imaging***, 15th Semiconducting and Insulating Materials Conference, Vilnius, Lithuania, MAY 09-11, 2016.
11. Meziani, Y. M.; Nishimura, T.; Tsuda, H.; Suemitsu, T.; Knap, W.; Popov, V. V.; Otsuji, T. In ***Enhancement of terahertz radiation by CW infrared laser excitation in a doubly interdigitated grating gates transistors***, 16th international conference on Electron Dynamics In Semiconductors, Optoelectronics and Nanostructures, Montpellier (France), AUG 24-28, 2009.
12. Nadar, S.; Coquillat, D.; Sakowicz, M.; Videlier, H.; Teppe, F.; Dyakonova, N.; Knap, W.; Peiris, J. M.; Lyonnet, J.; Seliuta, D. In ***Terahertz imaging using high electron mobility transistors as plasma wave detectors***, 15th International Semiconducting and Insulating Materials Conference (SIMC-XV), Vilnius Univ, Vilnius, LITHUANIA, JUN 15-19, 2009.
13. Ortolani, M.; Gaspare, A. D.; Giovine, E.; Evangelisti, F.; Foglietti, V.; Doria, A.; Gallerano, G. P.; Giovenale, E.; Messina, G.; Spassovsky, I.; Coppa, A.; Lanzieri, C.; Peroni, M.; Cetronio, A.; Sakowicz, M.; Knap, W. In ***Detection of terahertz radiation by AlGaN/GaN field-effect transistors***, 2009 34th International Conference on Infrared, Millimeter, and Terahertz Waves, Busan, South Korea 21-25 Sept. 2009.
14. S. Boubanga-Tombet, M. S., D. Coquilat, F. Teppe, N. Dyakonova, W. Knap, K. Karpierz, J. Łusakowski In ***Plasma wave THz detection by field effect transistor in high magnetic field***, 15th Semiconducting and Insulating Materials Conference, Physica Status Solidi, Vilnius, Lithuania, AUG 24-28, 2009.
15. S. Nadar, D. C., M. Sakowicz, H. Videlier, F. Teppe, N. Dyakonova, W. Knap, J.-M. Peiris, J. Lyonnet, D. Seliuta, I.Kašalynas, G. Valušis, K. Madjour, D. Théron, C. Gaquière, M.-A. Poisson In ***Terahertz imaging using GaAs field effect transistors as plasma wave detectors***, 15th Semiconducting and Insulating Materials Conference, Vilnius, Lithuania, Vilnius, Lithuania, June 15-19, 2009.
16. Seok, E.; Shim, D.; Mao, C.; Han, R.; Sankaran, S.; Cao, C.; Knap, W.; K. K, O. In ***Progress and Challenges Towards Terahertz CMOS Integrated Circuits***, IEEE Custom Integrated Circuits Conference, San Jose, CA, 13-16 Sept. 2009
17. Shim, D.; Mao, C.; Han, R.; Sankaran, S.; Seok, E.; Cao, C.; Knap, W.; K. K, O. In ***Paths to terahertz CMOS integrated circuits***, 2009 IEEE Custom Integrated Circuits Conference, San Jose, CA, 13-16 Sept. 2009.
18. Takuya, N.; Nobuhiro, M.; Irina, K.; Tetsuya, S.; Wojtek, K.; Taiichi, O. In ***Analysis of Fringing Effect on Resonant Plasma Frequency in Plasma Wave Devices***, International Conference on Solid State Devices and Materials, Tsukuba, JAPAN, SEP 24-26, 2008.

**2008**

1. Fatimy, A. E.; Abraham, E.; Nguema, E.; Mounaix, P.; Teppe, F.; Knap, W.; Otsuji, T. In ***Room temperature terahertz imaging by a GaAs-HEMT transistor associated with a THz time domain spectrometer***, 33rd International Conference on Infrared, Millimeter and Terahertz Waves, Pasadena, CA, USA 15-19 Sept. 2008.
2. Knap, W. In ***Terahertz detectors and emitters based on plasma wave oscillations in nanometer gate length transistors***, Conference on Lasers and Electro-Optics and 2008 Conference on Quantum Electronics and Laser Science, San Jose, CA, USA, 4-9 May 2008.
3. Knap, W.; Dyakonov, M.; Coquillat, D.; Teppe, F.; Dyakonova, N.; Łusakowski, J.; Karpierz, K.; Sakowicz, M.; Valusis, G.; Seliuta, D.; Kasalynas, I.; El Fatimy, A.; Meziani, Y. M.; Otsuji, T. In ***Field Effect Transistors for Terahertz Detection: Physics and First Imaging Applications***, 33rd International Conference on Infrared, Millimeter, and Terahertz Waves, Pasadena, CA, SEP, 2008.
4. Lusakowski, J.; Sakowicz, M.; Karpierz, K.; Knap, W.; Grynberg, M. In ***THz detection by field effect transistors: Antenna and high magnetic field effects***, 33rd International Conference on Infrared, Millimeter and Terahertz Waves, Pasadena, CA, USA 15-19 Sept. 2008.
5. Meziani, Y. M.; Hiroyuki, H.; Knap, W.; Taiichi, O.; Eiichi, S.; Popov, V. V. In *R****oom temperature terahertz emission from two-dimensional plasmons in doubly interdigitated grating gate heterostructure transistors***, Conference on Lasers and Electro-Optics and 2008 Conference on Quantum Electronics and Laser Science, San Jose, CA, USA 4-9 May 2008.
6. Meziani, Y. M.; Nishimura, T.; Handa, H.; Knap, W.; Otsuji, T.; Sano, E.; Popov, V. V.; Coquillat, D.; Teppe, F. In ***Room temperature generation of terahertz radiation from dual grating gate HEMT***, 33rd International Conference on Infrared, Millimeter and Terahertz Waves, Pasadena, CA, USA 15-19 Sept. 2008.
7. Nishimura, T.; Magome, N.; Khmyrova, I.; Suemitsu, T.; Knap, W.; Otsuji, T. In ***Analysis of Fringing Effect on Resonant Plasma Frequency in Plasma Wave Devices***, International Conference on Solid State Devices and Materials, Tsukuba, JAPAN, SEP 24-26, 2008.
8. Otsuji, T.; Komori, T.; Watanabe, T.; Suemitsu, T.; Coquillat, D.; Knap, W. In ***Plasmon-resonant microchip emitters and detectors for terahertz sensing and spectroscopic applications***, 29th International Conference on Physics of Semiconductors, Rio de Janeiro, BRAZIL, JUL 27-AUG 01, 2008.
9. Polischuk, O. V.; Popov, V. V.; Knap, W.; Fatimy, A. E. In ***Plasmon-plasmon scattering in two-dimensional electron channel of a terahertz nanotransistor***, 4th International Conference on Advanced Optoelectronics and Lasers, Alushta, Ukraine Sept. 29 2008-Oct. 4 2008.
10. Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Grynberg, M.; Gwarek, W.; Boubanga, S.; Coquillat, D.; Knap, W.; Shchepetov, A.; Bollaert, S. In ***A High Mobility Field‐Effect Transistor as an Antenna for sub‐THz Radiation***, 29th International Conference on Physics of Semiconductors, Rio de Janeiro, BRAZIL, JUL 27-AUG 01, 2008.
11. Sakowicz, M.; Lusakowski, J.; Karpierz, K.; Grynberg, M.; Gwareky, W.; Knap, W. In ***Antenna effects in detection of 100 GHZ radiation by high electron mobility field-effect transistors***, MIKON 2008 - 17th International Conference on Microwaves, Radar and Wireless Communications, Wroclaw, Poland 19-21 May 2008.
12. Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Grynberg, M.; Knap, W.; Köhler, K.; Valušis, G.; Gołaszewska, K.; Kamińska, E.; Piotrowska, A. In ***The role of gated and ungated plasma in THz detection by field effect transistors***, 29th International Conference on Physics of Semiconductors, Rio de Janeiro, BRAZIL, JUL 27-AUG 01, 2008.
13. Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Knap, W.; Grynberg, M.; Köhler, K.; Valusis, G.; Gołaszewska, K.; Kamińska, E.; Piotrowska, A. In ***Terahertz Detection by the Entire Channel of High Electron Mobility Transistors***, XXXVII International School of Semiconducting Compounds, Jaszowiec, POLAND, JUN 07-13, 2008.
14. Sakowicz, M.; Lusakowski, J.; Karpierza, K.; Grynberg, M. In ***Mechanism of radiation coupling to plasma wave field effect transistor sub-THz detectors***, XXXVII International School of Semiconducting Compounds, , Jaszowiec, POLAND, JUN 07-13, 2008.

**2007**

1. El Fatimy, A.; Tauk, R.; Boubanga, S.; Teppe, F.; Dyakonova, N.; Knap, W.; Lyonnet, J.; Meziani, Y. M.; Otsuji, T.; Poisson, M. A. In ***Plasma oscillations in nanotransistors for room temperature detection and emission of terahertz radiation***, 15th International Conference on Nonequilibrium Carrier Dynamics in Semiconductors, Tokyo, JAPAN, JUL 23-27, 2007.
2. Fatimy, A. E.; Teppe, F.; Boubanga, S.; Dyakonova, N.; Gil, B.; Coquillat, D.; Seliuta, D.; Valušis, G.; Poisson, M. A.; Morvan, E. In ***Nitride based nanotransistors as new sources and detectors of THz radiations***, 7th International Conference on Nitride Semiconductors (ICNS-7) Las Vegas, NV, SEP 16-21, 2007.
3. Knap, W.; Teppe, F.; Fatimy, A. E.; Dyakonova, N.; Boubanga, S.; Coquillat, D.; Gaquiere, C.; Shchepetov, A.; Bollaert, S. In ***Room temperature detection and emission of Terahertz radiation by plasma oscillations in nanometer size transistors***, 32nd International Conference on Infrared and Millimeter Waves and the 15th International Conference on Terahertz Electronics, Cardiff, UK 2-9 Sept. 2007.
4. Martín, M. J.; Rengel, R.; Pascual, E.; Łusakowski, J.; Knap, W.; González, T. In ***Onset of quasi‐ballistic transport and mobility degradation in ultra scaled MOSFETs: a Monte Carlo study***, 15th International Conference on Nonequilibrium Carrier Dynamics in Semiconductors, Tokyo, JAPAN, JUL 23-27, 2007.
5. Millithaler, J. F.; Varani, L.; Palermo, C.; Pousset, J.; Knap, W.; Mateos, J.; González, T.; Perez, S.; Pardo, D.; Reggiani, L. In ***Monte Carlo simulation of plasma oscillations in ultra‐thin layers***, 15th International Conference on Nonequilibrium Carrier Dynamics in Semiconductors, Tokyo, JAPAN, JUL 23-27, 2007.
6. Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Grynberg, M.; Majkusiak, B.; Tauk, R.; Tiberj, A.; Knap, W.; Bougrioua, Z.; Azize, M. In ***Electron Mobility and Concentration on Submicrometer Scale—Investigation of Si and AlGaN/GaN Field Effect Transistors by AC Magnetoresistance Method***, 28th International Conference on the Physics of Semiconductors (ICPS-28), Vienna, AUSTRIA, 2007.
7. Siekacz, M.; Dybko, K.; Maude, D.; Potemski, M.; Knap, W.; Skierbiszewski, C. In ***Electron-Electron Interaction Effects in Quantum Hall Regime of GaN/AlGaN Heterostructures***, 36th International School on the Physics of Semiconducting Compounds, Jaszowiec, POLAND, JUN 09-15, 2007.
8. Teppe, F.; Fatimy, A. E.; Boubanga, S.; Seliuta, D.; Valusis, G.; Chenaud, B.; Knap, W. In ***Terahertz resonant detection by plasma waves in nanometric transistors***, 13th International Symposium on Ultrafast Phenomena in Semiconductors, Vilnius, LITHUANIA, AUG 26-29, 2007.

**2006**

1. Dyakonova, N.; El Fatimy, A.; Łusakowski, J.; Knap, W.; Dyakonov, M. I.; Poisson, M. A.; Morvan, E.; Bollaert, S.; Shchepetov, A.; Roelens, Y. In ***Room-temperature terahertz emission from nanometer field-effect transistors***, 31st International Conference on Infrared and Millimeter Waves/14th International Conference on Terahertz Electronics, Shanghai, CHINA, SEP 18-22, 2006.
2. El Fatimy, A. T., F. / Knap, W. / Seliuta, D. / Valusis, G. / Orlov, M. / Bollaert, S. / Caquiere, C. / Shchepetov, A. In ***Resonant Terahertz Detection in InGaAs/AlInAs and AlGaN/GaN - Based Nanometric Transistors***, 17th International Symposium on Space Terahertz Technology, Paris 2006.
3. Inushima, T.; Maude, D. K.; Kato, N.; Lu, H.; Schaff, W. J.; Tauk, R.; Meziani, Y.; Ruffenach, S.; Briot, O.; Knap, W. In ***Superconductivity of InN as an intrinsic property***, 28th International Conference on the Physics of Semiconductors (ICPS-28), Vienna, AUSTRIA, JUL 24-28, 2006.
4. Knap, W. In ***Terahertz detection and emission related to two dimensional plasma oscillations in nanometer size transistors***, 31st International Conference on Infrared and Millimeter Waves/14th International Conference on Terahertz Electronics, Shanghai, China, SEP 18-22, 2006.
5. Knap, W.; El Fatimy, A.; Tauk, R.; Tombet, S. B.; Teppe, F. In ***Terahertz Detection Related to Plasma Excitations in Nanometer Gate Length Field Effect Transistor***, Symposium on Group 4 Semiconductor Nanostructures held at the 2006 MRS Fall Meeting, Boston, MA, NOV 27-DEC 01, 2006.
6. Knap, W.; El Fatimy, A.; Torres, J.; Teppe, F.; Orlov, M.; Gavrilenko, V. In ***Plasma wave resonant detection of terahertz radiations by nanometric transistors***, 16th Ural International Winter School on Pysics of Semiconductors, Kyshtym, RUSSIA, Feb 2006.
7. Millithaler, J. F., L. Varani, C. Palermo, J. Mateos, T. Gonzalez, S. Perez, D. Pardo, W. Knap, J. Lusakowski, N. Dyakonova, S. Bollaert, and A. Cappy In ***TeraHertz Emission from Nanometric HEMTs Analyzed by Noise Spectra***, 14th Int. Conf. on Nonequilibrium Carrier Dynamics in Semiconductors, Berlin, Heidelberg 2006.
8. Sakowicz, M.; Łusakowski, J.; Karpierz, K.; Grynberg, M.; Majkusiak, B.; Tauk, R.; Tiberj, A.; Knap, W.; Bougrioua, Z.; Azize, M. In ***Electron Mobility and Concentration on Submicrometer Scale—Investigation of Si and AlGaN/GaN Field Effect Transistors by AC Magnetoresistance Method***, 28th International Conference on the Physics of Semiconductors (ICPS-28), Vienna, AUSTRIA, JUL 24-28, 2006.
9. Shchepetov, A.; Roelens, Y.; Bollaert, S.; Cappy, A.; Dyakonova, N.; Knap, W.; Lusakowski, J.; Teppe, F.; Fatimy, A. E.; Dyakonov, M. In ***Plasma Wave HEMTs for THz applications***, 31st International Conference on Infrared Millimeter Waves and 14th International Conference on Teraherz Electronics, Shanghai, China, 18-22 Sept. 2006.
10. Tauk, R.; Tiberj, A.; Lorenzini, P.; Bougrioua, Z.; Azize, M.; Sakowicz, M.; Karpierz, K.; Knap, W. In ***Magnetotransport characterization of AlGaN/GaN interfaces***, 2nd International Workshop on Modulation Spectroscopy of Semiconductor Structures, Wroclaw, POLAND, JUN 29-JUL 01, 2006.

**2005**

1. Cappy, A.; Galloo, J. S.; Bollaert, S.; Roelens, Y.; Mateos, J.; Gonzalez, T.; Knap, W. In ***InP based ballistic nanodevices***, International Conference on Indium Phosphide and Related Materials, 2005, Glasgow, SCOTLAND, 8-12 May 2005.
2. Inushima, T.; Kato, N.; Maude, D. K.; Lu, H.; Schaff, W. J.; Tauk, R.; Meziani, Y.; Ruffenack, S.; Briot, O.; Knap, W. In ***Superconductivity of InN with a well defined Fermi surface***, 6th International Conference on Nitride Semiconductors (ICNS-6), Bremen, GERMANY, AUG 28-SEP 02, 2005.
3. Knap, W.; Łusakowski, J. In ***Terahertz plasma oscillations in nanotransistors***, 14th International Conference on Nonequilibrium Carrier Dynamics in Semiconductors, Chicago, USA, JUL 25-29, 2005.
4. Knap, W.; Teppe, F.; Dyakonova, N.; El Fatimy, A. In ***Terahertz emission and detection by plasma waves in nanometer size field effect transistors***, 6th Topical Workshop on Heterostructure Microelectronics (TWHM 2005), Awaji Isl, JAPAN, AUG, 2005.
5. Łusakowski, J.; Knap, W.; Meziani, Y.; Cesso, J. P.; El Fatimy, A.; Tauk, R.; Dyakonova, N.; Ghibaudo, G.; Boeuf, F.; Skotnicki, T. In ***Electron mobility in quasi-ballistic Si MOSFETs***, 35th European Solid-State Device Research Conference, Grenoble, FRANCE, SEP 12-16, 2005.
6. Lusakowski, J.; Knap, W.; Meziani, Y.; Cesso, J. P.; Fatimy, A. E.; Tauk, R.; Dyakonova, N.; Ghibaudo, G.; Boeuf, F.; Skotnicki, T. In ***Influence of ballistic and pocket effects on electron mobility in Si MOSFETs***, 35th European Solid-State Device Research Conference, ESSDERC 2005, Grenoble, FRANCE, 12-16 Sept. 2005.
7. Mateos, J.; Pérez, S.; Pardo, D.; González, T.; Łusakowski, J.; Dyakonova, N.; Knap, W.; Bollaert, S.; Roelens, Y.; Cappy, A. In ***Terahertz emission and noise spectra in HEMTs***, 4th International Conference on Unsolved Problems of Noise and Fluctuations in Physics, Biology and High Technology, Gallipoli, ITALY, JUN 06-10, 2005.
8. Meziani, Y. M.; Dyakonova, N.; Knap, W.; Seliuta, D.; Sirmulis, E.; Devenson, J.; Valusis, G.; Boeuf, F.; Skotnicki, T. In ***Non resonant response to terahertz radiation by submicron CMOS transistors***, 6th Topical Workshop on Heterostructure Microelectronics (TWHM 2005), Awaji Isl, JAPAN, AUG, 2005.
9. Meziani, Y. M.; Lusakowski, J.; Dyakonova, N.; Knap, W.; Seliuta, D.; Sirmulis, E.; Devenson, J.; Valusis, G.; Boeuf, F.; Skotnicki, T. In ***Non-resonant detection of terahertz radiation by nanometer field effect transistors***, 30th International Conference on Infrared and Millimeter Waves and 13th International Conference on Terahertz Electronics, Williamsburg, VA., 19-23 Sept. 2005.
10. Millithaler, J. F.; Varani, L.; Palermo, C.; Mateos, J.; González, T.; Perez, S.; Pardo, D.; Knap, W.; Lusakowski, J.; Dyakonova, N. In ***TeraHertz emission from nanometric HEMTs analyzed by noise spectra***, 18th International Conference on Noise and Fluctuations, Salamanca, SPAIN, July 25–29, 2005.
11. Polischuk, O. V.; Popov, V. V.; Shur, M. S.; Knap, W. In ***Excitation of gated and ungated plasmons and generation of terahertz radiation in nanometer-gate field-effect transistor***, Second International Conference on Advanced Optoelectronics and Lasers, 2005., Yalta, UKRAINE, 12-17 Sept. 2005.

**2004**

1. Gallon, C.; Fenouillet-Beranger, C.; Meziani, Y. M.; Cesso, J. P.; Lusakowski, J.; Teppe, F.; Dyakonova, N.; Vandooren, A.; Knap, W.; Ghibaudo, G.; Delille, D.; Cristoloveanu, S.; Skotnicki, T. In ***New magnetoresistance method for mobility extraction in scaled fully-depleted SOI devices***, 2004 IEEE International SOI Conference (IEEE Cat. No.04CH37573), Charleston, SC, 4-7 Oct. 2004.
2. Knap, W.; Lusakowski, J.; Teppe, F.; Dyakonova, N.; Meziani, Y. In ***Terahertz Generation and Detection by Plasma Waves in Nanometer Gate High Electron Mobility Transistors***, 12th International Symposium on Ultrafast Phenomena in Semiconductors (12-UFPS), Vilnius, LITHUANIA, 2004.
3. Knap, W.; Skierbiszewski, C.; Dybko, K.; Łusakowski, J.; Siekacz, M.; Grzegory, I.; Porowski, S. In ***Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures***, International Workshop on Bulk Nitride Semiconductors III., Zakopane, POLAND, SEP 04-09, 2004.
4. Meziani, Y. M.; Lusakowski, J.; Teppe, F.; Dyakonova, N.; Knap, W.; Romanjek, K.; Ferrier, M.; Clerc, R.; Ghibaudo, G.; Boeuf, F.; Skotnicki, T. In ***Magnetoresistance mobility measurements in sub 0.1 /spl mu/m Si MOSFETs***, Proceedings of the 30th European Solid-State Circuits Conference (IEEE Cat. No.04EX850), Leuven, BELGIUM, 21-23 Sept. 2004.
5. Popov, V. V.; Polischuk, O. V.; Shur, M. S.; Knap, W. In ***Plasmon terahertz response of submicron-gate high electron mobility transistor***, The Fifth International Kharkov Symposium on Physics and Engineering of Microwaves, Millimeter, and Submillimeter Waves (IEEE Cat. No.04EX828), Kharkov, UKRAINE, 21-26 June 2004.
6. Popov, V. V.; Polischuk, O. V.; Tsymbalov, G. M.; Shur, M. S.; Knap, W. In ***Electrodynamics of plasma oscillations in semiconductor microdevices with two-dimensional electron channels***, 10th International Conference on Mathematical Methods in Electromagnetic Theory, 2004., Dniepropetrovsk, Ukraine, 14-17 Sept. 2004.
7. Popov, V. V.; Tsymbalov, G. M.; Shur, M. S.; Knap, W. In ***Plasmon terahertz response of a slot diode with a two-dimensional electron channel***, The Fifth International Kharkov Symposium on Physics and Engineering of Microwaves, Millimeter, and Submillimeter Waves (IEEE Cat. No.04EX828), Kharkov, Ukraine, 21-26 June 2004.
8. Rumyantsev, S. L.; Shur, M. S.; Knap, W.; Dyakonova, N.; Pascal, F.; Hoffman, A.; Ghuel, Y.; Gaquiere, C.; Theron, D. In ***1/f noise and ballistic mobility in GaN/AlGaN heterostructure field effect transistors in high magnetic fields***, Conference on Noise in Devices and Circuits, Maspalomas, SPAIN, 25 May 2004.
9. Siekacz, M.; Dybko, K.; Skierbiszewski, C.; Knap, W.; Wasilewski, Z.; Maude, D.; Łusakowski, J.; Krupczyński, W.; Nowak, G.; Boćkowski, M. In ***High magnetic field studies of AlGaN/GaN heterostructures grown on bulk GaN***, 7th International Workshop on Expert Evaluation and Control of Compound Semiconductor Materials and Technologies, Montpellier, FRANCE, Montpellier, FRANCE, 2004.
10. Teppe, F.; Łusakowski, J.; Dyakonova, N.; Meziani, Y. M.; Knap, W.; Parenty, T.; Bollaert, S.; Cappy, A.; Popov, V.; Boeuf, F. In ***Terahertz emission and detection by plasma waves in nanoscale transistors***, 27th International Conference on the Physics of Semiconductors (ICPS-27), Flagstaff, AZ, JUL 26-30, 2004.
11. Teppe, F.; Meziani, Y.; Dyakonova, N.; Lusakowski, J.; Knap, W.; Boeuf, F.; Skotnicki, T.; Maude, D.; Rumyantsev, S.; Shur, M. S. In ***Detection of sub-Terahertz and Terahertz radiation by plasma waves in silicon field effect transistors***, IEEE Sensors 2004 Conference, Vienna Univ Technol, Vienna, AUSTRIA, 24-27 Oct. 2004.
12. Teppe, F.; Meziani, Y. M.; Dyakonova, N.; Łusakowski, J.; Boeuf, F.; Skotnicki, T.; Maude, D.; Rumyantsev, S.; Shur, M. S.; Knap, W. In ***Terahertz detectors based on plasma oscillations in nanometric silicon field effect transistors***, 7th International Workshop on Expert Evaluation and Control of Compound Semiconductor Materials and Technologies, Montpellier, FRANCE, 2004.

**2003**

1. Antonov, A. V.; Gavrilenko, V. I.; Demidov, E. V.; Morozov, S. V.; Dubinov, A. A.; Lusakowski, J.; Knap, W.; Dyakonova, N.; Kaminska, E.; Piotrowska, A.; Golaszewska, K.; Shur, M. S. In ***Electron transport and terahertz radiation detection in submicrometer-sized GaAs/AlGaAs field-effect transistors with two-dimensional electron gas***, Conference Dedicated to Oleg Vladimirovich Losev (1903-1942) - Pioneer of Semiconductor Electronics, Nizhnii Novgorod, Russia, March 17–20, 2003.
2. Chwalis, B.; Wysmołek, A.; Stępniewski, R.; Potemski, M.; Knap, W.; Baranowski, J. M.; Grandjean, N.; Massies, J.; Prystawko, P.; Grzegory, I. In ***Optical detection of 2DEG in GaN/AlGaN structures–High magnetic field studies***, Symposium on Novel Wide Bandgap Materials for Optoelectronic and Electronic Applications/5th International Workshop on Molecular Beam Epitaxy and Vapour Phase Epitaxy Growth Physics and Technology held at the E-MRS 2003 Fall Meeting, Warsaw, POLAND, 2003.
3. Chwalisz, B.; Wysmołek, A.; Bożek, R.; Korona, K.; Stępniewski, R.; Knap, W.; Pakuła, K.; Baranowski, J.; Grandjean, N.; Massies, J. In ***Localization effects in GaN/AlGaN quantum well-Photoluminescence studies***, 32nd International School on the Physics of Semiconducting Compounds, Jaszowiec, Poland, 2003.
4. Gaubert, C.; Chusseau, L.; Giani, A.; Gasquet, D.; Garet, F.; Aquistapace, F.; Duvillaret, L.; Coutaz, J. L.; Knap, W. In ***THz fractal antennas for electrical and optical semiconductor emitters and receptors***, 3rd International Conference on Physics of Light-Matter Coupling in Nanostructures (PLMCN3), Acireale, ITALY, 2003.
5. Lusakowski, J.; Knap, W.; Dyakonova, N.; Kaminska, E.; Piotrowska, A.; Golaszewska, K.; Shur, M. S.; Smirnov, D.; Gavrilenko, V.; Antonov, A.; Morozov, S. In ***Magnetotransport characterization of THz detectors based on plasma oscillations in submicron field-effect transistors***, Conference Dedicated to Oleg Vladimirovich Losev (1903-1942) - Pioneer of Semiconductor Electronics, NIZHNII NOVGOROD, RUSSIA, March 17–20, 2003.
6. Łusakowski, J.; Knap, W.; Kamińska, E.; Piotrowska, A.; Gavrilenko, V. In ***Magnetoconductivity of GaAs transistors as detectors of THz radiation***, 32nd International School on the Physics of Semiconducting Compounds, Jaszowiec, Poland, 2003.
7. Neu, G.; Teisseire‐Doninelli, M.; Morhain, C.; Semond, F.; Grandjean, N.; Beaumont, B.; Frayssinet, E.; Knap, W.; Witowski, A. M.; Sadowski, M. L. In ***Residual donors in wurtzite GaN homoepitaxial layers and heterostructures***, International Conference on Shallow-Level Centers in Semiconductors, Warsaw, Poland, 2003.

**2002**

1. Deng, Y.; Knap, W.; Rurayantsev, S.; Gaska, R.; Khan, A.; Ryzhii, V.; Kaminska, E.; Piotrowska, A.; Lusakowski, J.; Shur, M. S. In ***Subterahertz detection by high electron mobility transistors at large forward gate bias***, IEEE Lester Eastman Conference on High Performance Devices, UNIV DELAWARE, NEWARK, DE, 6-8 Aug. 2002.
2. Knap, W.; Deng, Y.; Kachorovskii, V.; Rumyantsev, S.; Shur, M. S. In ***Detection of terahertz radiation by plasma waves in field effect transistors***, IEEE Tenth International Conference on Terahertz Electronics, Cambridge, England, SEP 09-10, 2002.
3. Łusakowski, J.; Cywiński, G.; Korona, K.; Knap, W.; Kossut, J. In ***Mixing of impurity levels by a built‐in electric field in a CdMgTe/CdZnTe heterostructure***, 10th International Conference on Shallow Level Centers in Semiconductors, Warsaw, POLAND, JUL 24-27, 2002.

**2000**

1. Frayssinet, E.; Knap, W.; Krukowski, S.; Perlin, P.; Wisniewski, P.; Suski, T.; Grzegory, I.; Porowski, S. In ***Evidence of free carrier concentration gradient along the c-axis for undoped GaN single crystals***, 4th European Workshop on Gallium Nitride, Nottingham, England, JUL 02-05, 2000.

**1999**

1. Frayssinet, E.; Knap, W.; Robert, J.; Prystawko, P.; Leszczynski, M.; Suski, T.; Wisniewski, P.; Litwin-Staszewska, E.; Porowski, S.; Beaumont, B.; Gibart, P. In ***Infrared reflectivity and transport investigations of GaN single crystals and homoepitaxial layers***3rd International Conference on Nitride Semiconductors (ICNS 99), MONTPELLIER, FRANCE, JUL 04-09, 1999.
2. Knap, W.; Frayssinet, E.; Skierbiszewski, C.; Chaubet, C.; Sadowski, M. L.; Maude, D.; Asif Khan, M.; Shur, M. S. In ***Conduction Band Energy Spectrum of Two‐Dimensional Electrons in GaN/AlGaN Heterojunctions***, 3rd International Conference on Nitride Semiconductors (ICNS 99), Montpellier, France, JUL 04-09, 1999.

**1998**

1. Aleshkin, V. Y.; Andronov, A. A.; Antonov, A. V.; Bekin, N. A.; Gavrilenko, A. V.; Gavrilenko, V. I.; Revin, D. G.; Uskova, E. A.; Zvonkov, B. N.; Zvonkov, N. B. In ***Far Infrared Emission and Population Inversion of Hot Holes in MQW InGaAs/GaAs Heterostructures under Real Space Transfer***, 10th International Symposium on Ultrafast Phenomena in Semiconductors (10-UFPS), Vilnius, Lithuania, 1998.
2. Aleshkin, V. Y.; Andronov, A. A.; Antonov, A. V.; Bekin, N. A.; Gavrilenko, A. V.; Gavrilenko, V. I.; Revin, D. G.; Uskova, E. A.; Zvonkov, B. N.; Zvonkov, N. B. In ***Far infrared emission and population inversion of hot holes in MQW InGaAs/GaAs heterostructures excited at lateral transport***, 25th International Symposium on Compound Semiconductors, NARA, JAPAN, OCT 12-16, 1998.
3. Arushanov, E.; Zhitar, V.; Knap, W.; Kulikova, O.; Kulyuk, L.; Siminel, A. In ***Optical absorption of CdGa2S4***CAS'98 PROCEEDINGS - 1998 INTERNATIONAL SEMICONDUCTOR CONFERENCE, 21ST EDITION, VOLS 1 AND 2, SINAIA, ROMANIA, OCT 06-10, 1998.
4. Leszczyński, M.; Prystawko, P.; Śliwinski, A.; Suski, T.; Litwin-Staszewska, E.; Porowski, S.; Paszkiewicz, R.; Tłaczała, M.; Beaumont, B.; Gibart, P. In ***Polarity related problems in growth of GaN homoepitaxial layers***, XXVII International School on Physics of Semiconducting Compounds, JASZOWIEC, POLAND, JUN 07-12, 1998.
5. Prystawko, P.; Leszczynski, M.; Beaumont, B.; Gibart, P.; Frayssinet, E.; Knap, W.; Wisniewski, P.; Bockowski, M.; Suski, T.; Porowski, S. In ***Doping of homoepitaxial GaN layers***, 8th International Conference on Shallow-Level Centres in Semiconductors (SLCS-(\*), Montpellier, France, JUL 27-30, 1998.

**1997**

1. Allegre, J.; Lefebvre, P.; Juillaguet, S.; Camassel, J.; Knap, W.; Chen, Q.; Khan, M. In ***Optical properties of InGaN/GaN multiple quantum wells***, 7th International Conference on Silicon Carbide, III-Nitrides and Related Materials (ICSCIII-N 97), STOCKHOLM, SWEDEN, AUG 31-SEP 05, 1997.
2. Contreras, S.; Goiran, M.; Knap, W.; Yang, F.; Rakoto, H.; Barbaste, R.; Robert, J. L.; Leotin, J.; Askenazy, S.; Chen, Q.; Asif Khan, M. In ***High magnetic field studies of quantum transport and cyclotron resonance on 2D gas in GaN/GaAlN heterojunction***, 5th International Symposium on Research in High Magnetic Fields, Sydney, Australia, AUG 04-06, 1997.
3. Dmowski, L.; Cheremisin, M.; Skierbiszewski, C.; Knap, W. In ***Far-infrared narrow-band photodetector based on magnetically tunable cyclotron resonance-assisted transitions in pure n-type InSb***XXVI International School on Physics of Semiconducting Compounds, JASZOWIEC, POLAND, JUN 06-13, 1997.
4. Goiran, M.; Engelbrecht, F.; Yang, F.; Knap, W.; Huant, S.; Negre, N.; Barbaste, R.; Leotin, J.; Helbig, R.; Askenazy, S. In ***Cyclotron resonance of electrons in 6H-SiC in high magnetic fields up to 50T***, 5th International Symposium on Research in High Magnetic Fields, Sydney, Australia, AUG 04-06, 1997.

**1996**

1. Alause, H.; Grasdepot, F.; Malzac, J. P.; Knap, W.; Hermann, J. In ***Micromachined optical tunable filter for domestic gas sensors***, EUROSENSORS X Meeting, Louvain, Belgium, SEP 08-11, 1996.
2. Alause, H.; Knap, W.; Azema, S. C.; Bluet, J. M.; Sadowski, M. L.; Huant, S.; Young, J.; Khan, M. A.; Chen, Q.; Shur, M. In ***Optical and electrical properties of 2-dimensional electron gas in GaN/AlGaN heterostructures***, Symposium A: High Temperature Electronics: Materials, Devices and Applications at the European-Materials-Research-Society 1996 Spring Meeting, Strasbourg, France, JUN 04-07, 1996.
3. Alause, H.; Malzac, J. P.; Grasdepot, F.; Nouaze, V.; Hermann, J.; Knap, W. In ***Micromachined optical tunable filter for long term stability gas sensors***, 1st International Conference on Mid-IR Optoelectronics - Materials and Devices, Lancaster, England, SEP, 1996; Lancaster, England, 1996; pp 350-354.
4. Alause, H.; Skierbiszewski, C.; Dyakonov, M.; Knap, W.; Sadowski, M. L.; Huant, S.; Young, J.; Asif Khan, M.; Chen, Q. In ***Contactless characterisation of 2D-electrons in GaN/AlGaN HFETs***, 1st European Conference on Silicon Carbide and Related Materials (ECSCRM 96), IRAKLION, GREECE, OCT 06-09, 1996.
5. Contreras, S.; Knap, W.; Skierbiszewski, C.; Alause, H.; Robert, J. L.; Khan, M. A. In ***Observation of quantum Hall effect in 2D-electron gas confined in GaN/GaAlN heterostructure***, Symposium A: High Temperature Electronics: Materials, Devices and Applications at the European-Materials-Research-Society 1996 Spring Meeting, Strasbourg, France, JUN 04-07, 1996; Strasbourg, France, 1996; pp 92-95.
6. Dmowski, L. H.; Zduniak, A.; Litwin‐Staszewska, E.; Contreras, S.; Knap, W.; Robert, J. L. In ***Study of quantum and classical scatterIng times In pseudomorphic AlGaAs/InGaAs/GaAs by means of pressure***, 7th International Conference on High Pressure Semiconductor Physics (HPSP-VII), Schwabisch Gmund, Germany, JUL 28-31, 1996.
7. Grasdepot, F.; Alause, H.; Knap, W.; Malzac, J. P.; Suski, J. In ***Domestic gas sensor with micromachined optical tunable filter***, Proceedings of the 6th International Meeting on Chemical Sensors, Gaithersburg, Md., JUL 22-25, 1996.
8. Knap, W.; Zduniak, A.; Dmowski, L. H.; Contreras, S.; Dyakonov, M. I. In ***Study of transport, phase, and spin relaxation times of 2D electrons by means of pressure***, 7th International Conference on High Pressure Semiconductor Physics (HPSP-VII), SCHWABISCH GMUND, GERMANY, JUL 28-31, 1996.
9. Perlin, P.; Knap, W.; Camassel, J.; Polian, A.; Chervin, J. C.; Suski, T.; Grzegory, I.; Porowski, S. In ***Metal‐Insulator Transition in GaN Crystals***, 7th International Conference on High Pressure Semiconductor Physics (HPSP-VII), Schwabisch Gmund, Germany, JUL 28-31, 1996.
10. Perlin, P.; Suski, T.; Polian, A.; Chervin, J. C.; Knap, W.; Camassel, J.; Grzegory, I.; Porowski, S.; Erickson, J. W. In ***Coexistence of Shallow and Localized Donor Centers in Bulk GaN Crystals Studied by High-Pressure Raman Spectroscopy***, Symposium on III-V Nitrides, BOSTON, MA, DEC 02-06, 1996.

**1995**

1. Perlin, P.; Knap, W.; Taliercio, T.; Camassel, J.; Robert, J. L.; Suski, T.; Grzegory, I.; Jun, J.; Porowski, S.; Chervin, J. C. In ***Optical characterization of the free electron gas in bulk single crystals of GaN by means of Raman scattering and infrared reflectivity: evidence of phonon-plasmon coupled modes***, International Conference on Silicon Carbide and Related Materials 1995 (ICSCRM-95), Kyoto, Japan, SEP 18-21, 1995.
2. Zduniak, A.; Dyakonov, M. I.; Litwin-Staszewska, E.; Knap, W. In ***Universal Behaviour of Magnetoconductance due to Weak Localization in Two-Dimensional Systems-Example of GaInAs Quantum Wells***, XXIV International School on Physics of Semiconducting Compounds, JASZOWIEC, POLAND, MAY 27-JUN 02, 1995.

**1994**

1. Knap, W.; Skierbiszewski, C.; Litwin-Staszewska, E.; Kobbi, F.; Zduniak, A.; Robert, J. L.; Pikus, G. E.; Iordanskii, S. V.; Mosser, V.; Zekentes, K. In ***Weak Antilocalization in Quantum Wells***, XXIII International School on Physics of Semiconducting Compounds, Jaszowiec, Poland, MAY 28-JUN 03, 1994.
2. Lancefield, D.; Adams, A. R.; Meney, A. T.; Knap, W.; Litwin-Staszewska, E.; Skierbiszewski, C.; Robert, J. L. In ***The light-hole mass in a strained InGaAs/GaAs single quantum well and its pressure dependence***, 6th International Conference on High pressure Physics, Vancouver Canada AUG 21-24, 1994.

**1993**

1. DUR, D.; KNAP, W.; CHAUBET, C.; RAYMOND, A.; VICENTE, P.; DUBOIS, A.; SALESSE, I.; ETIENNE, B.; STANLEY, C. In ***Far infrared radiation (FIR) sources based on impurity emissionfrom selectively doped multi quantum wells (MQW)***, 18th International Conference on Infrared and Millimeter Waves, UNIV ESSEX, COLCHESTER, ENGLAND, SEP 06-10, 1993.
2. Knap, W.; DUR, D.; CHAUBET, C.; RAYMOND, A. In ***Ultralow background radiation far infrared spectroscopy based on the magnetically tunable selective sources, filters and detectors***, 18th International Conference on Infrared and Millimeter Waves, UNIV ESSEX, COLCHESTER, ENGLAND, SEP 06-10, 1993.
3. Litwin-Staszewska, E.; Kobbi, F.; Kamal-Saadi, M.; Dur, D.; Skierbiszewski, C.; Sibari, H.; Zekentes, K.; Mosser, V.; Raymond, A.; Knap, W.; Robert, J. L. In ***Determination of the basic parameters of pseudomorphic GaInAs quantum wells by means of simultaneous transport and optical investigations***, 6th International Conference on Modulated Semiconductor Structures, Garmisch Partenkir, Germany, AUG 23-27, 1993.
4. SIRMAIN, G.; PASQUIER, S.; MENY, C.; ETIEVE, P.; KNAP, W.; ADET, P.; FABRE, N.; MURRAY, A.; GRIFFIN, M.; LEOTIN, J. In ***BIB photodetectors based on antimony doped silicon***, 18th International Conference on Infrared and Millimeter Waves, UNIV ESSEX, COLCHESTER, ENGLAND, SEP 06-10, 1993.
5. Vicente, P.; Kavokin, A. V.; Raymond, A.; Lyapin, S. G.; Zekentes, K.; Dur, D.; Knap, W. In ***Oscillator strength of the E1HH1 excitonic transition as a function of magnetic field in modulation doped GaAlAs/GaAs quantum well***, 3rd International Conference on Optics of Excitons in Confined Systems, Montpellier, France, AUG 30-SEP 02, 1993.
6. Zawadzki, W.; Chaubet, C.; Dur, D.; Knap, W.; Raymond, A. In ***Cyclotron FIR emission from hot electrons in GaAs/GaAlAs heterostructures***, 6th International Conference on Modulated Semiconductor Structures, Garmisch Partenkir, Germany, AUG 23-27, 1993.

**1992**

1. Gregorkiewicz, T.; Bekman, H. H. P. T.; Ammerlaan, C. A. J.; Knap, W.; Brunel, L. C.; Martinez, G. In ***High-resolution EPR spectroscopy of the Si-NL10 thermal donor***, 5th International Conf on Shallow Impurities in Semiconductors : Physics and Control of Impurities, Kobe, Japan, AUG 05-08, 1992.
2. Raymond, A.; Chaubet, C.; Dur, D.; Knap, W.; Zawadzki, W.; Andre, J. P. In ***FIR Properties of GaAs–GaAlAs Heterojunctions Controlled by Metastable States under Pressure***, 5th International Conf on High Pressure in Semiconductor Physics ( V HPSP 1992 ), Kyoto, Japan, AUG 18-20, 1992.

**1991**

1. Gregorkiewicz, T.; Knap, W.; Bekman, H. H. P. T.; Brunel, L. C.; Ammerlaan, C. A. J.; Martinez, G. In ***High-field EPR spectroscopy of thermal donors in silicon***, 3rd International Symp on Research on High Magnetic Fields a Satellite of the 3rd International Conf on Magnetism Amsterdam, Netherlands, 1991; Amsterdam, Netherlands.

**1990**

1. Huant, S.; Najda, S.; Knap, W.; Martinez, G.; Etienne, B.; Langerak, C.; Singleton, J.; Thomeer, R.; Hai, G.; Peeters, F.; Devreese, J. In ***Impurity states and phenomena in quantum-wells - 2-dimensional d-centers and tunable resonant polaron strength***20th International Conf on The Physics of Semiconductors, Thessaloniki, Greece, AUG 06-10, 1990.
2. Knap, W.; Brunel, L.; Witowski, A.; Martinez, G. In **S*pin relaxation processes in high magnetic-fields***20th International Conf on the Physics of Semiconductors, Thessaloniki, Greece, AUG 06-10, 1990.
3. Stepniewski, R.; Potemski, M.; Buhmann, H.; Toet, D.; Knap, W.; Raymond, A.; Martinez, G.; Maan, J.; ETIENNE, B. In ***Effects of screening and phase-space filling on the energy structure of modulation doped gaas/gaalas quantum-wells***20th International Conf on the Physics of Semiconductors, Thessaloniki, Greece, AUG 06-10, 1990.

**1989**

1. Stepniewski, R., W. Knap, A. Raymond, G. Martinez, J.C. Maan, B. Etienne, and K. Ploog In ***Exciton-one-component plasma interaction in high magnetic fields*** 8th International Conf on the Electronic Properties of Two-Dimensional Systems. Grenoble, France, SEP 04-08, 1989.